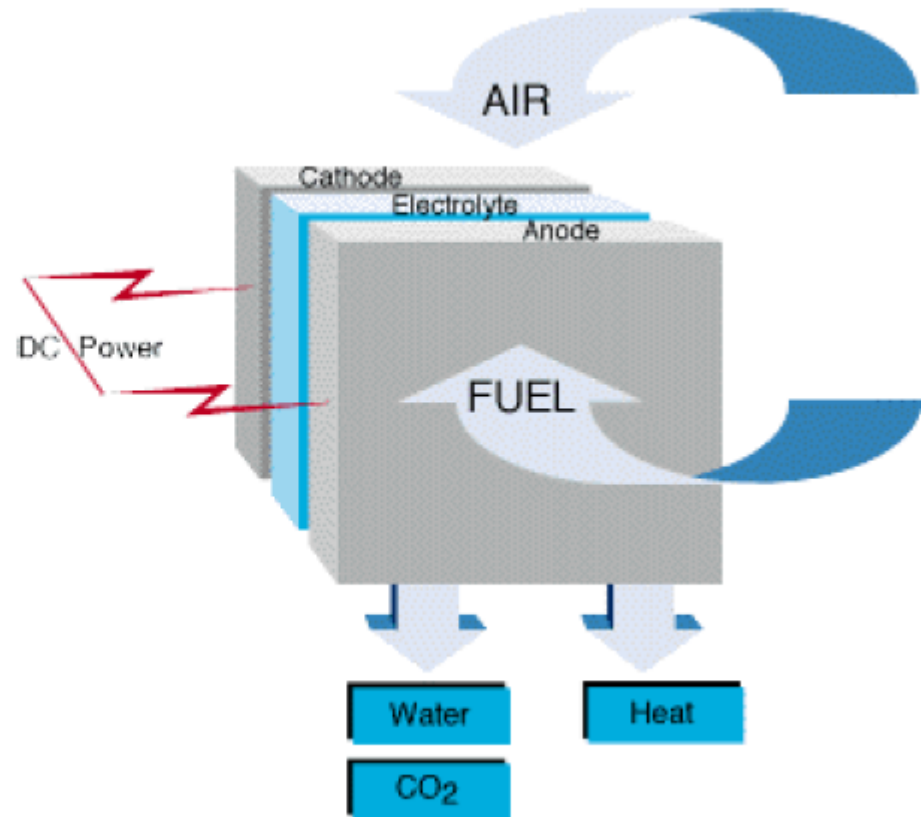


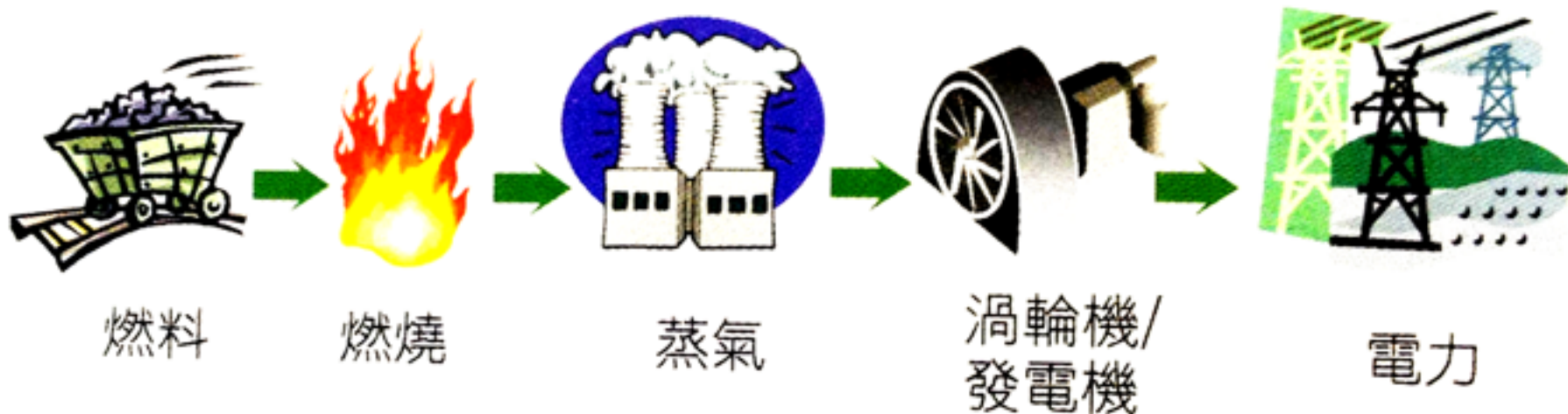
How a fuel cell function

- Unlike battery, fuel cell **does not run down or require recharging**.
- Fuel cell consists of two electrodes sandwiched around an electrolyte.
- Encouraged by catalysts, **H₂ (fuel)** and **O₂ (air)** occur anodic and cathodic reaction (with electrons create a separate current) then generate **electricity, water** and **heat** by chemical reaction.

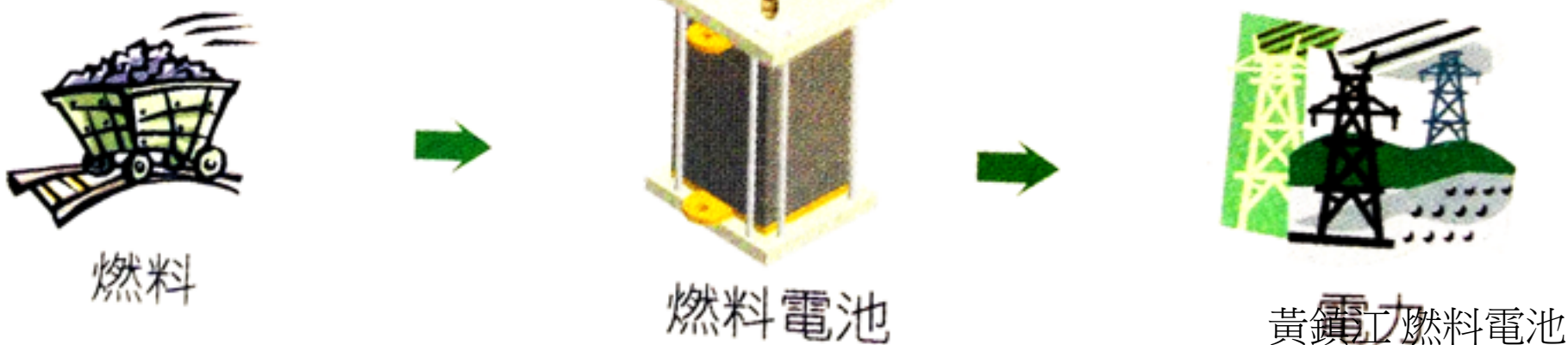


燃料電池與傳統熱機的火力發電比較

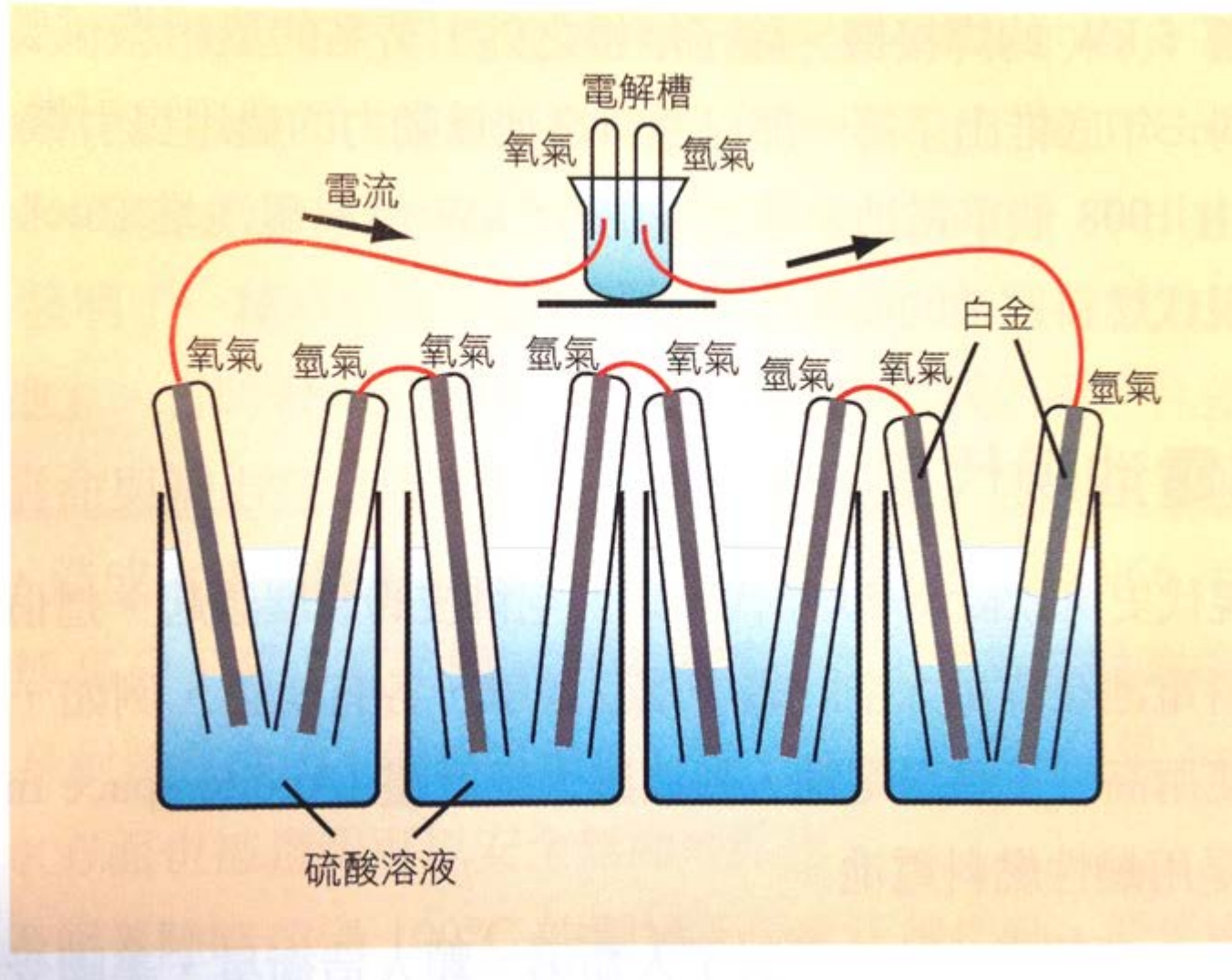
(a) 傳統熱機發電



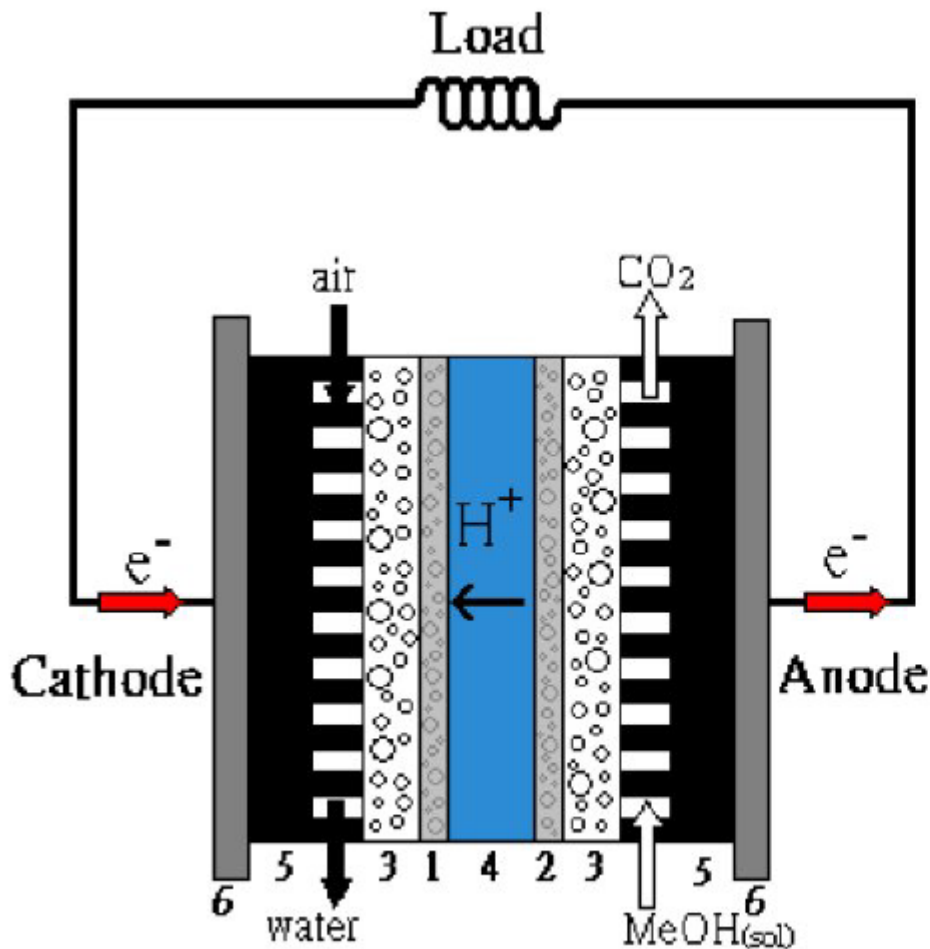
(b) 燃料電池發電



Willam R. Grove 進行的氣體電池實驗



DMFC, direct methanol fuel cell

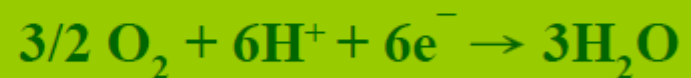


Anode

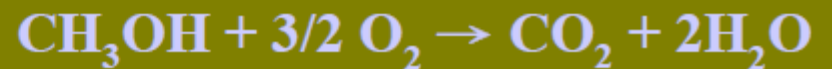


Electrolyte

Cathode



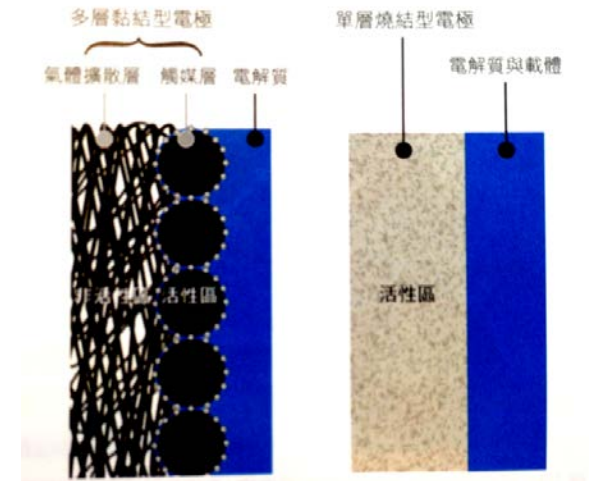
Overall



觸媒與多孔氣體擴散電極

表 1-5 燃料電池使用觸媒電極結構之比較

種類	AFC	PEMFC	PAFC	MCFC	SOFC
陽極觸媒	雷尼鎳、鉑/碳	鉑/碳	鉑/碳、鉑鈦/碳	鎳-鉻合金、鎳-鋁合金	鎳/YSZ
陰極觸媒	雷尼鎳、鉑/碳	鉑/碳	鉑/碳	鋰化-氧化鎳	摻錫錳酸鎳
電極結構	單層雷尼鎳電極或 多層黏結型電極	多層黏結型電極	多層黏結型電極	單層燒結型電極	單層燒結型電極



- 主要可分為單層燒結型電極以及多層的黏結型電極
- 單層：將金屬觸媒與電解質之混合粉末以燒結方式製作多孔結構
- 多層：在高分散型觸媒內填加黏結劑 (PTFE)後黏貼至氣體擴散層上。擴散區為非活性區

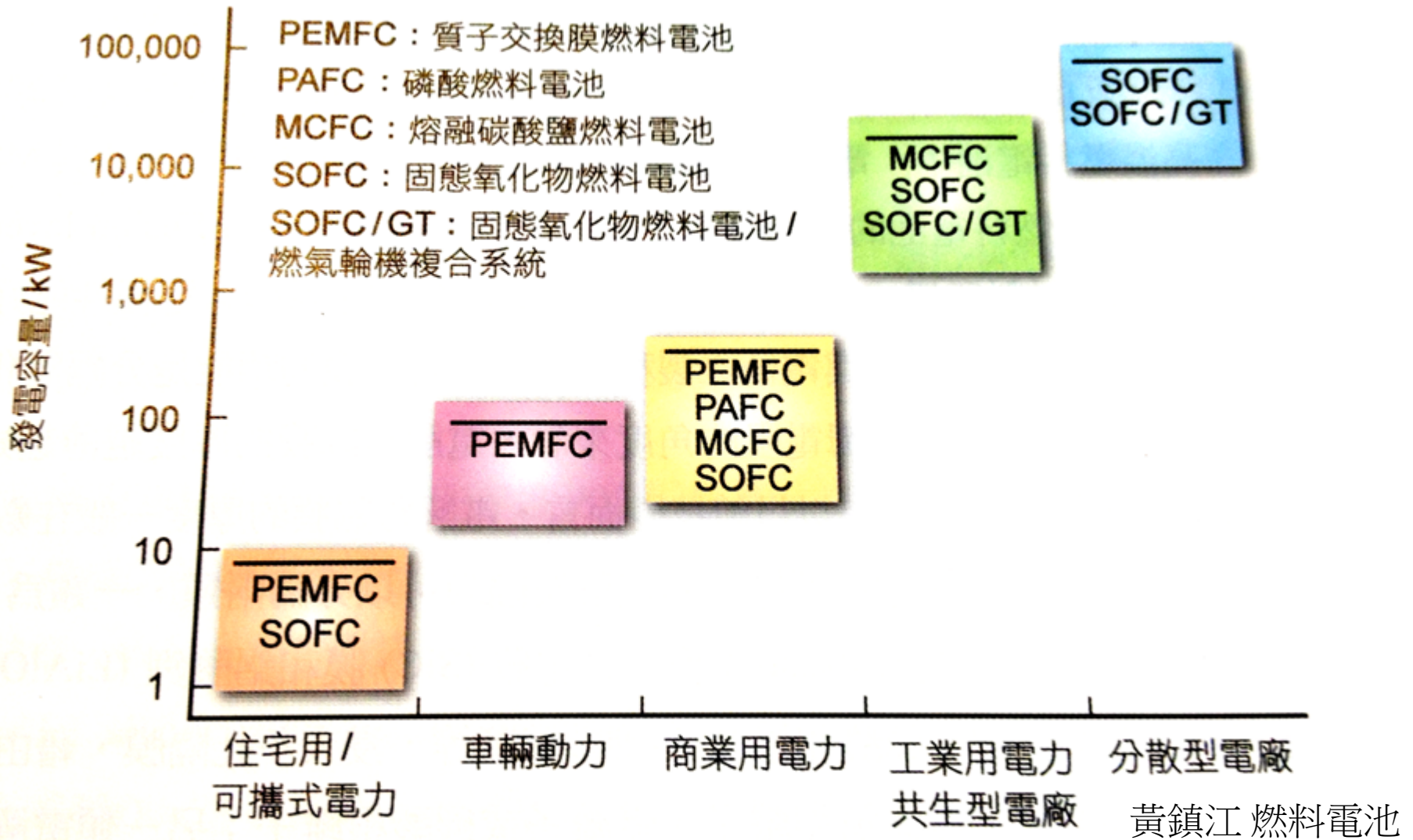
燃料電池用燃料系統之比較



燃料電池的分類

- 依電解液性質可分為五類
 - 1) 鹼性燃料電池 (alkaline fuel cell, AFC)
 - 2) 磷酸燃料電池 (phosphoric acid fuel cell, PAFC)
 - 3) 質子交換燃料電池 (proton exchange membrane fuel cell, PEMFC)
 - 4) 熔融碳酸鹽燃料電池 (molten carbonate fuel cell, MCFC)
 - 5) 固態氧化物燃料電池 (solid oxide fuel cell, SOFC)

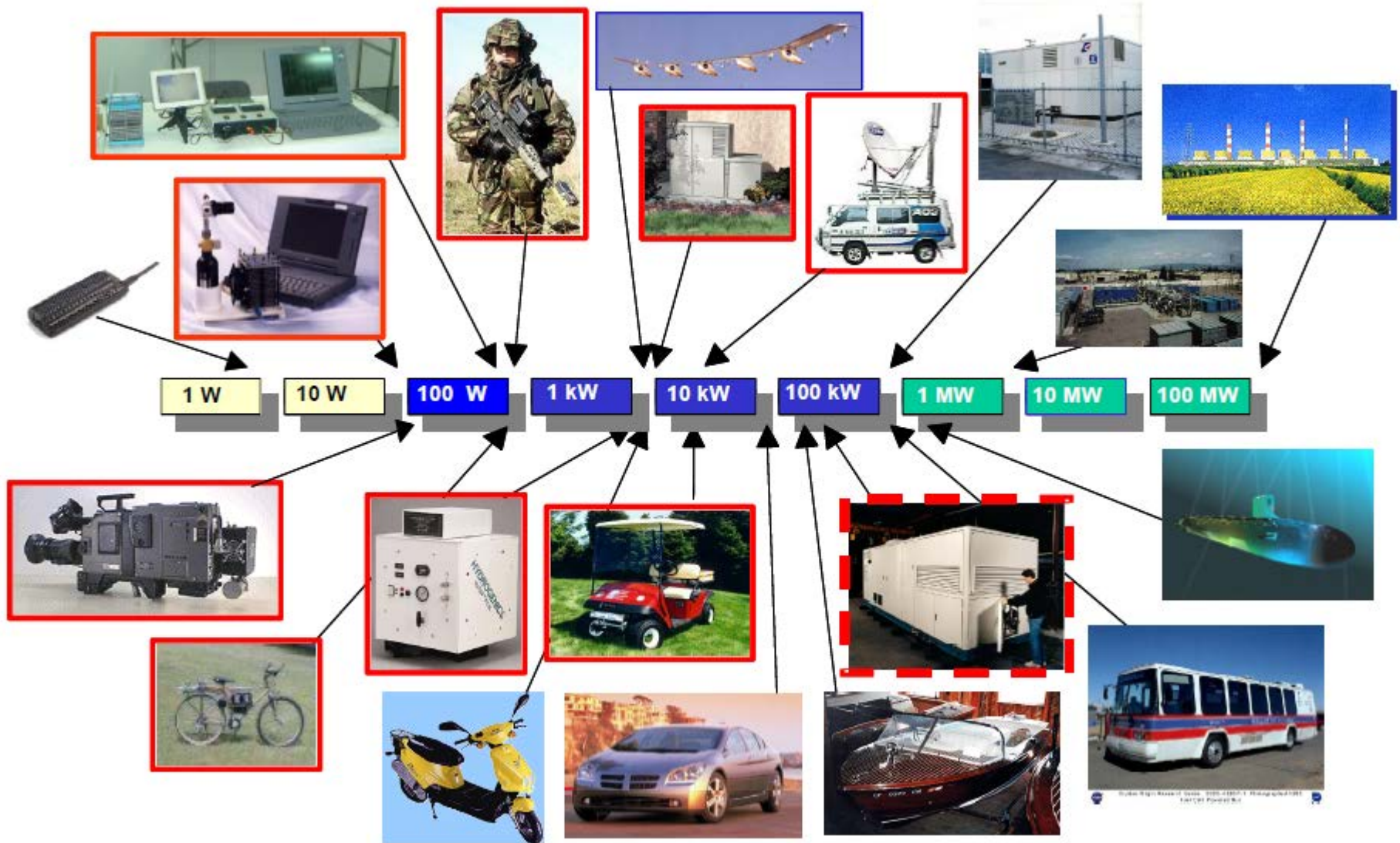
燃料電池發電容量與適用範圍



燃料電池特點

- 效率高：目前工作的燃料電池效率可達**40-60%**，平均單位質量燃料所產生的電能，僅次於核能
- 噪音低：結構簡單且沒有運轉機件
- 污染低：氫氣為主要燃料。
- 進料廣：只要含有氫原子的物質都可以當作燃料來源，包括天然氣、石油、燃煤、酒精、甲醇。
- 用途多：可提供的電力範圍在**1W~1000MW**間

Fuel Cell



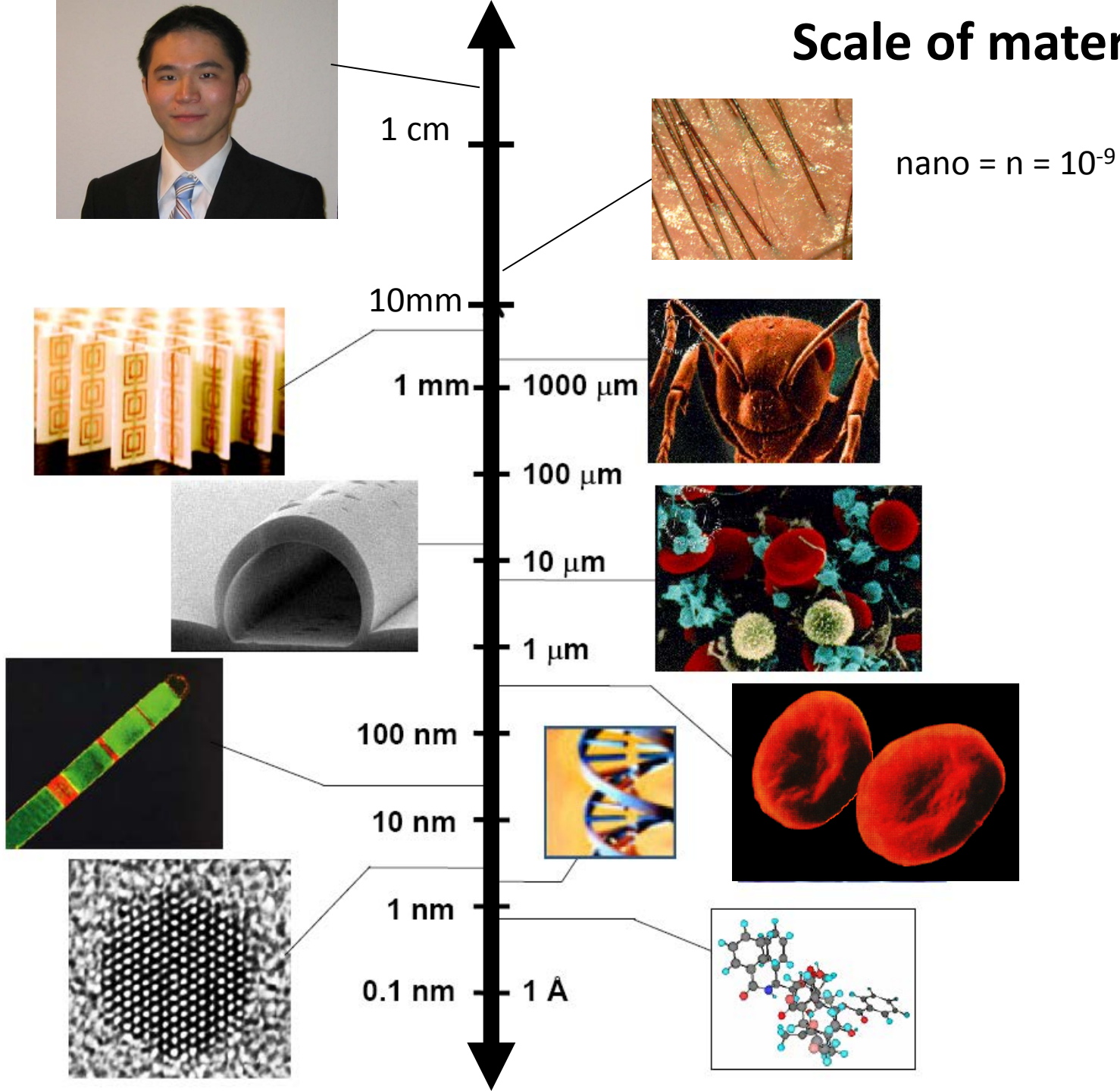
能源與環境

奈米材料於綠能科技的應用

Hsing-Yu Tuan (段興宇)

Assistant Professor in Chemical Engineering,
National Tsing Hua University

Scale of materials



Inorganic Nanomaterials: a inorganic kind of polymer




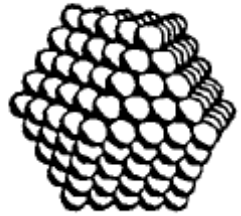
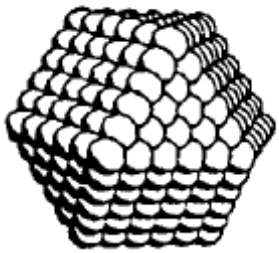
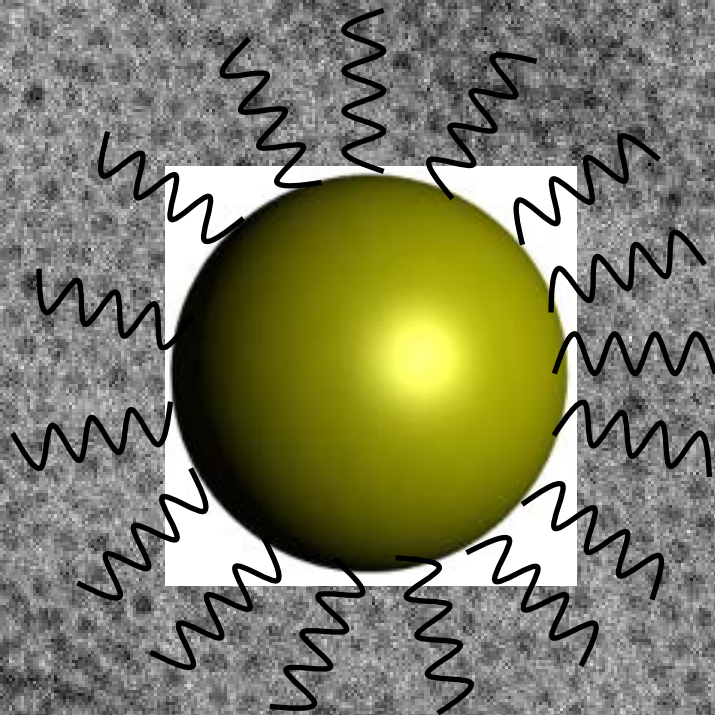
Full-shell "magic number" clusters					
Number of shells	1	2	3	4	5
Number of atoms in cluster	13	55	147	309	561
Percentage of surface atoms	92	76	63	52	45

Figure 4. Idealized representation of full-shell metal clusters with "magic numbers" of atoms, which are built upon the densest sphere packing (modified with permission from ref. [49c], copyright 1999 Elsevier).

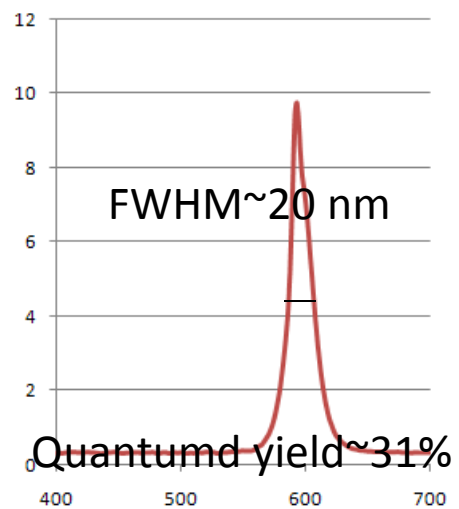
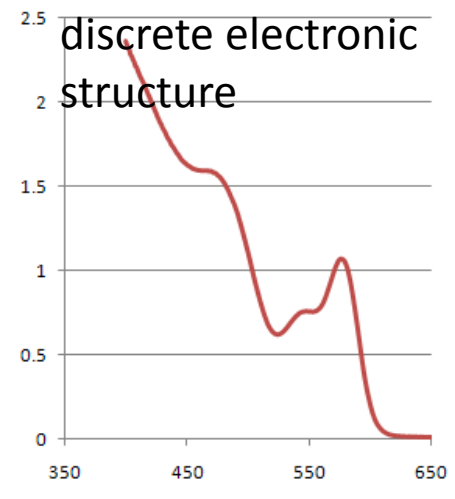
- For example,....Au₁₃, Au₂₀, Pt₃₈, Au₅₅, Rh₅₅, Pt₃₀₉, Pd₅₆₁, Pd₁₄₁₅, Pd₂₀₅₇...
- n could be over million

CdSe nanocrystals

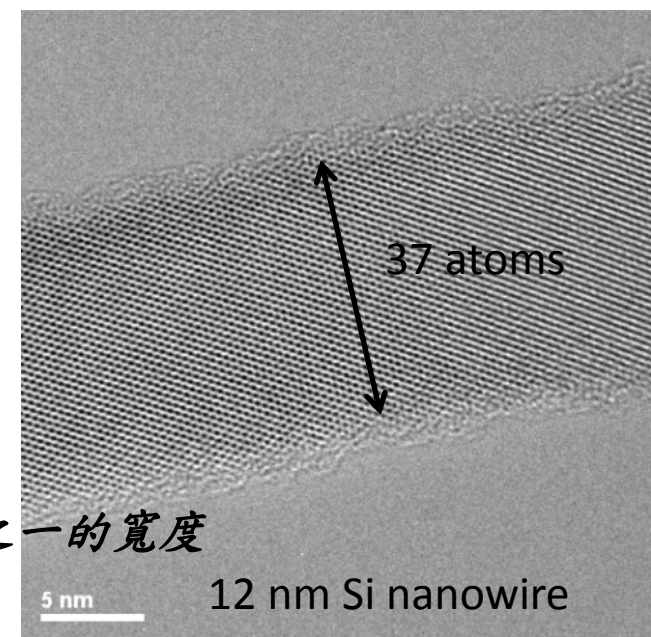
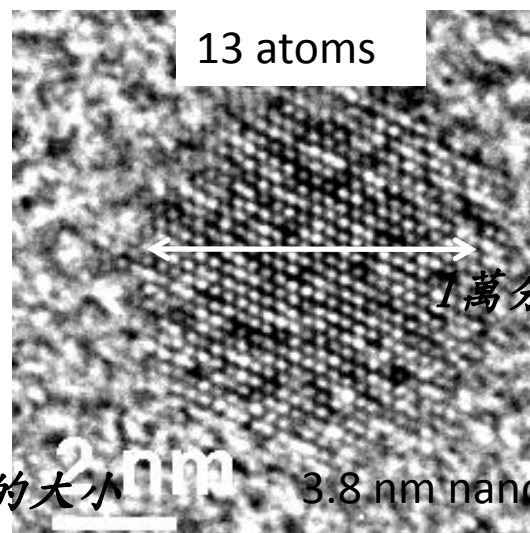
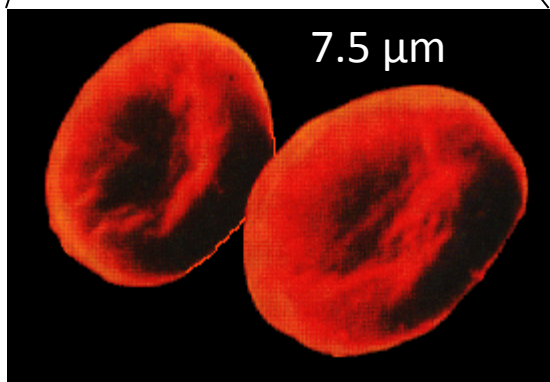
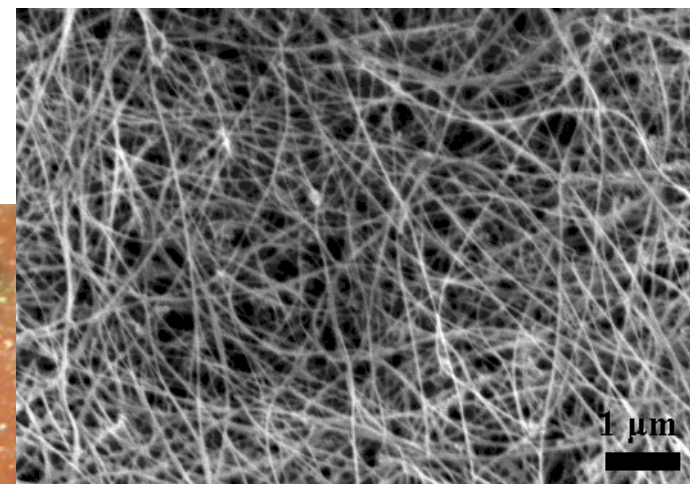
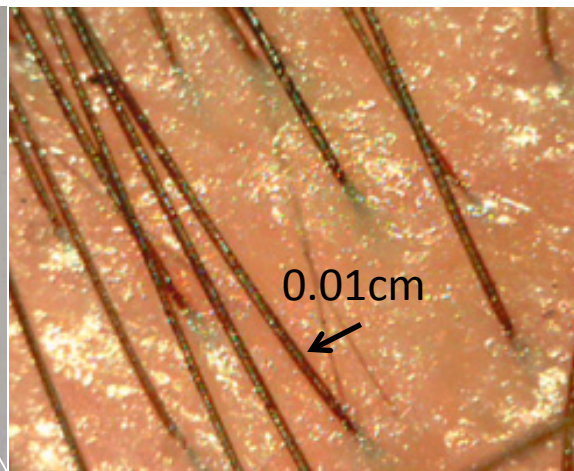
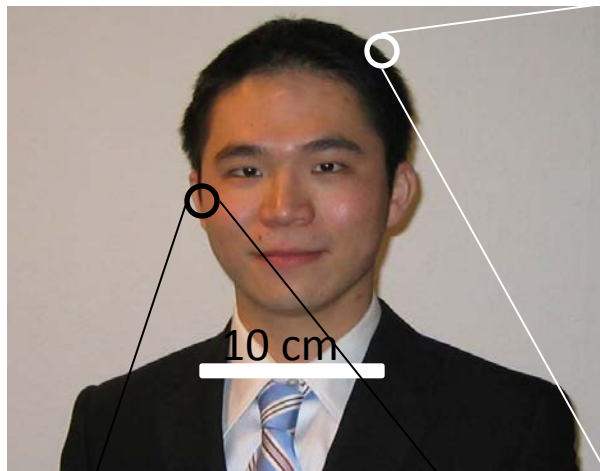
Average: 4.69nm
Size variation less
Than 20%



50 nm



Nanocrystals and nanowires



千分之一的大小 3.8 nm nanocrystal

Nanomaterials for Energy: Niche

Size and shape-dependent properties

Cost effective Large-Scale Production

Nano-scale structure/composition engineering via facile synthetic routes

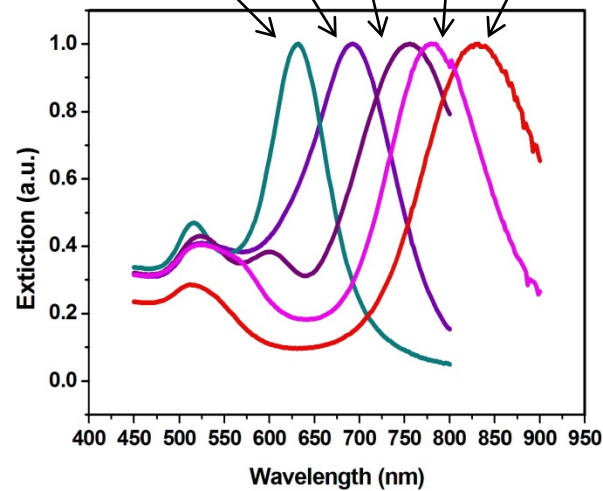
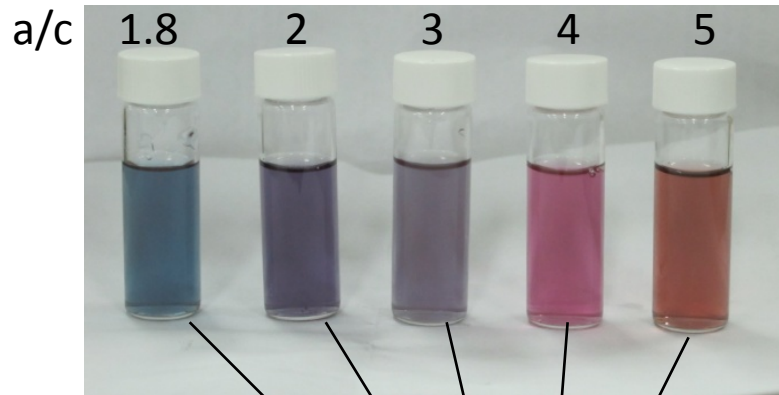
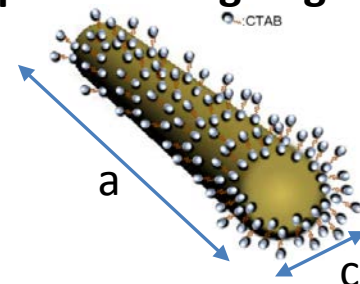
Fast and Continuous processing for device fabrication

Size and shape-dependent properties

Size Dependent optical properties of CdSe quantum dots

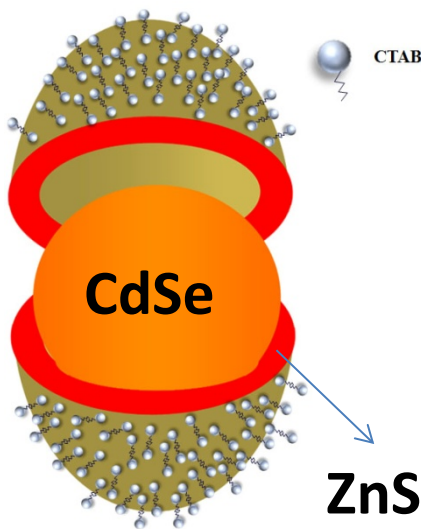


Plasmon absorption tuning of gold nanorods

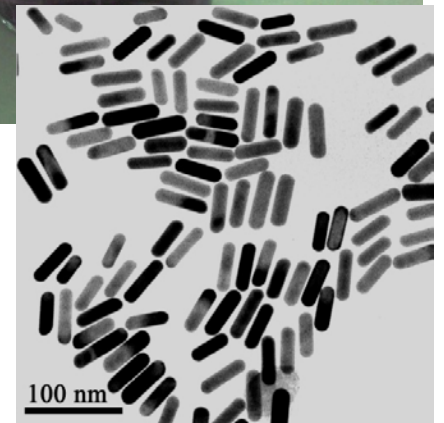
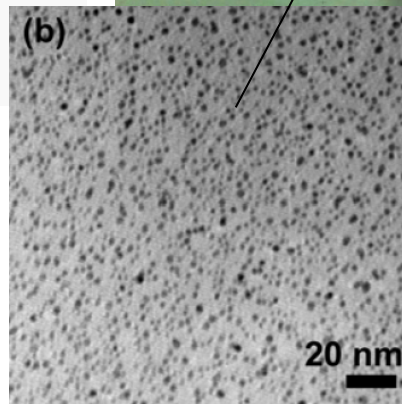
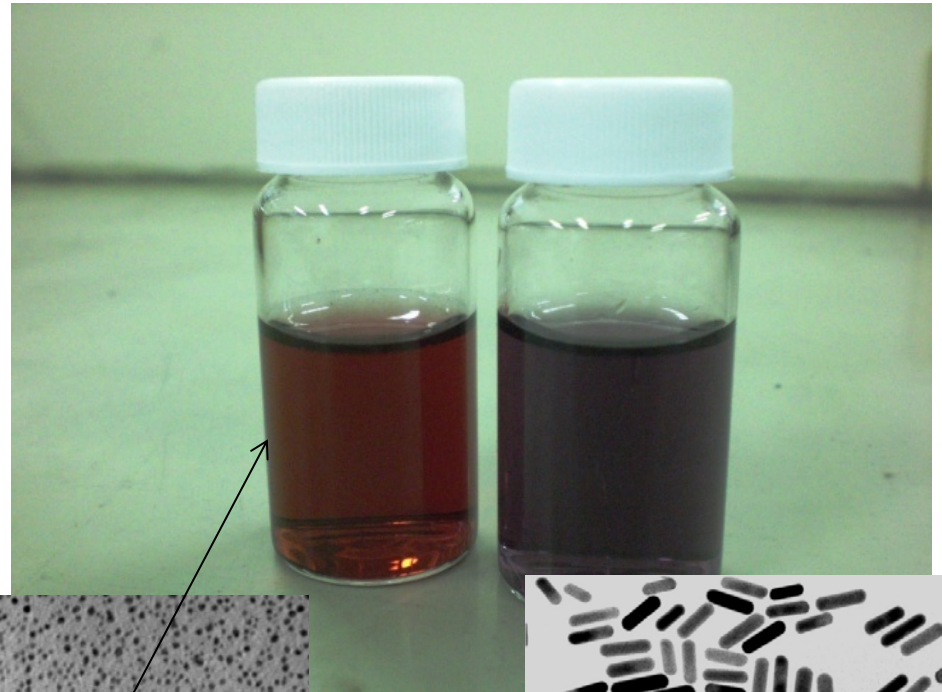


Bright water-soluble CdSe/ZnS/CTAB quantum dots

Quantum efficiency 40-60%



Color comparison between bulk gold and nanogold



Optical properties of CdSe Qdots

A)



Emission Wavelength (nm):

500

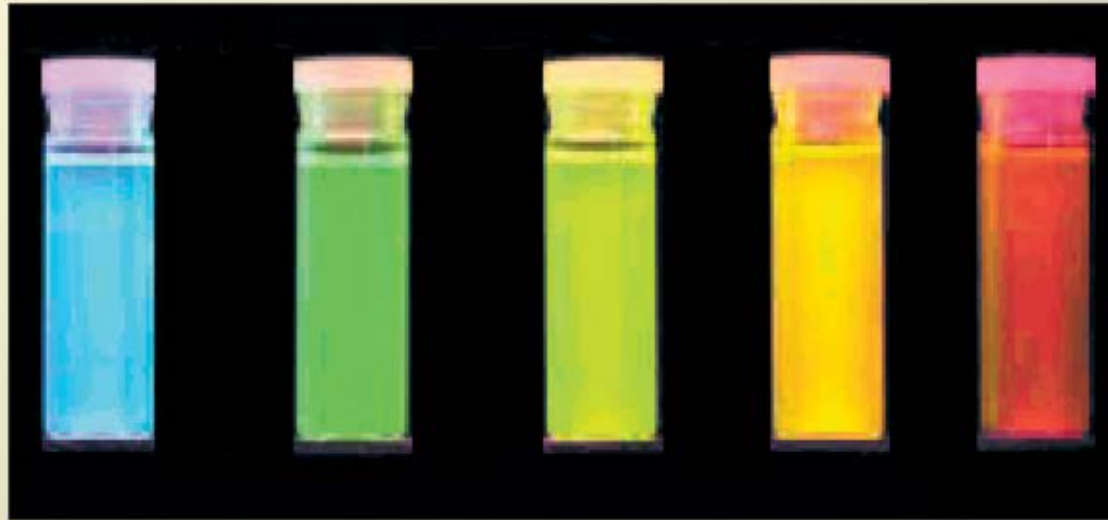
543

565

587

610

B)



C)

Conduction Band

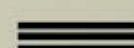


$\Delta E = 2.5 \text{ eV}$

Valence Band



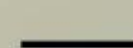
$\Delta E = 2.3 \text{ eV}$



$\Delta E = 2.2 \text{ eV}$



$\Delta E = 2.1 \text{ eV}$

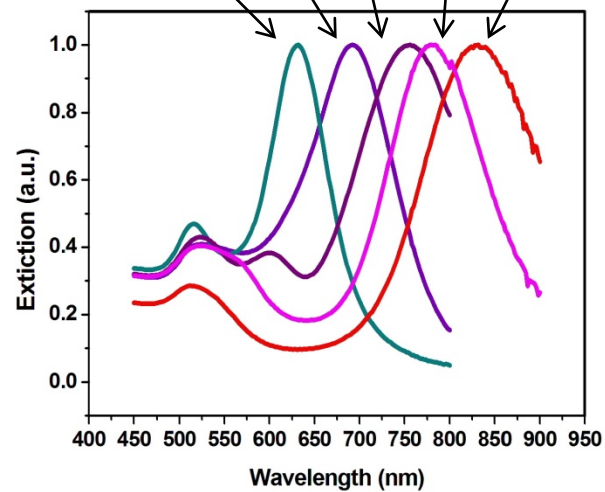
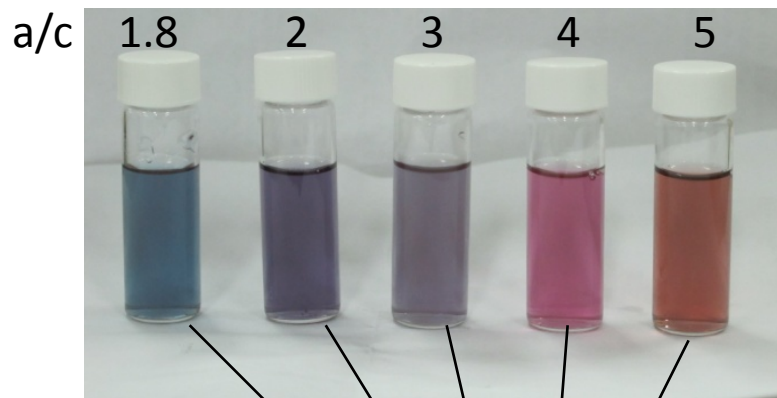
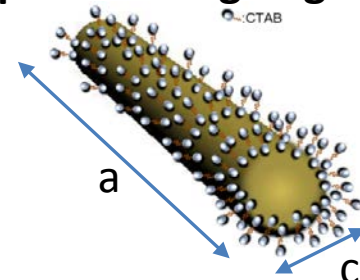
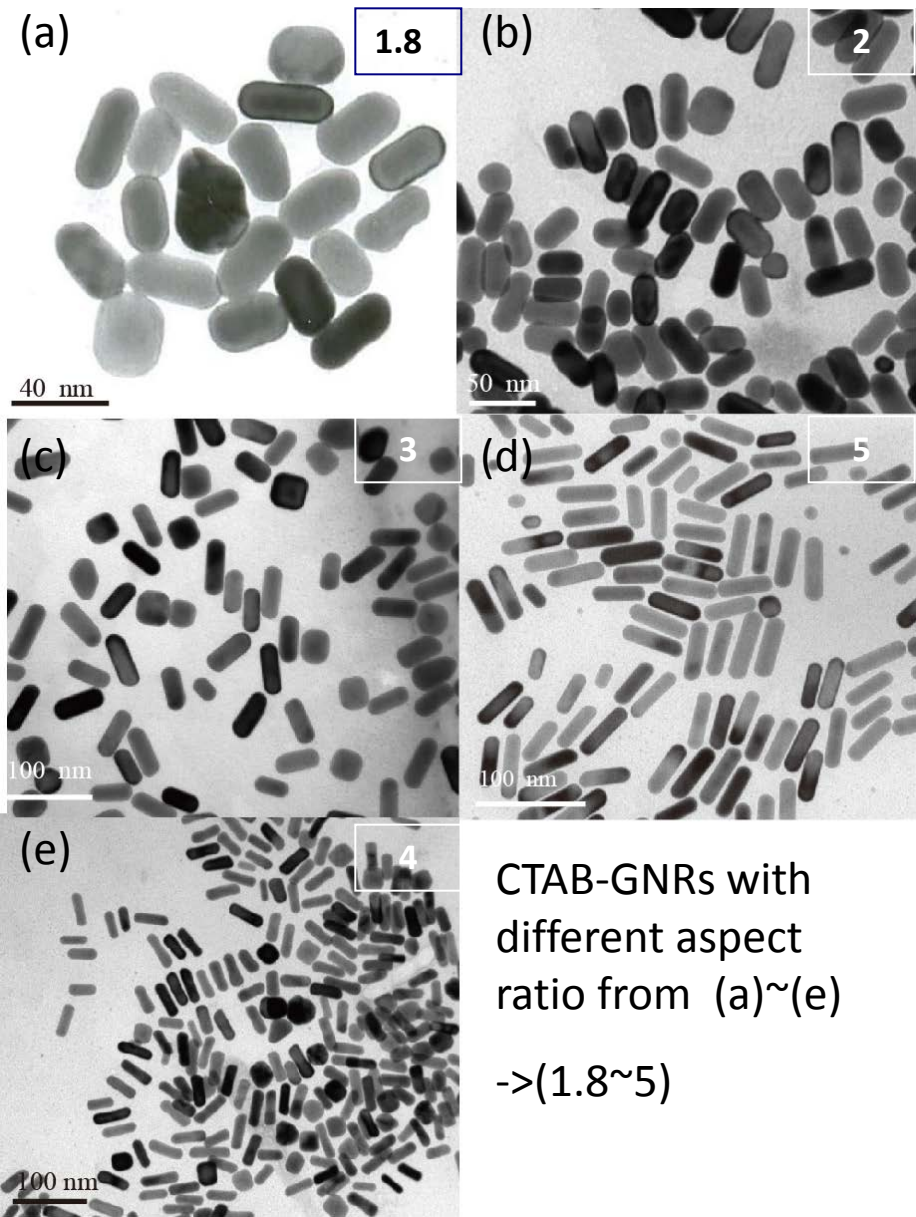


$\Delta E = 2.0 \text{ eV}$

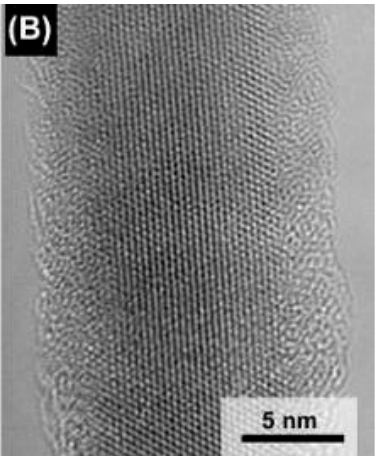
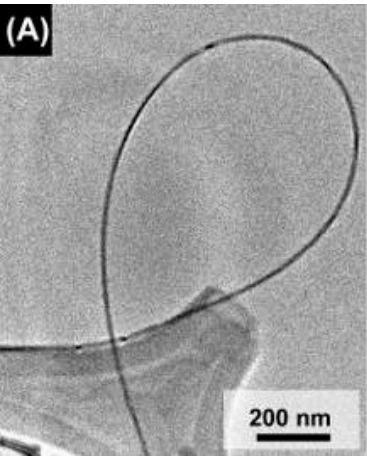
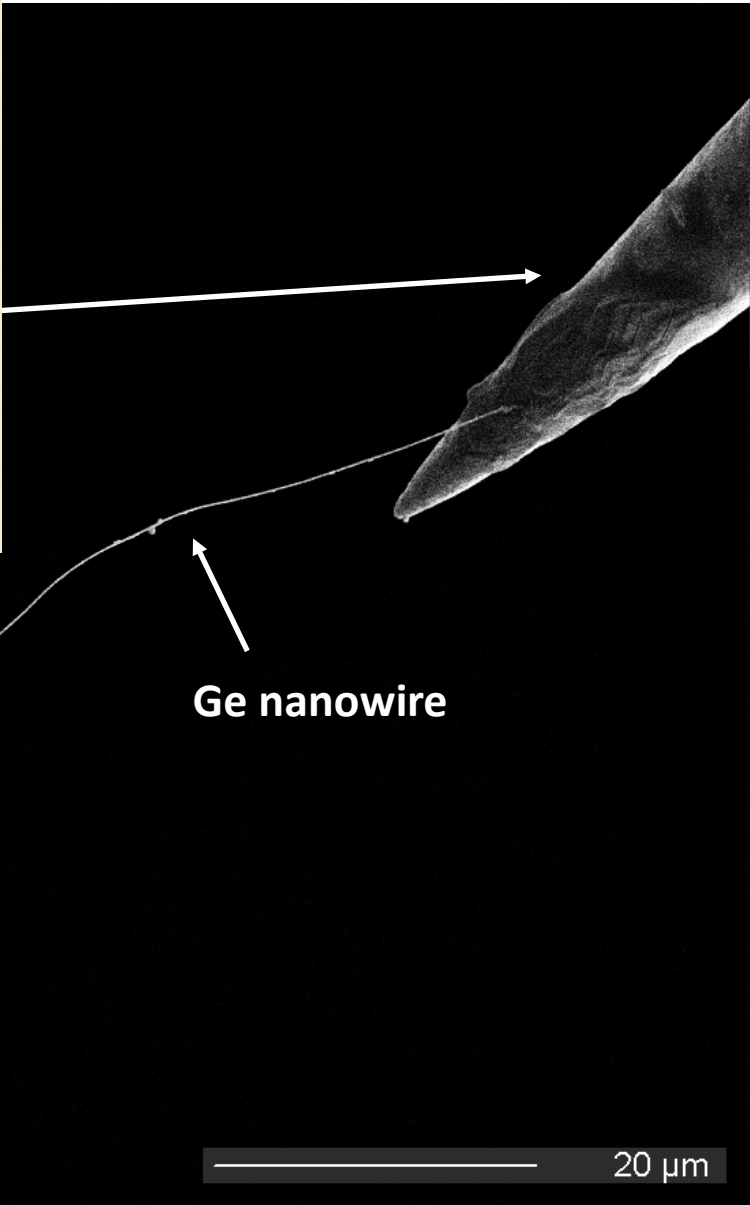


Characteristic of nanomaterials: plasmonic effect

Plasmon absorption tuning of gold nanorods



Characteristic of nanomaterials: flexible mechanics



Various carbon nanomaterials

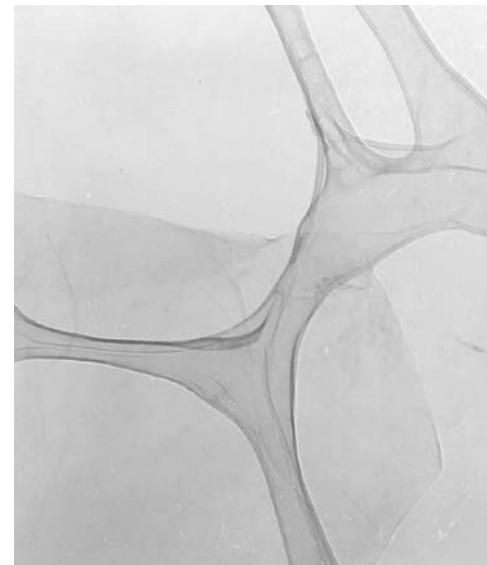
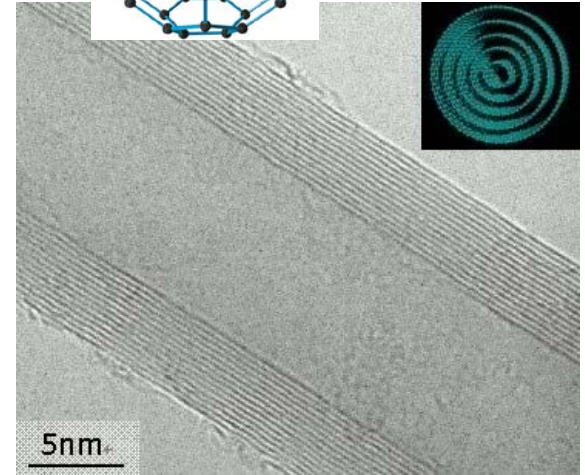
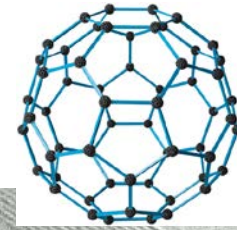
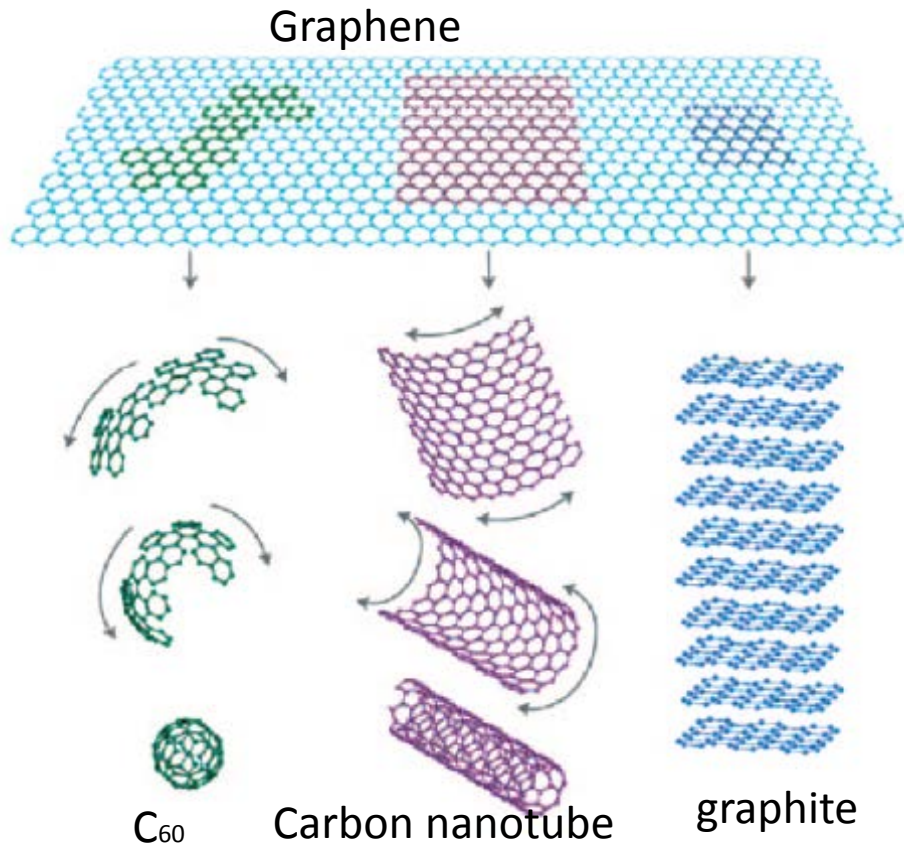
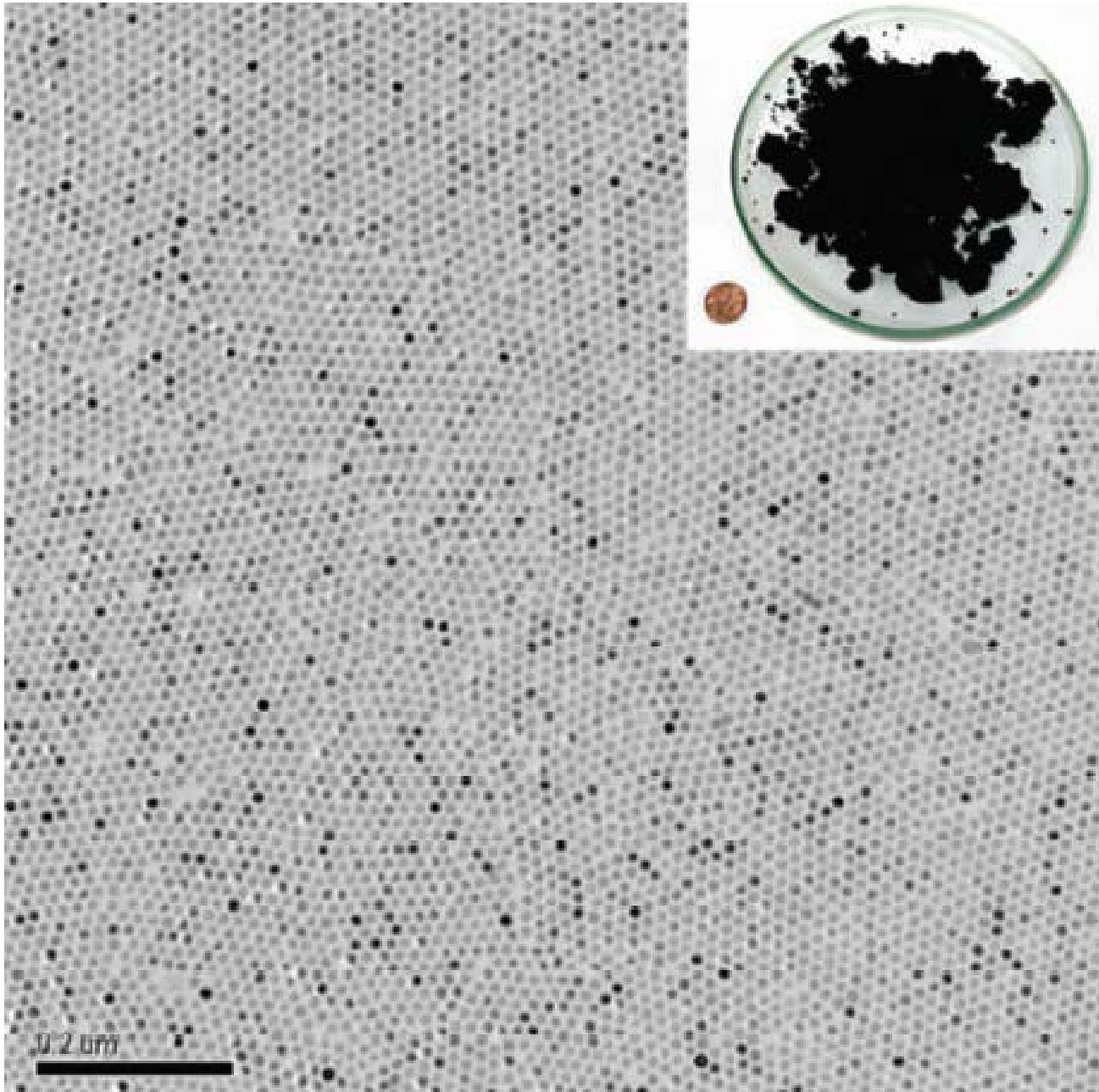


Figure 1. Graphene: the parent of all graphitic forms. (From Ref. [1a].)

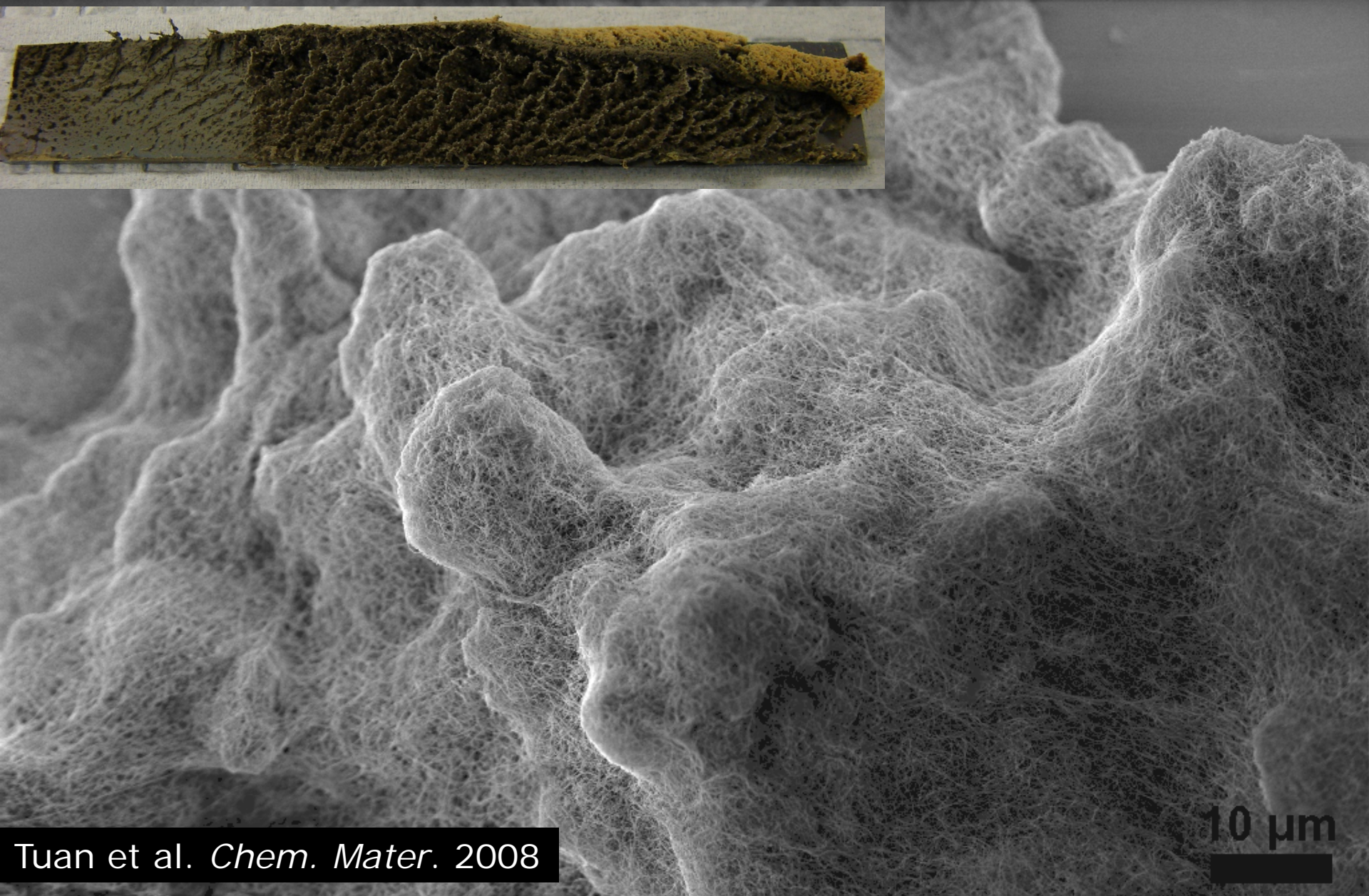
Cost effective Large-Scale Production

Gram-scale Fe₃O₄ nanocrystal production



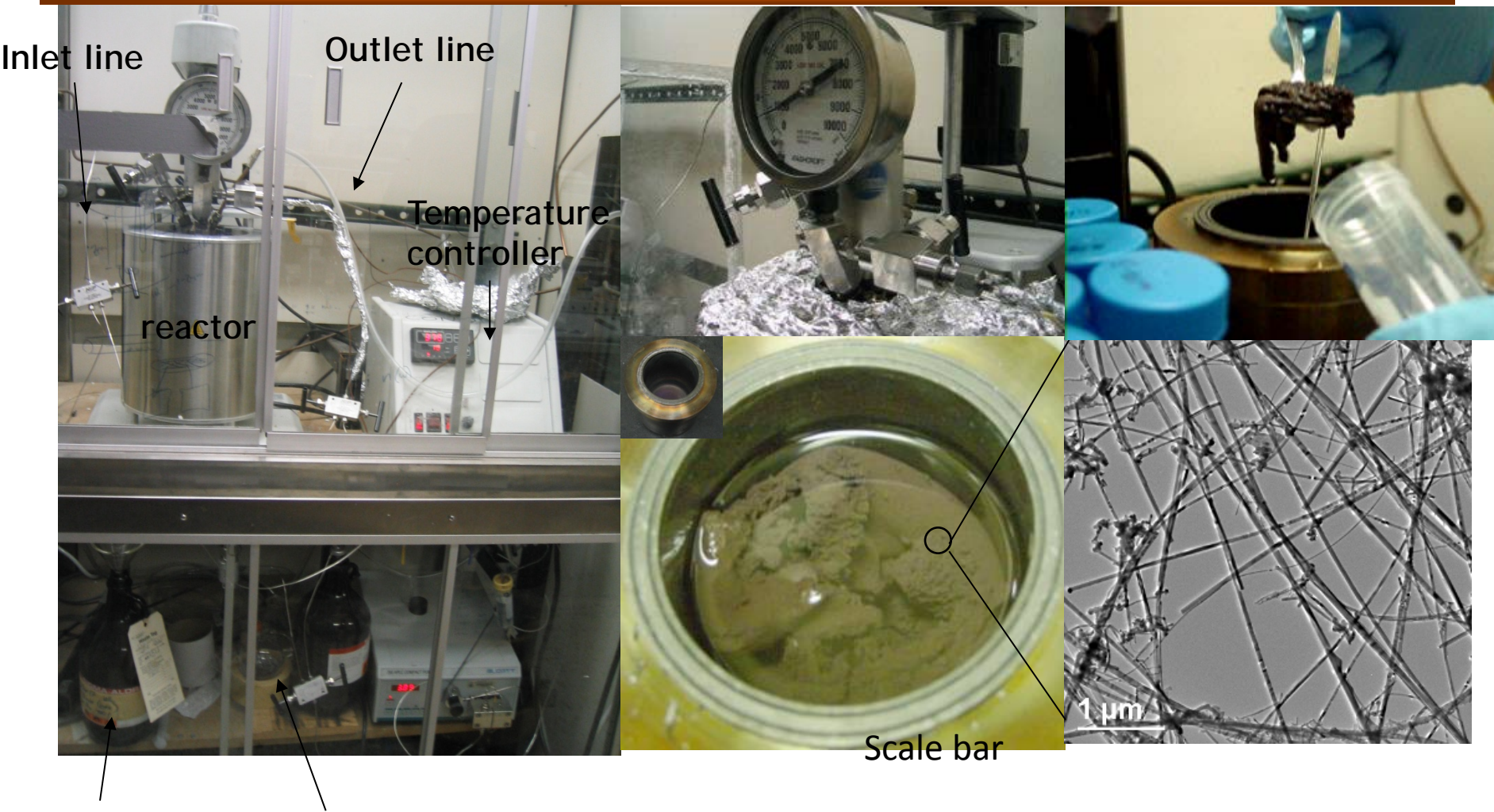
You need larger glassware

Chemical Engineering: Scale-Up synthesis of Silicon Nanowires



10 μm

Chemical Engineering: Scale-Up synthesis of Silicon Nanowires



250 ml Parr reactor operation
~ 1 gram germanium nanowires
~ high quality, pure nanowires

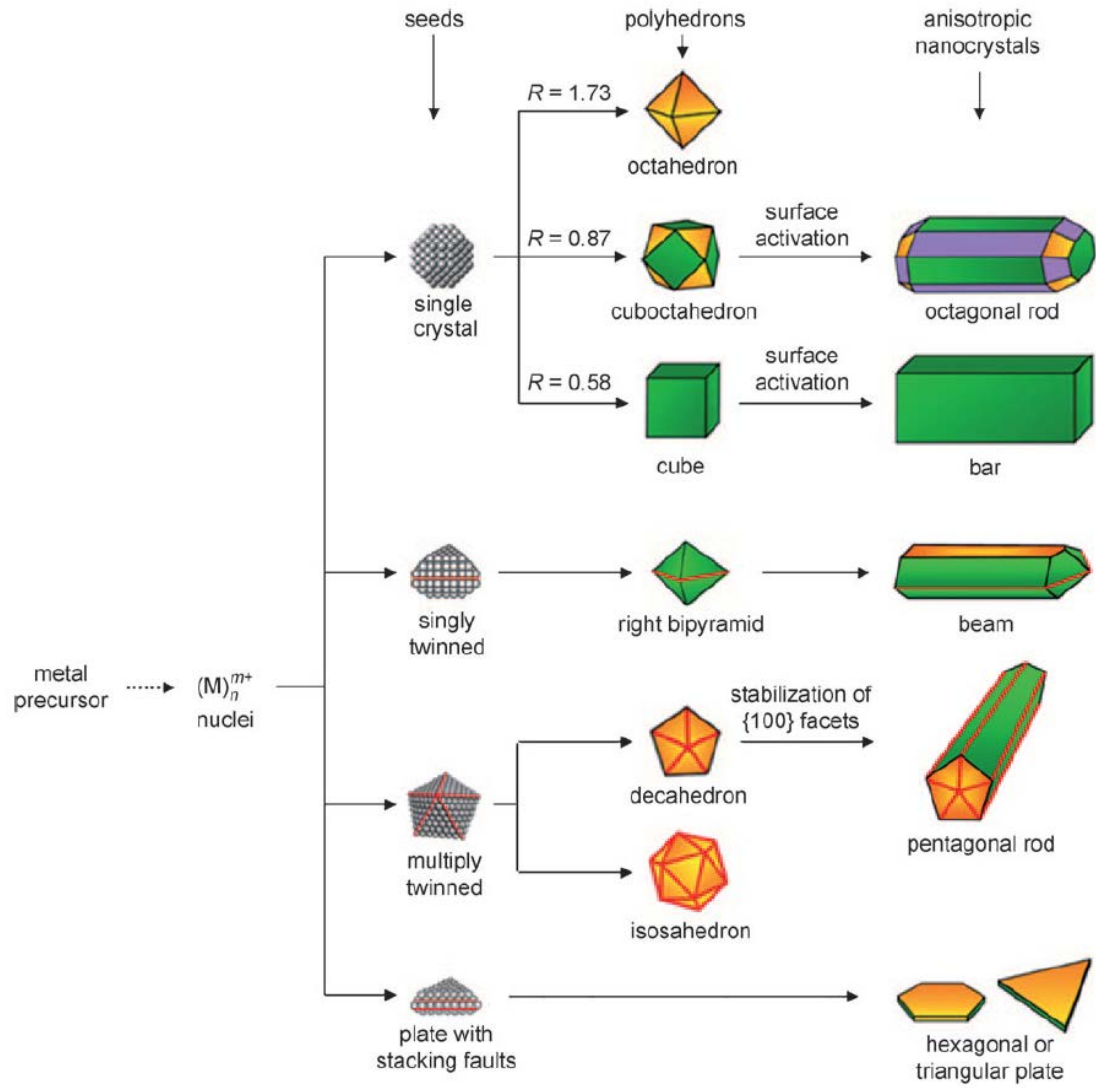
Large-scale Synthesis of Nanomaterials



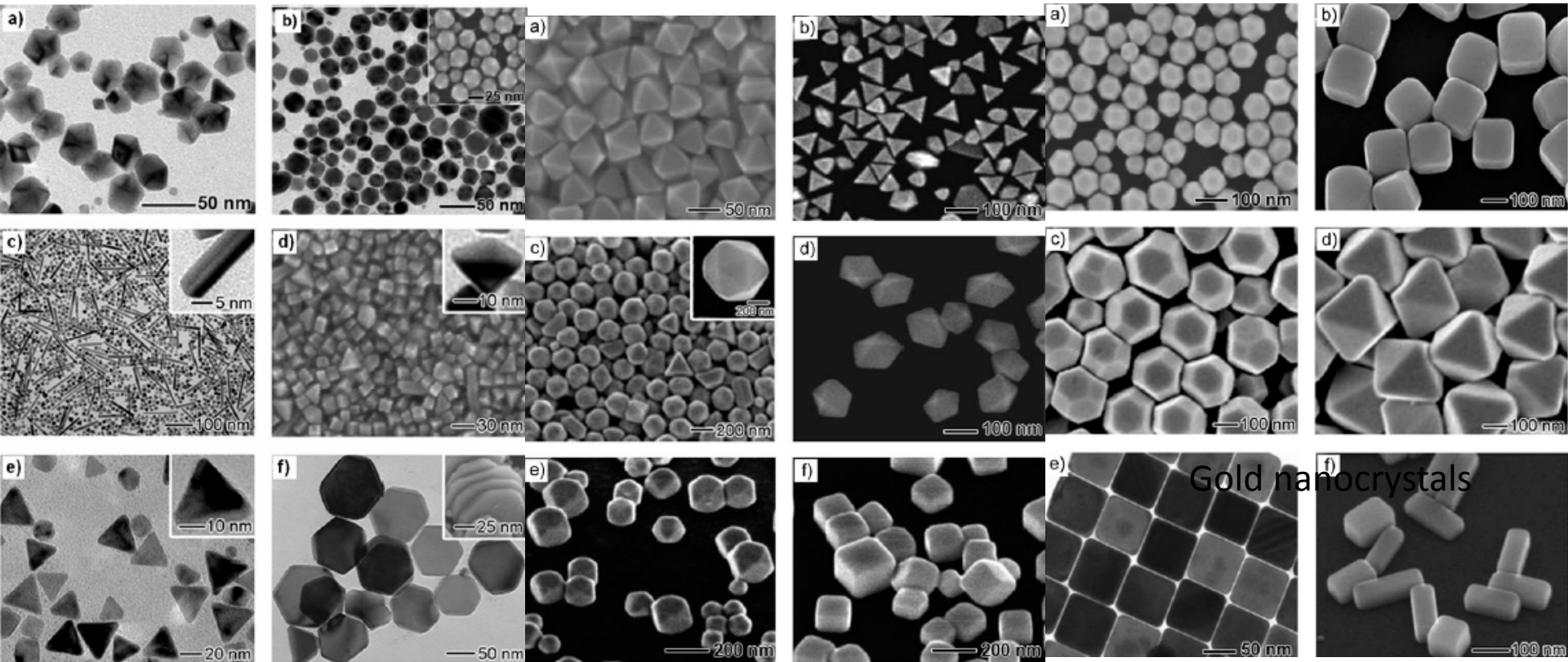
- Kg/day production!
- Chemists investigate new chemistry
- Chemical Engineers develop the large-scale process ---←\$\$\$\$\$\$\$\$

Nano-scale structure/composition
engineering via facile synthetic routes

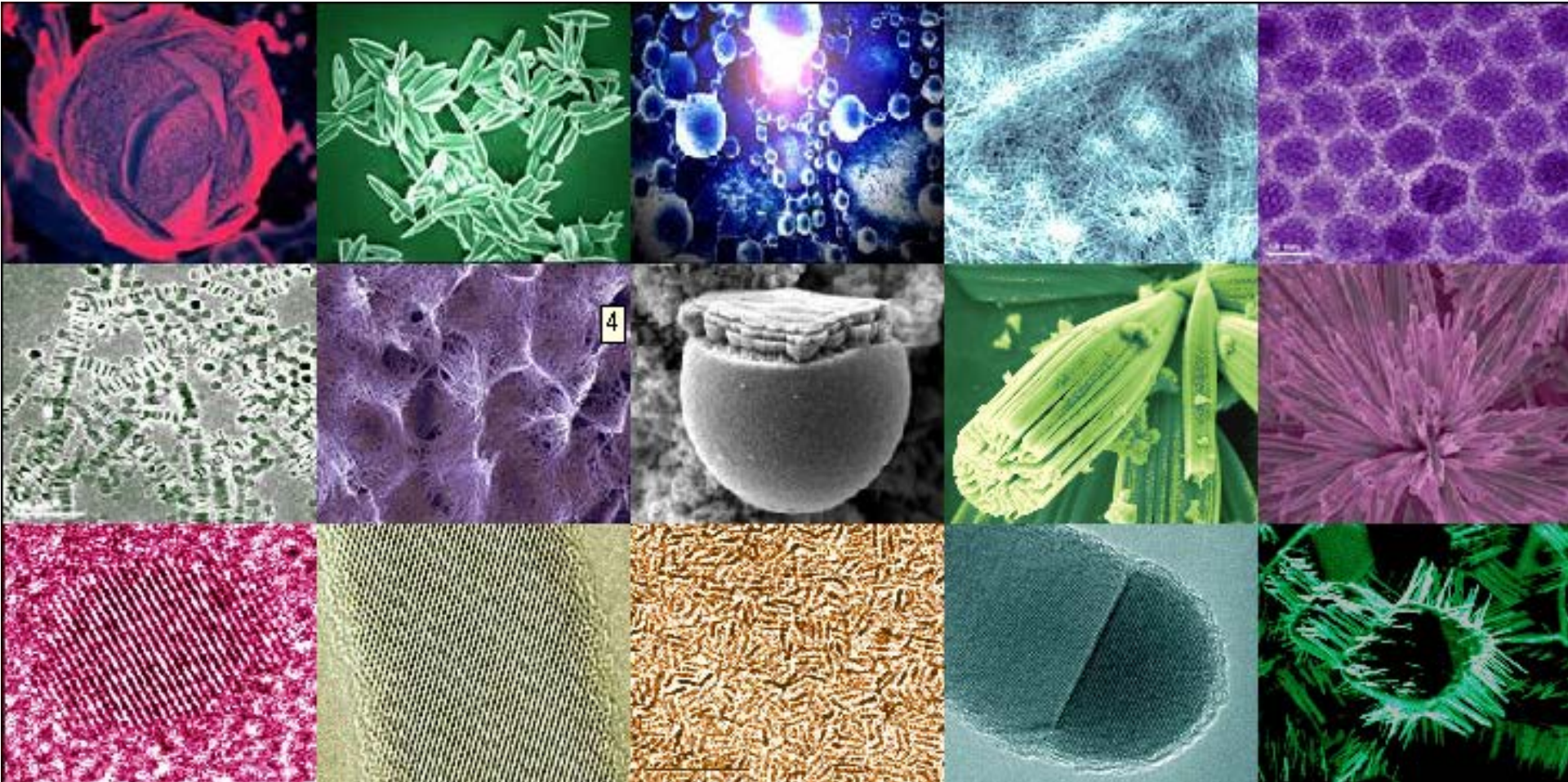
Artificial design of nanostructures



Morphology control of nanostructures

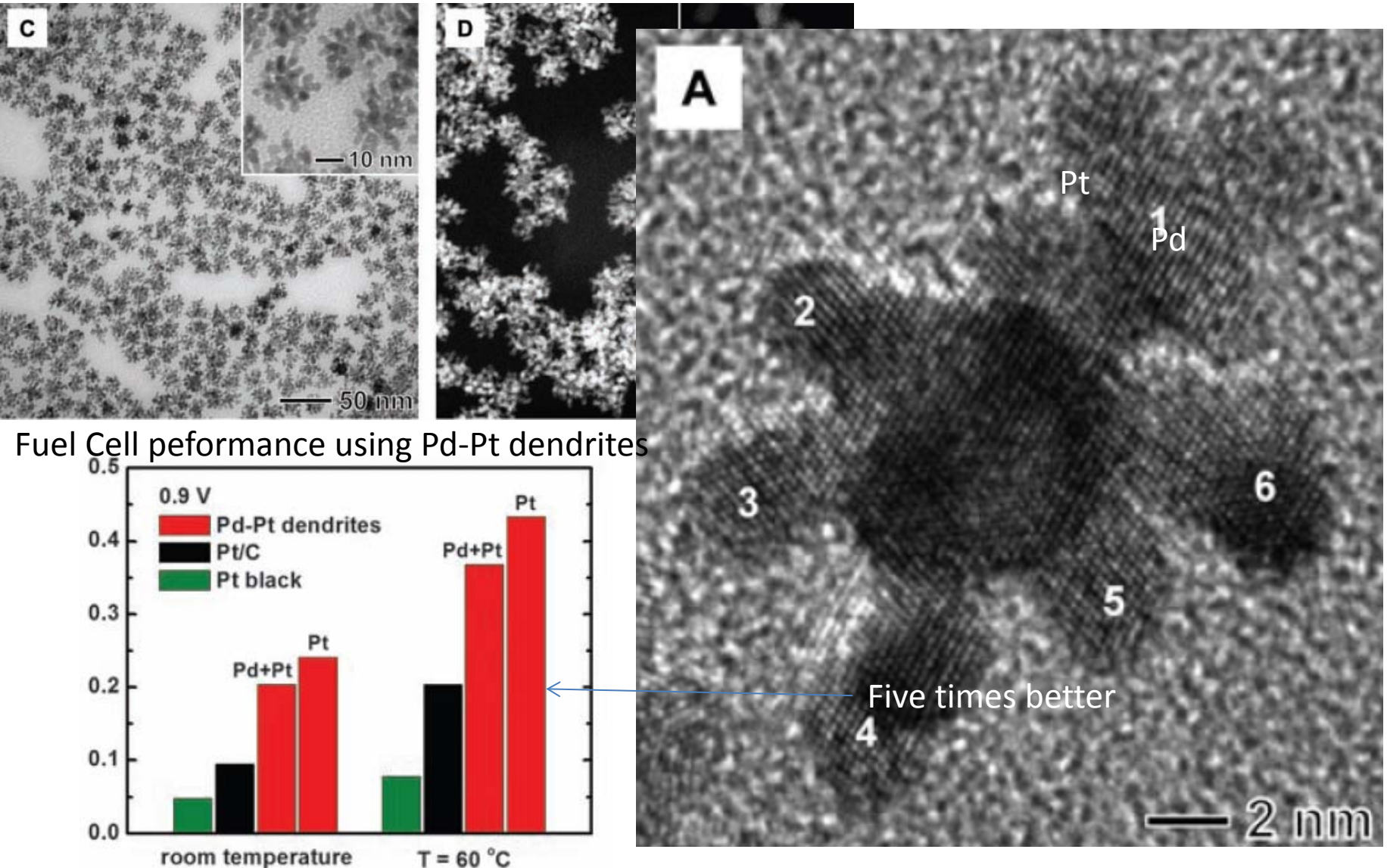


Size, shape, and structure control of various nanomaterials

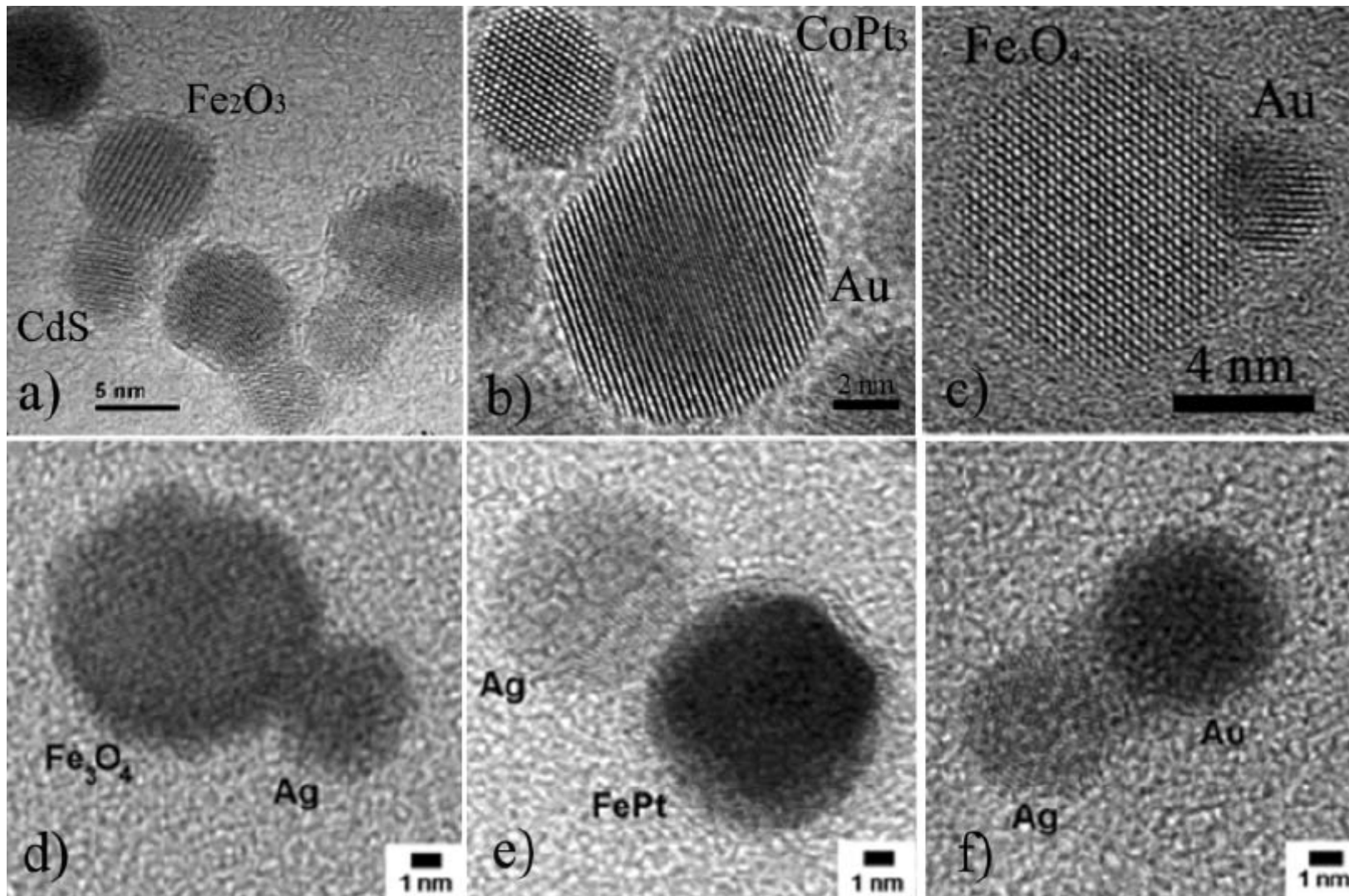


Interested materials: Au 、 Ag 、 Cu 、 Fe 、 Si 、 Ge 、 ZnO 、 TiO₂ 、 CIGS 、 NaYF₄:Er⁺²

Ultrahigh surface area of nanocrystals

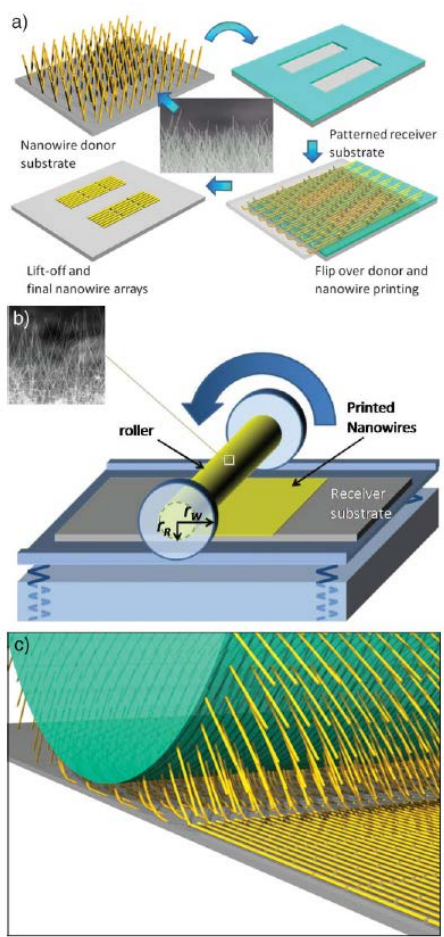
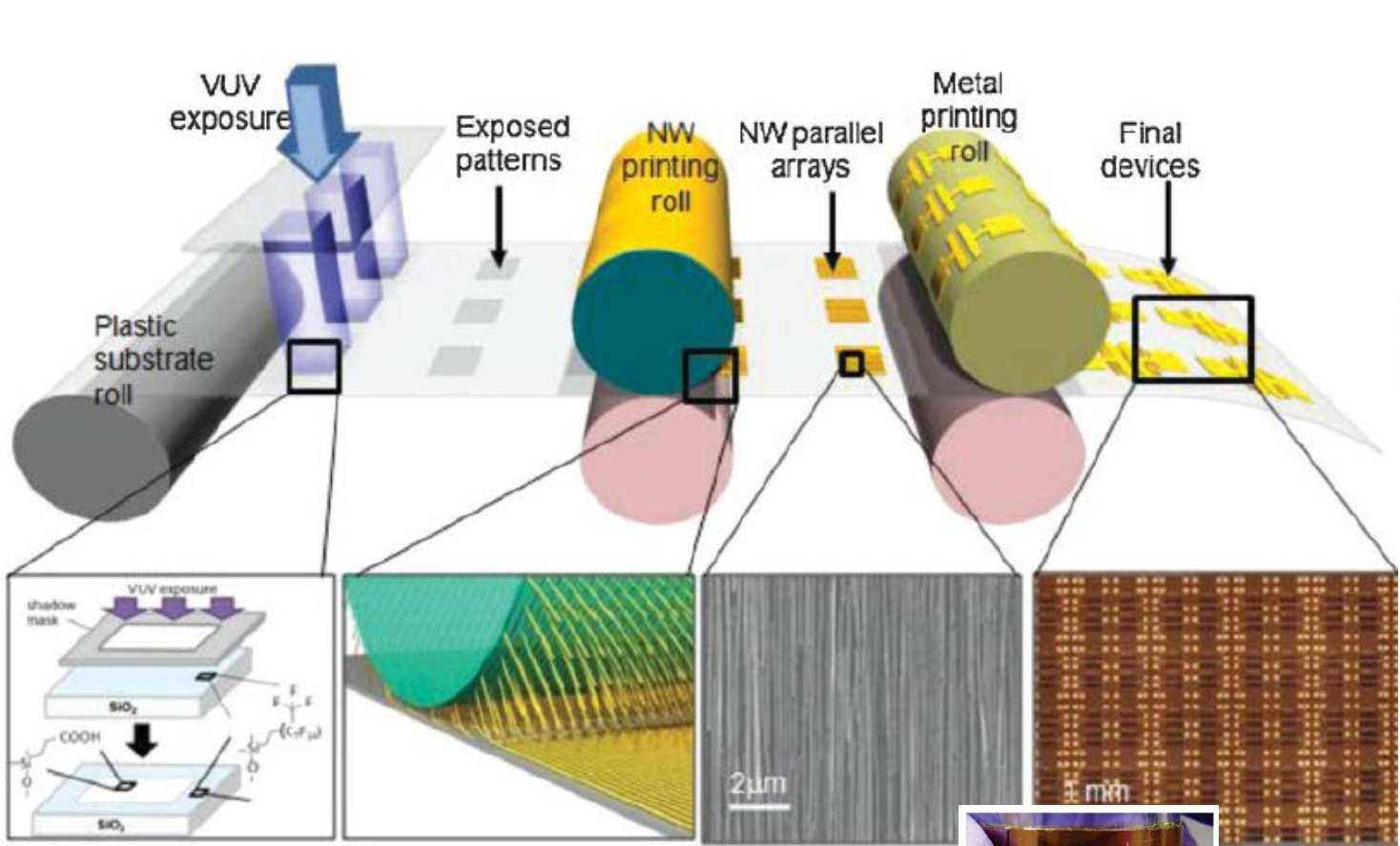


Heterodimers and oligomers of nanocrystals

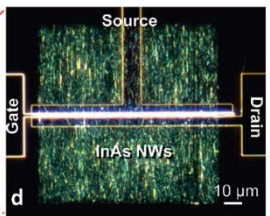
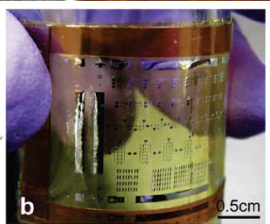


Fast and Continuous processing for
device fabrication

Cost-effective processing: Roll-to-Roll and nonvacuum

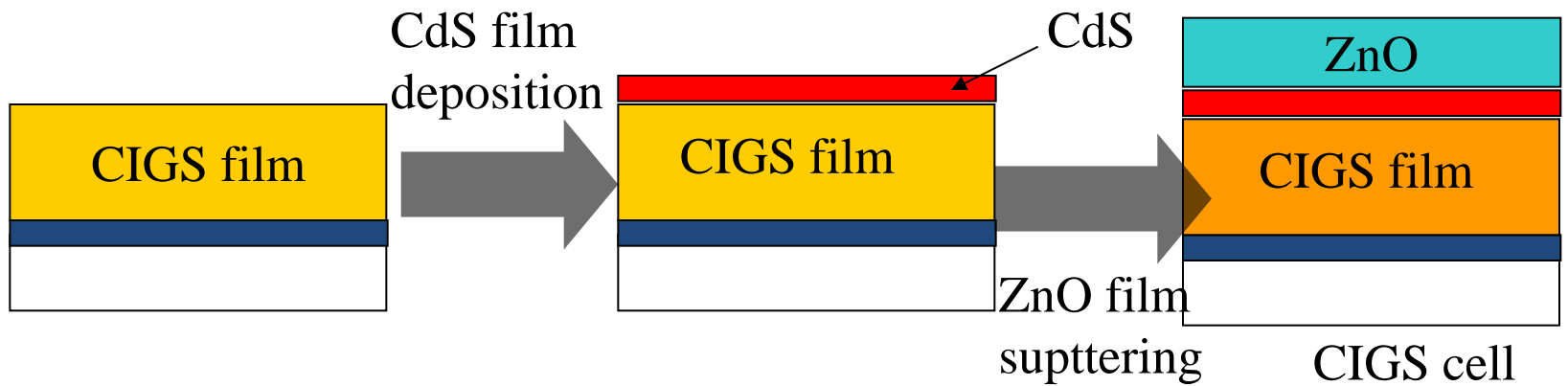
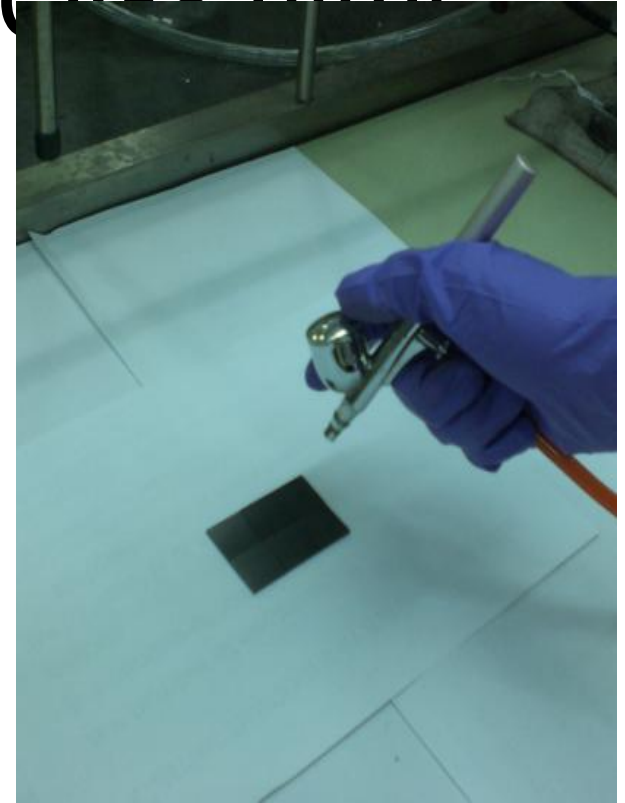
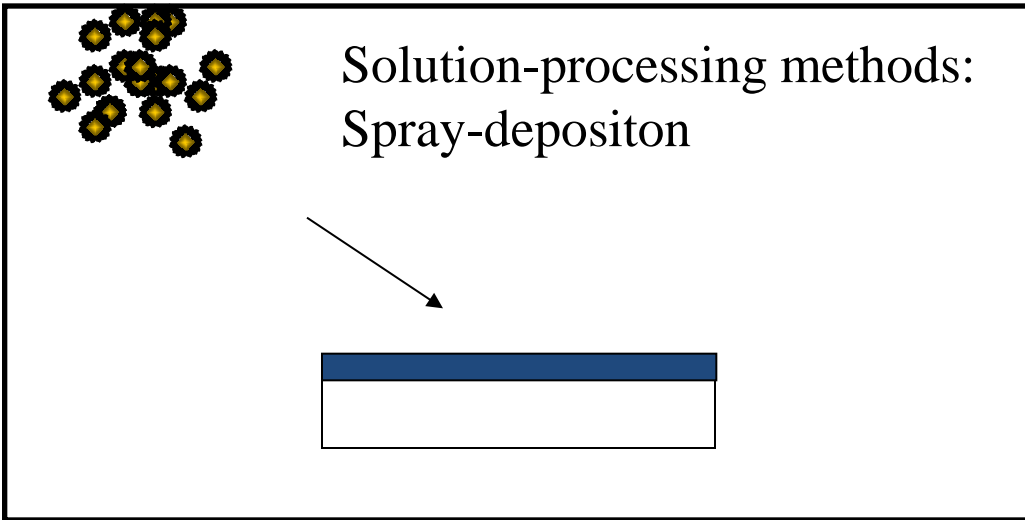


High-performance silicon nanowire transistor as a ultrasensitive biosensor



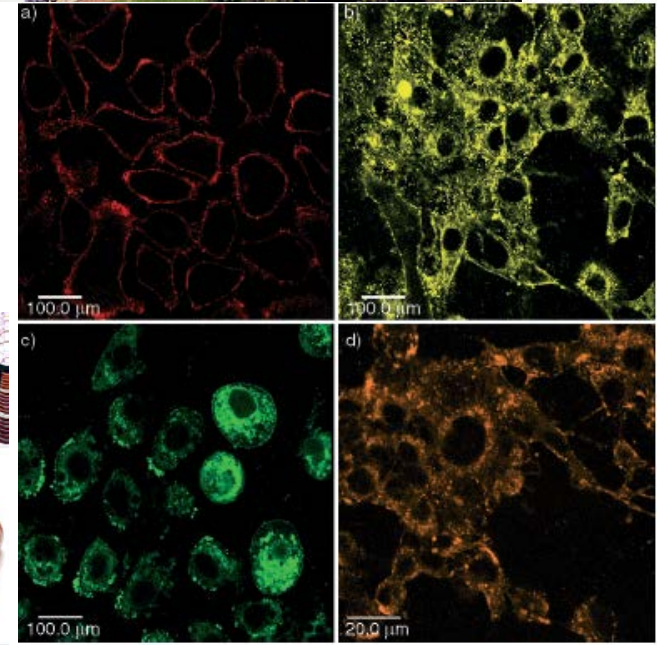
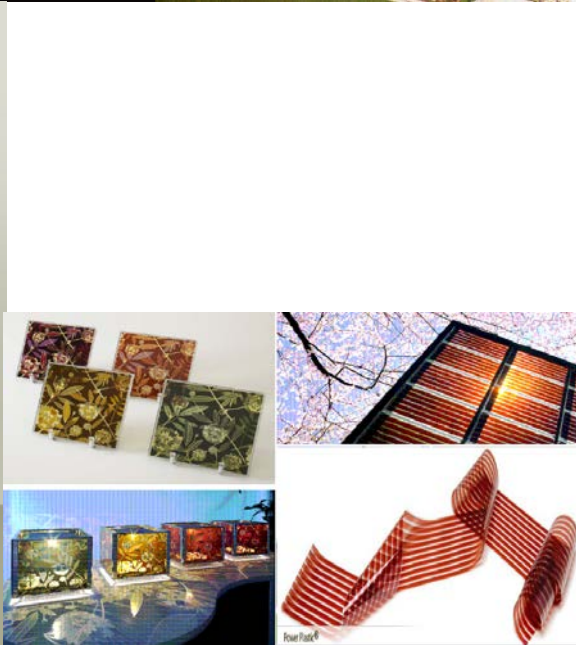
Javey et al., *Adv Mater.* 2009
 Tuan et al., *Angew Chemie.* 2005
 Whang et al., *Nano Lett.* 2003
 Whang et al., *Nano Lett.* 2003
 Andrew B et al., *App. Phys. Lett.*, 2005

Spray deposition of CIGS films

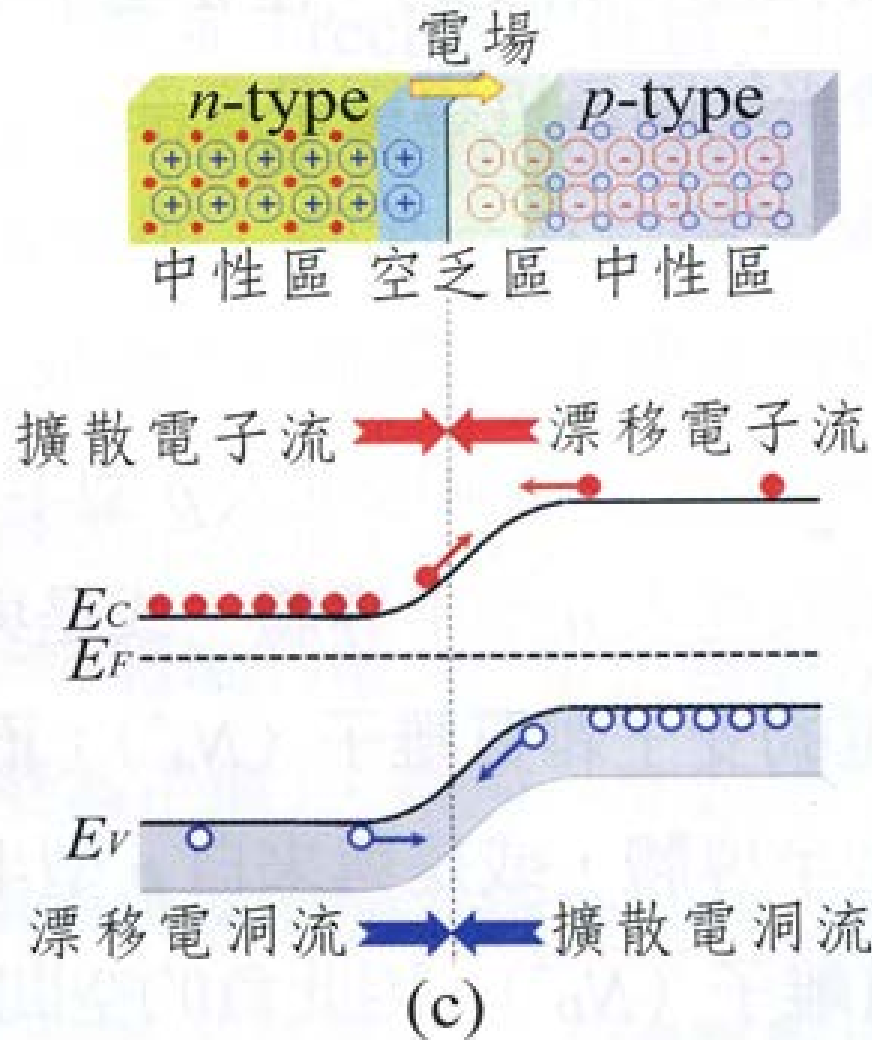


Nanomaterial Applications

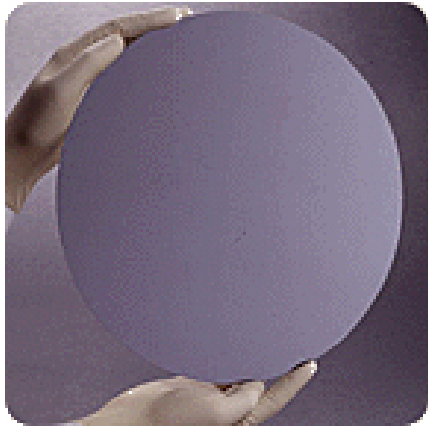
Bio+Energy+Environment, almost everything can be involved



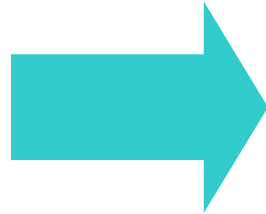
P-N junction : Frame structure for optoelectronic applications



Traditional Si-based semiconductor process

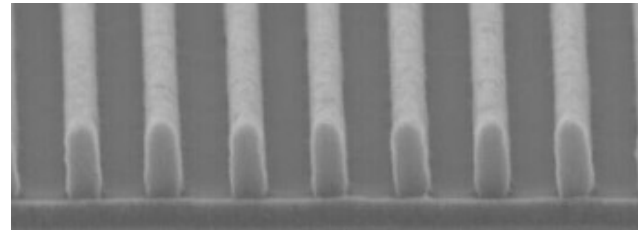


photolithography



"Top down" photolithography method

80nm



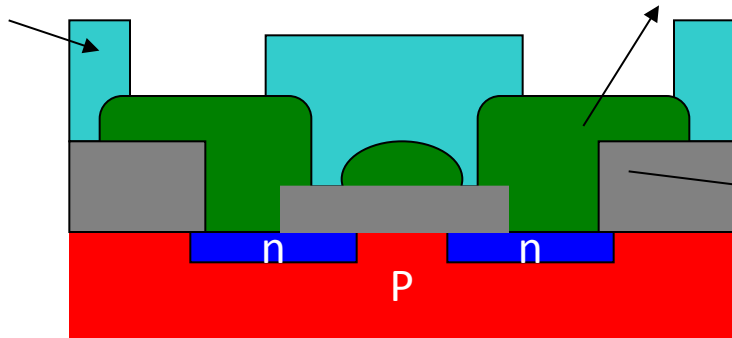
Patterning,
layering,
, heat treatment
, doping

Toward smaller size?

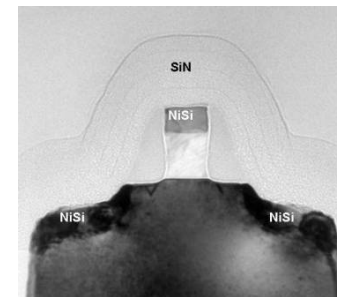
- the resolution limit of photolithography
- the extremely high cost of equipment

Passivation layer

metal layer

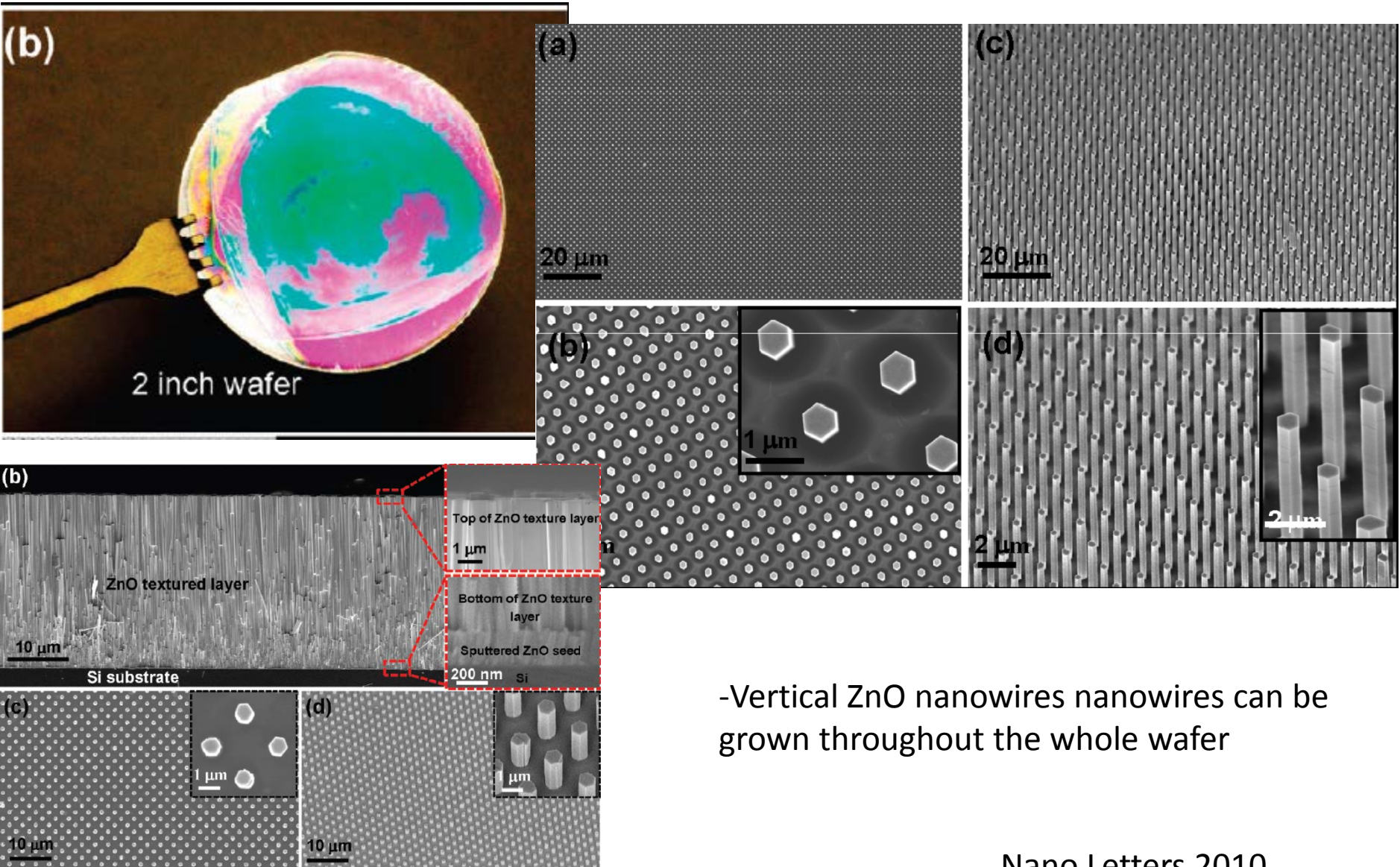


Oxide layer



Intel's 65nm nMOS transistor

Make Devices on Si wafer



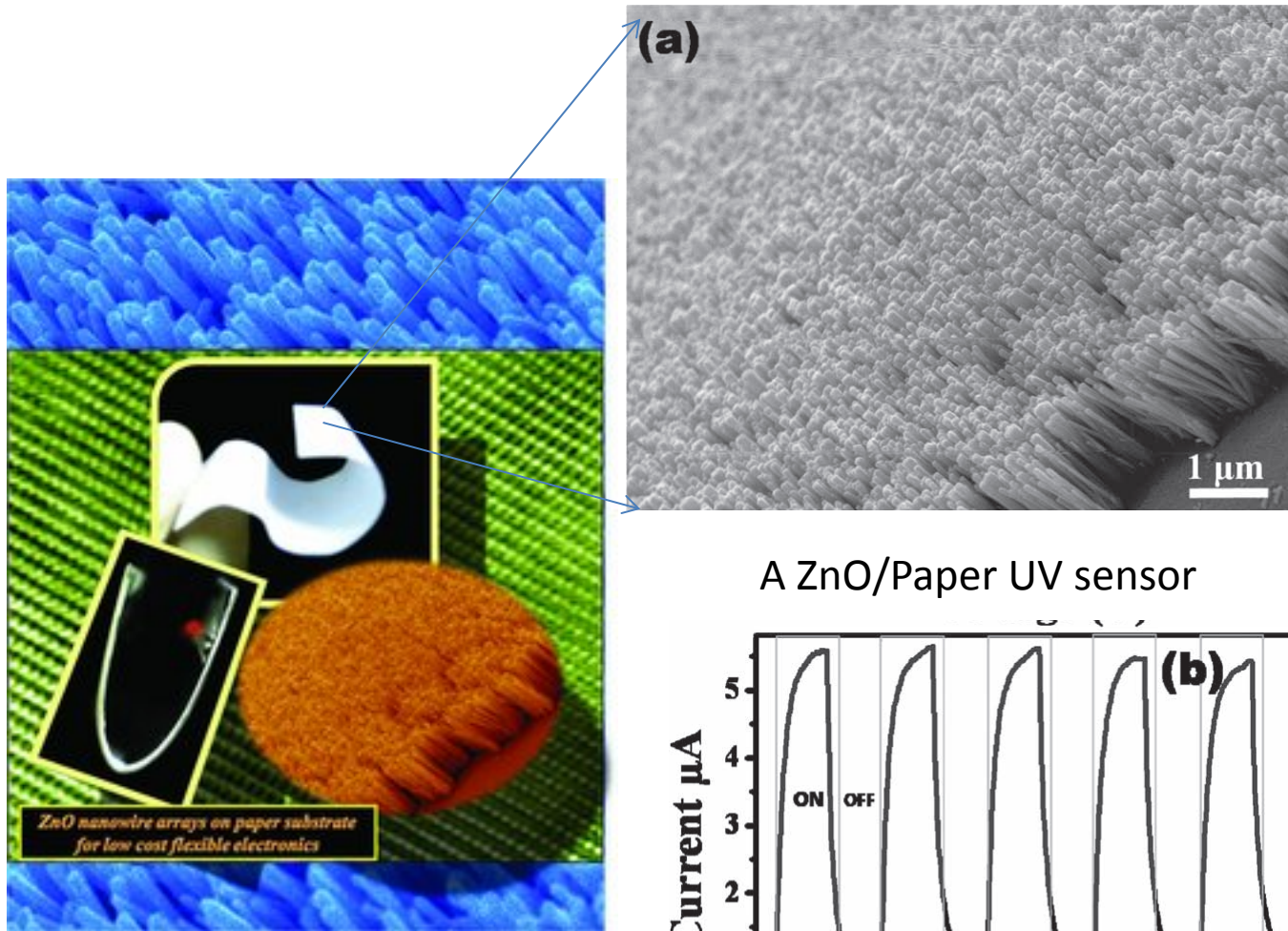
-Vertical ZnO nanowires nanowires can be grown throughout the whole wafer

Make devices on plastic

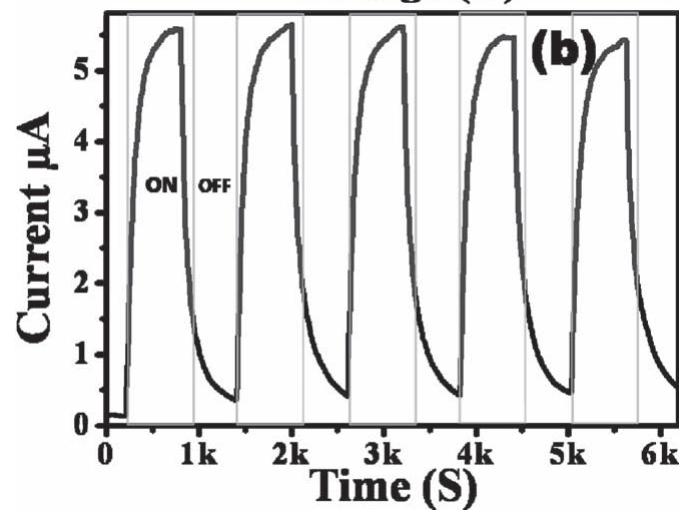


Figure 7. SEM images of the two-segment NW arrays a) on a ZnO substrate and b) after transferring on a flexible substrate. c) Bright-field optical image of the NW arrays on the flexible substrate. d) Low-magnification SEM image of the two-segment NW arrays on a flexible substrate. e) Current–voltage (I – V) curves of the as-transferred NW arrays in dark environment, under room light, and under UV illumination.

Make optoelectronic devices on paper

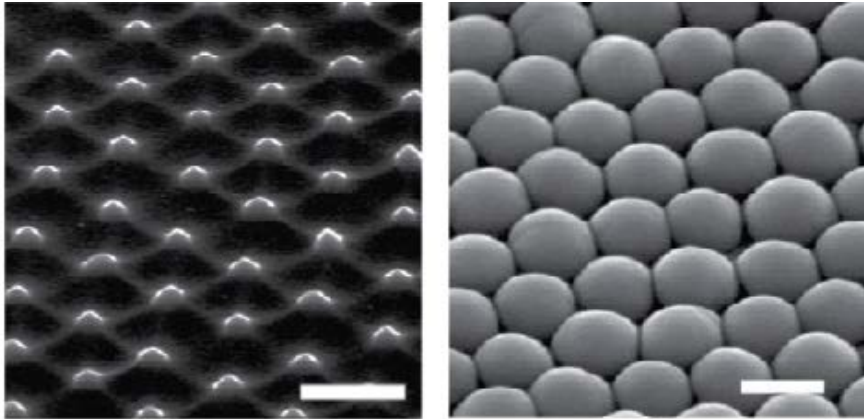


A ZnO/Paper UV sensor

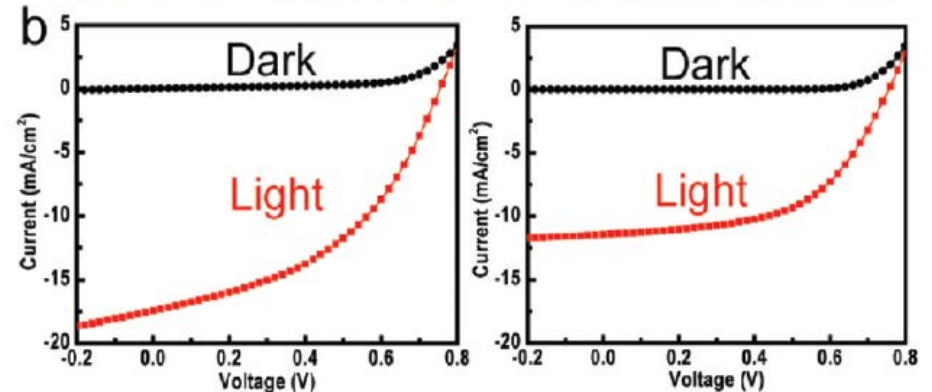
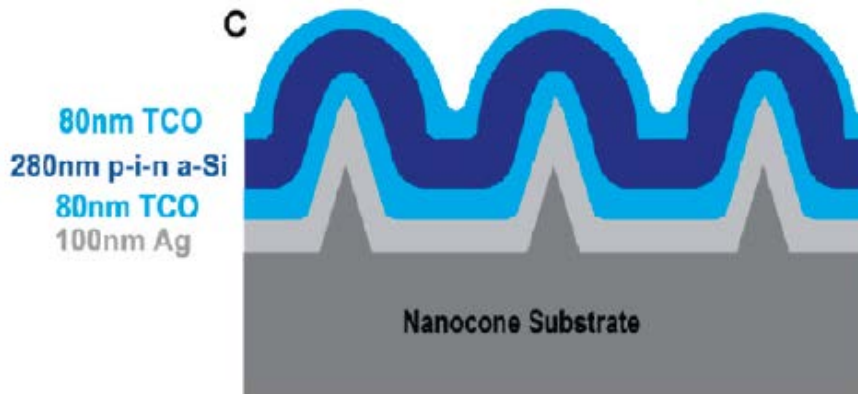


Nanodome solar cells

Dome-shaped surface can trap light efficiently

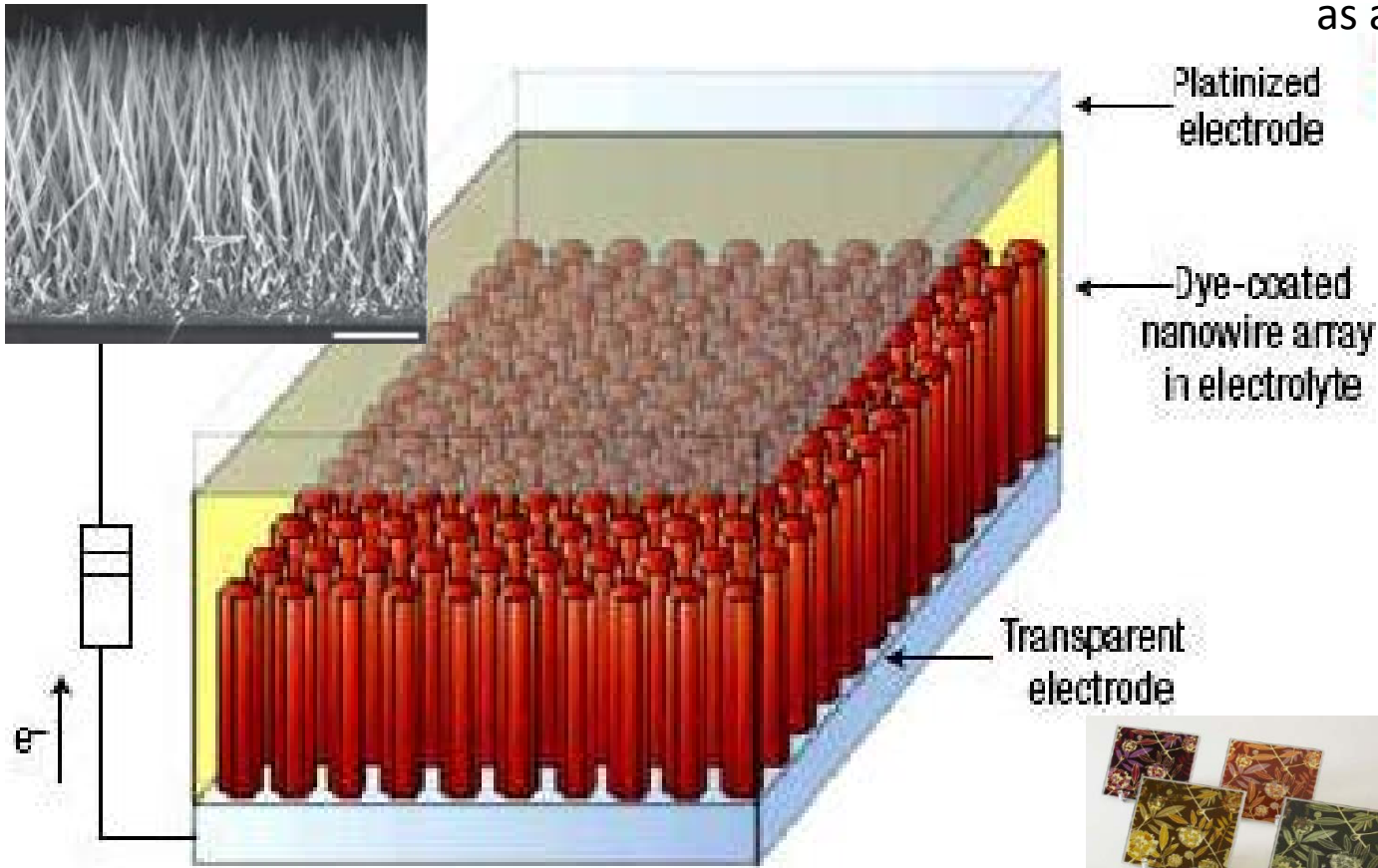


Much better light harvest!



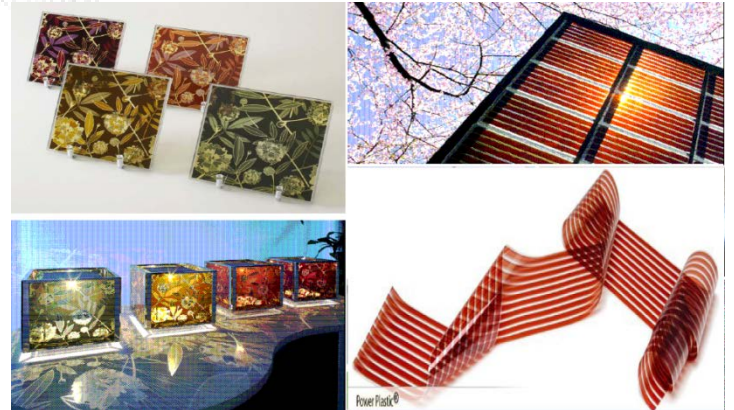
Dry-sensitized nanowire solar cell

Use ZnO nanowires
as a new photoelectrode

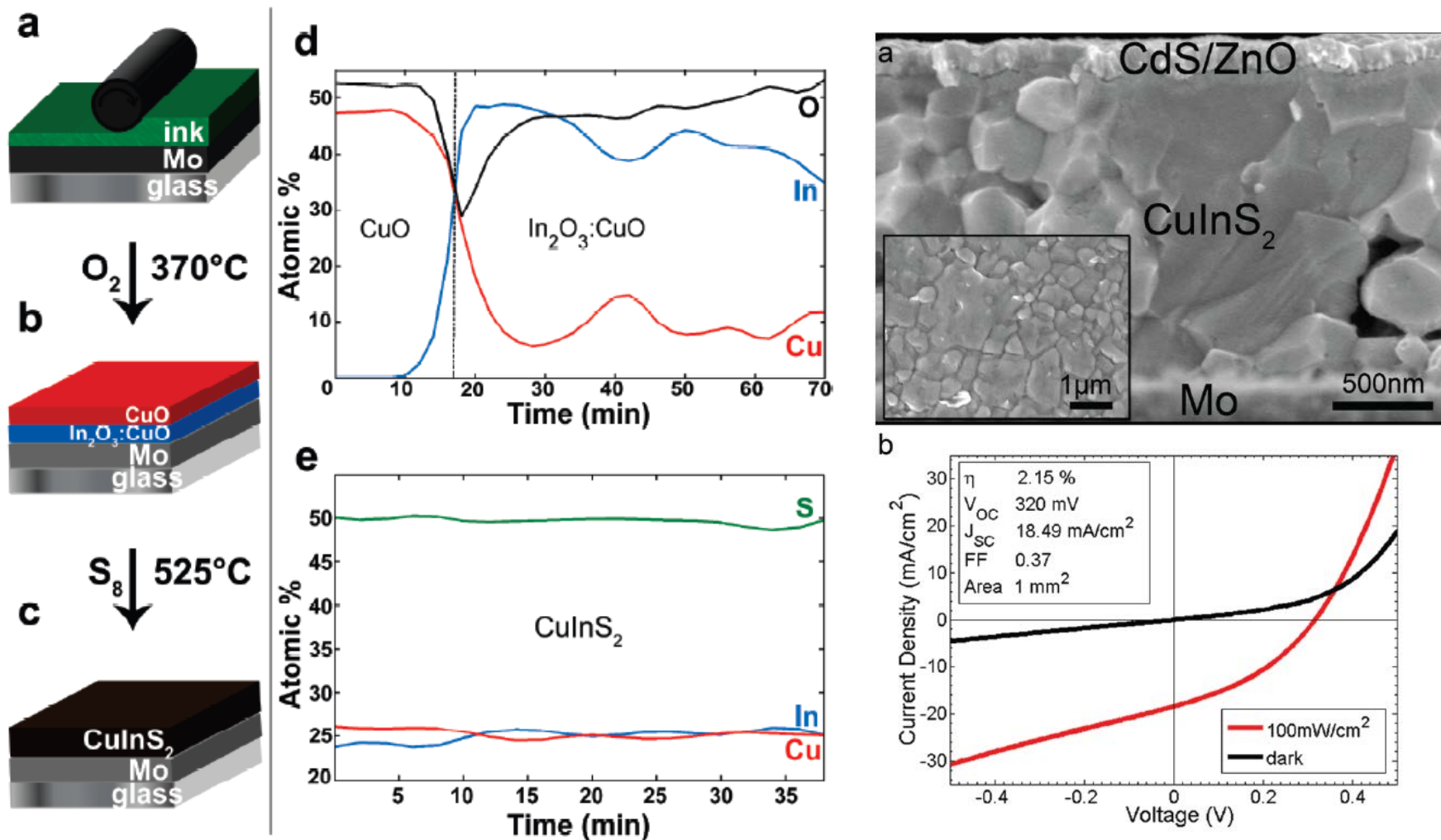


$\eta=1.2-1.5\%$

Yang et al., *Nature Materials*, 2005

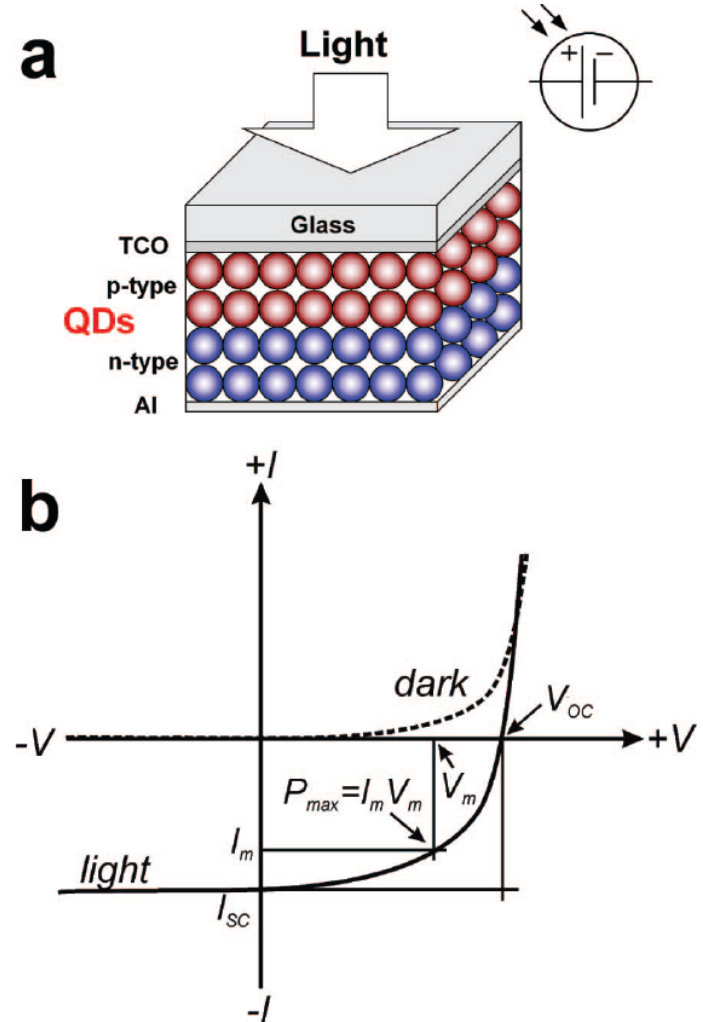
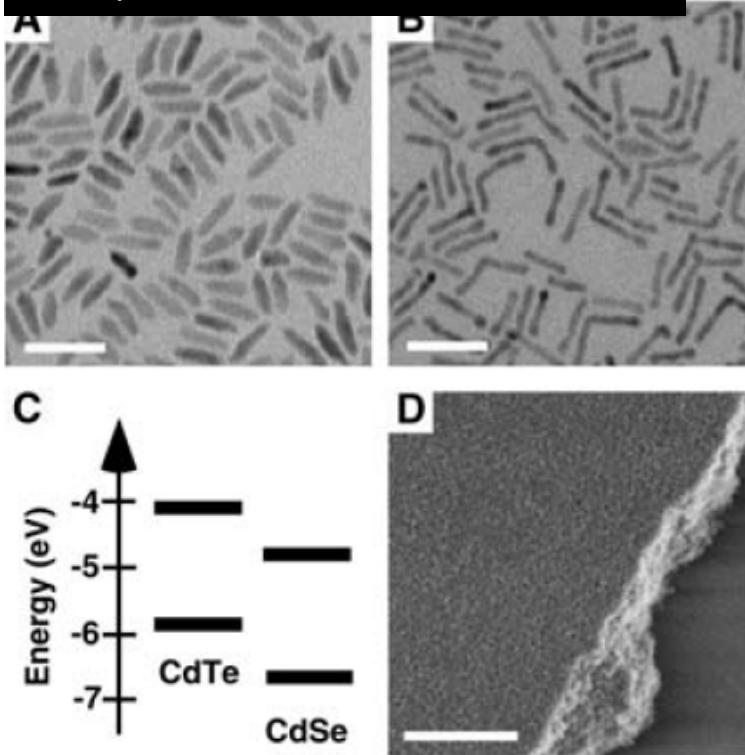


CuInS₂ Solar Cells by Air-Stable Rolling



Nanomaterial-based solar cell

CdTe/CdSe nanorod solar cell

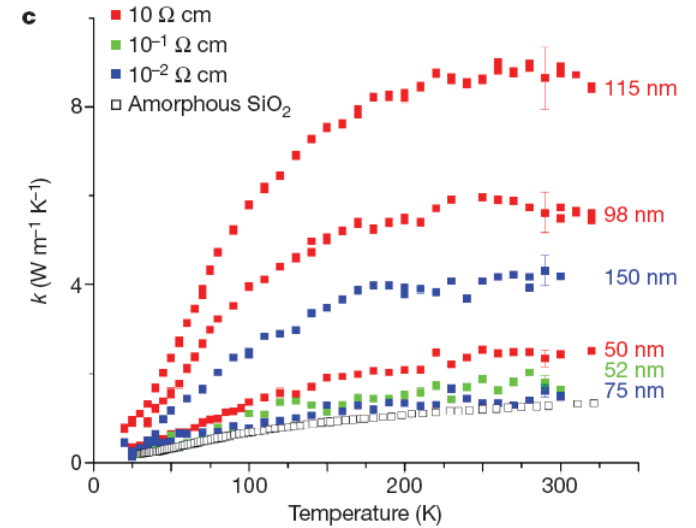
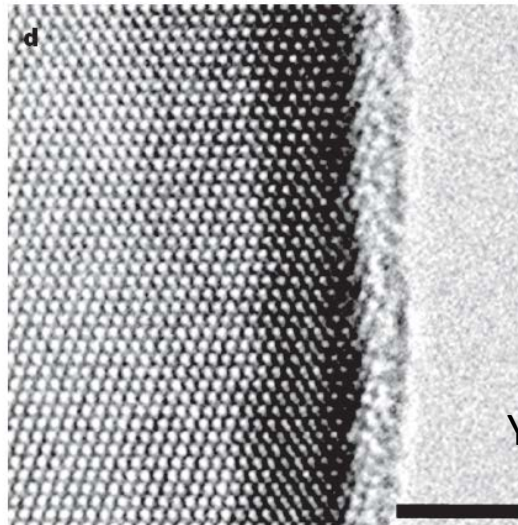
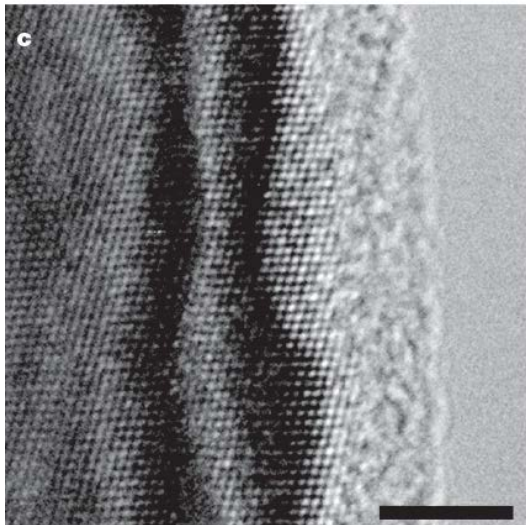
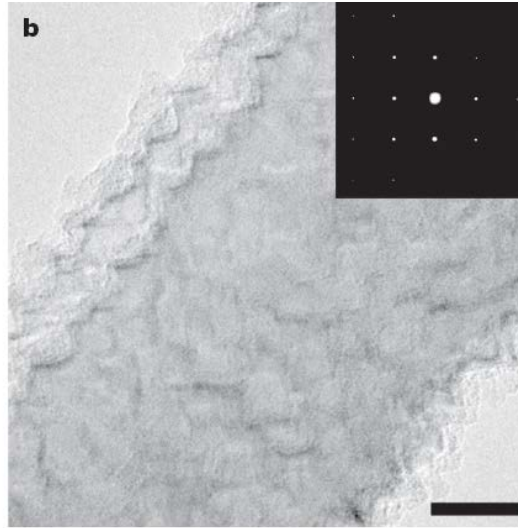
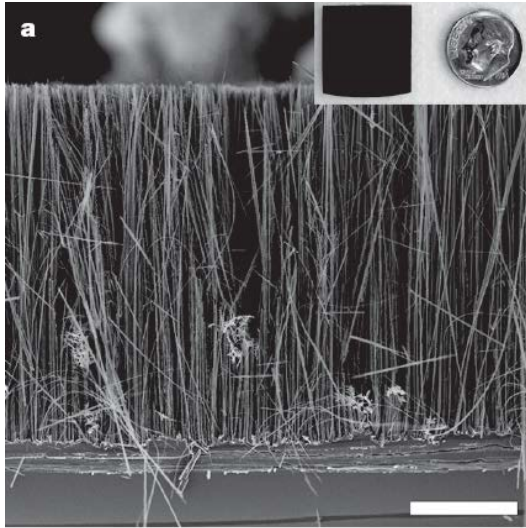


Alivisatos et al., Science, 2005

$\eta = 2.9\%$

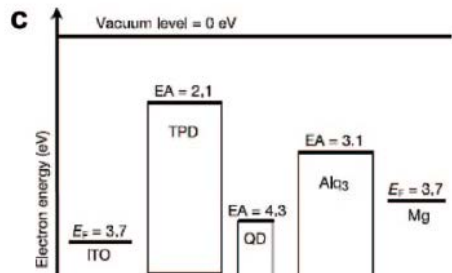
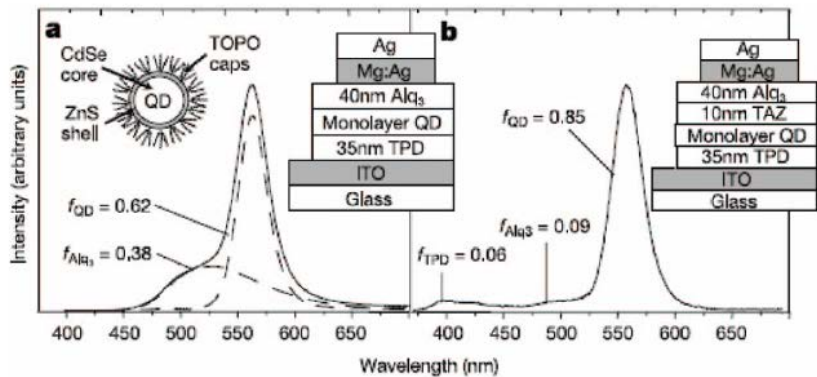
Si nanowire-based thermoelectrics

Transfer heat to energy

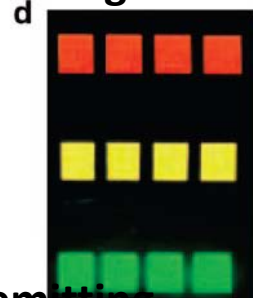


Yang et al., Nature, 2007

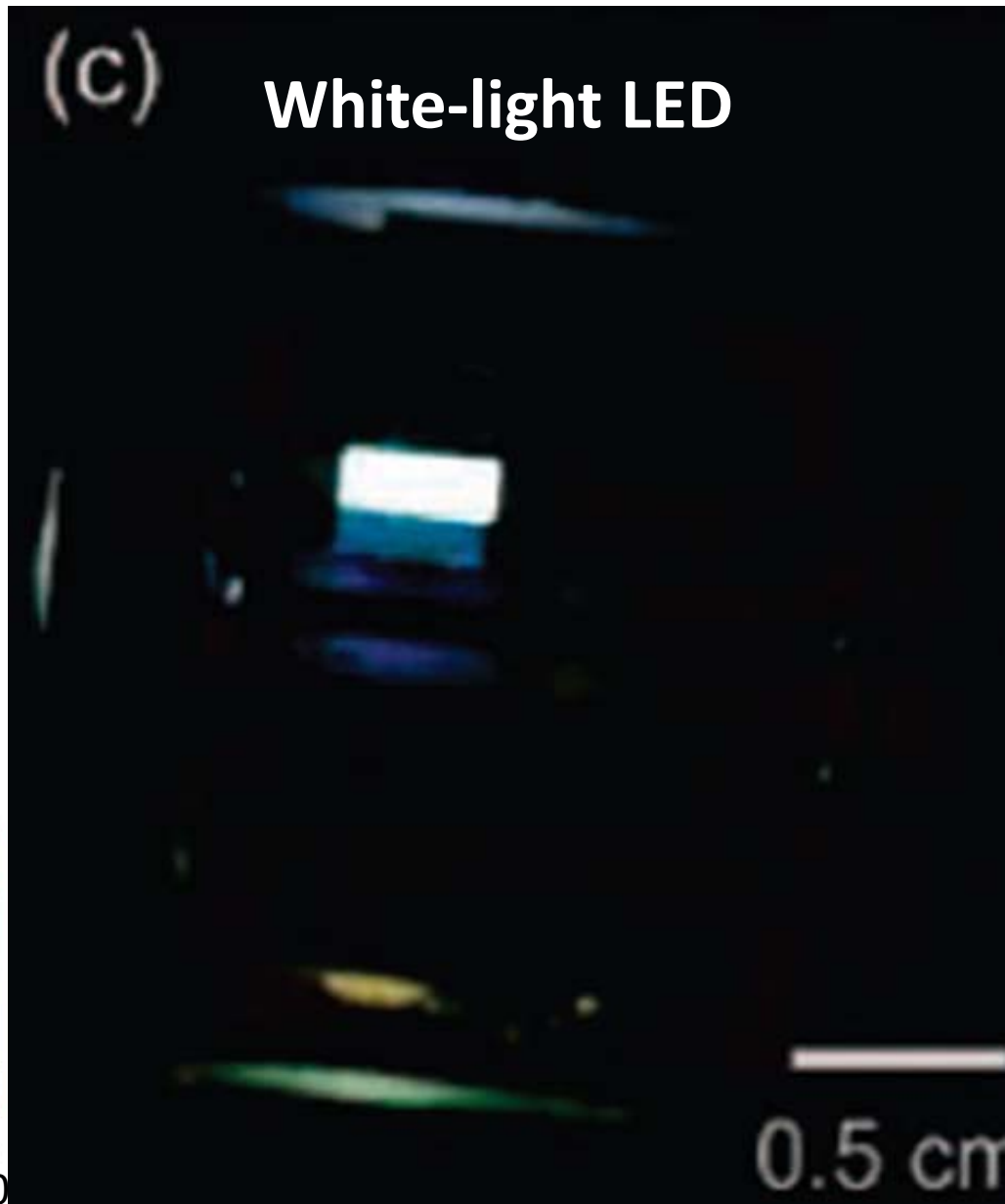
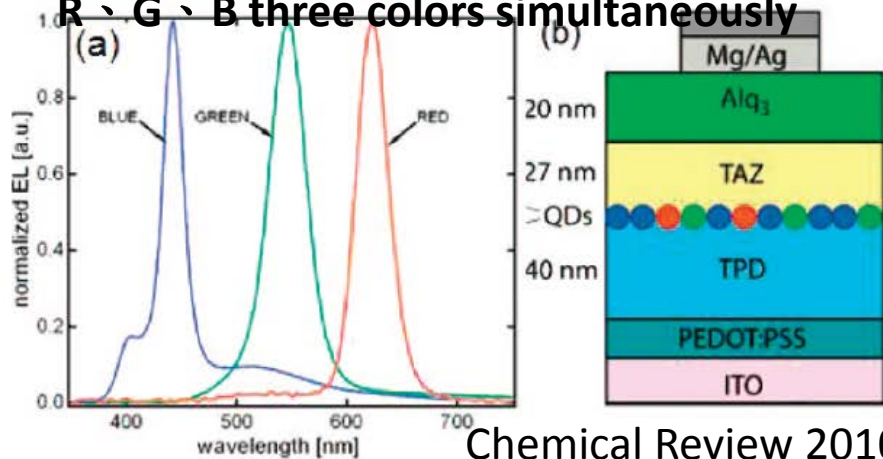
CdSe/ZnS nanocrystal LED



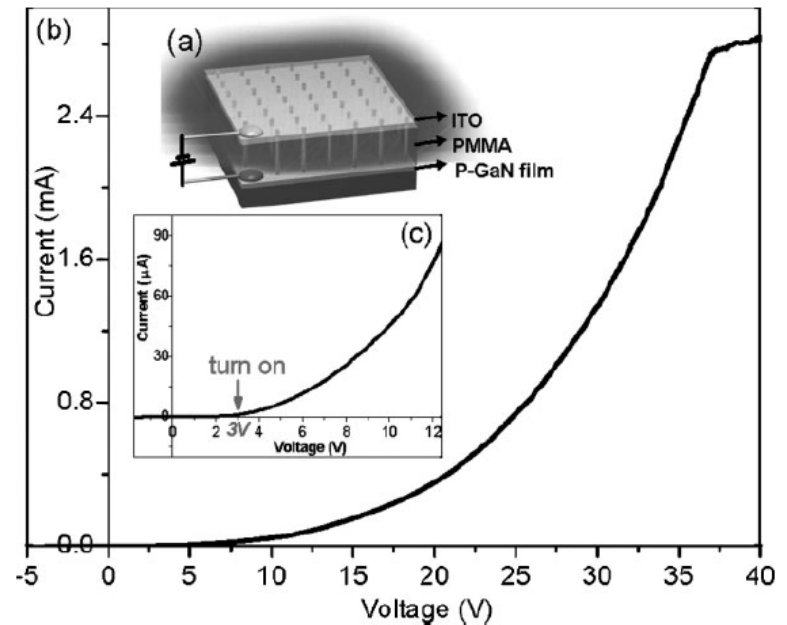
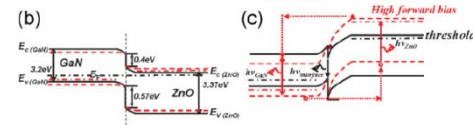
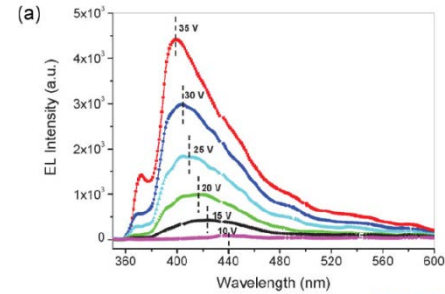
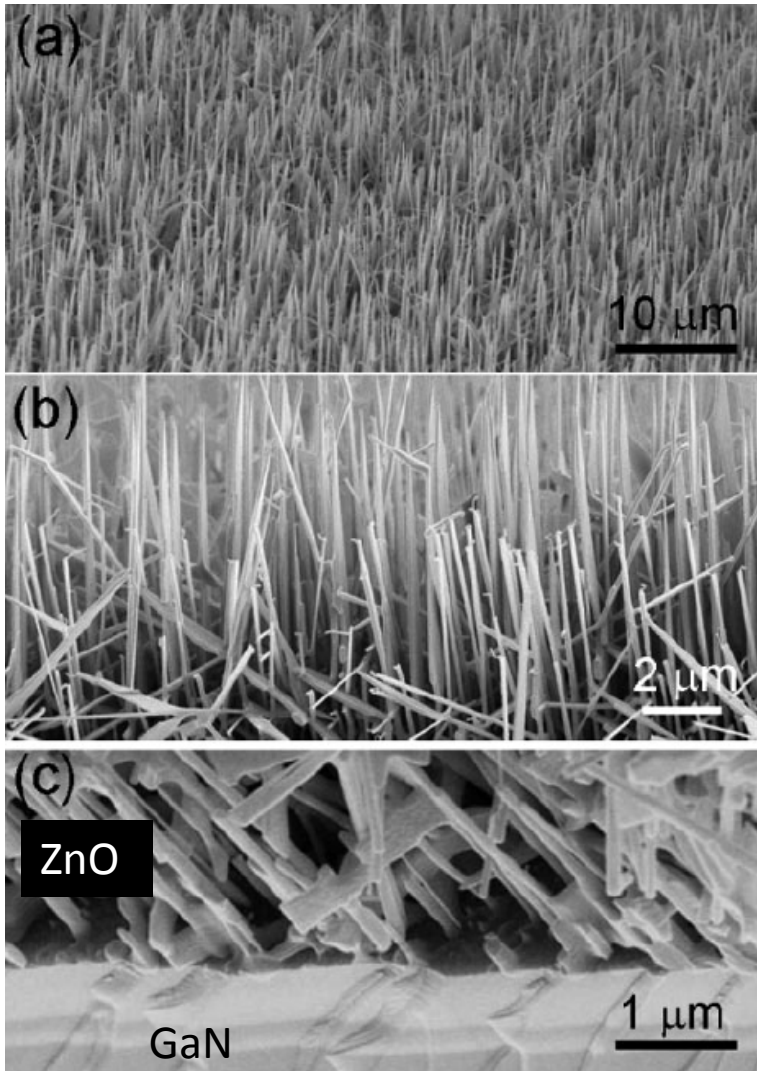
Single color



You can make a device emitting
R, G, B three colors simultaneously

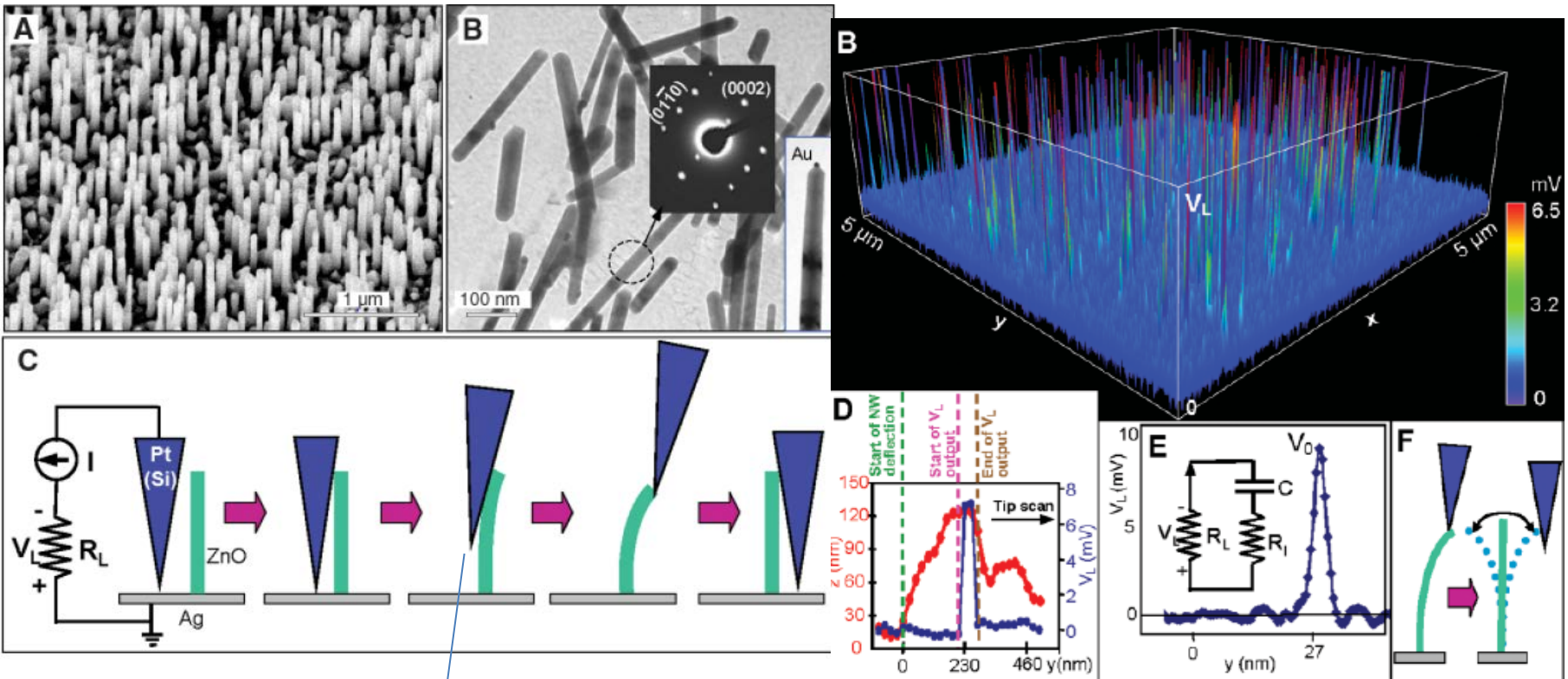


ZnO nanowire /GaN substrate LED



Zhang et al., Adv Mater., 2009

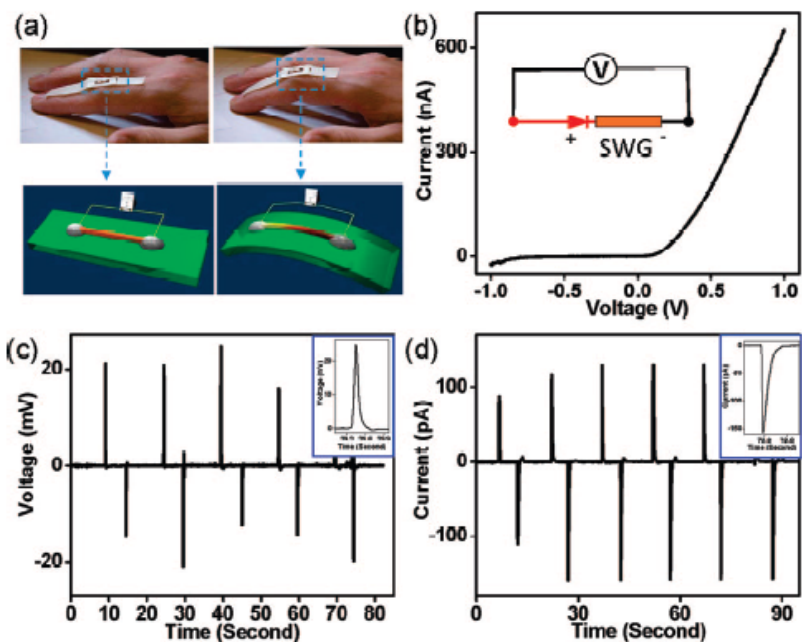
Piezoelectric nanogenerator



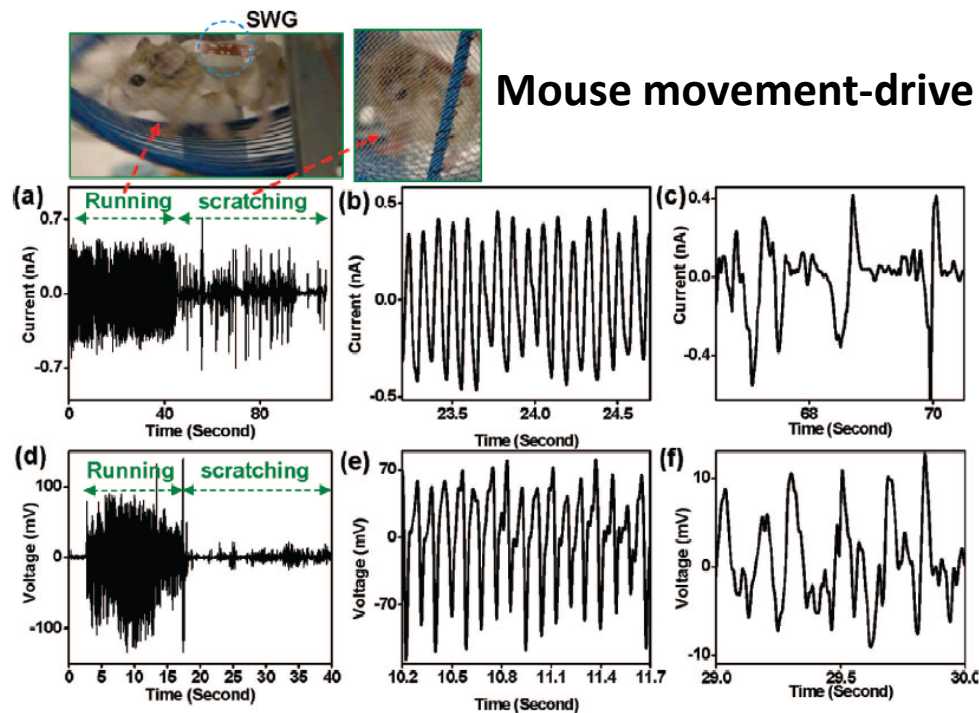
Transfer mechanical energy to electric energy

Muscle-Movement-Driven nanogenerator

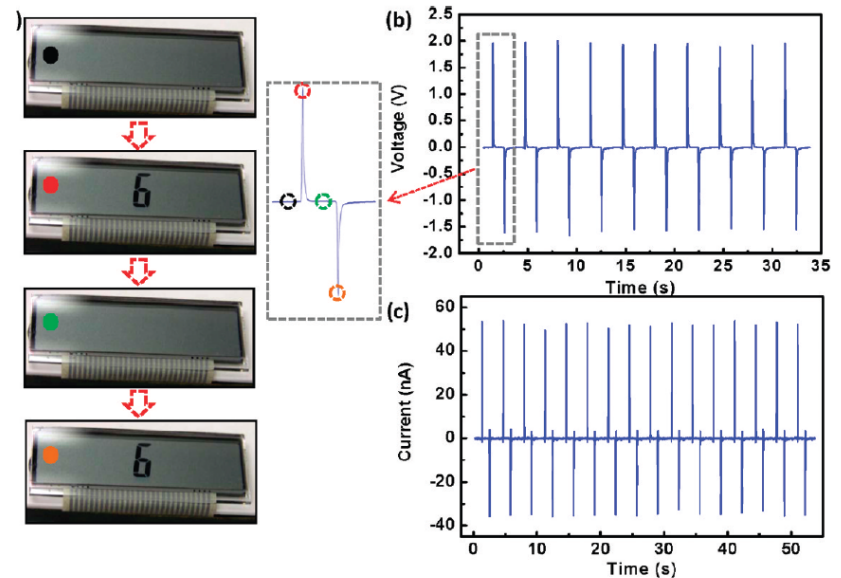
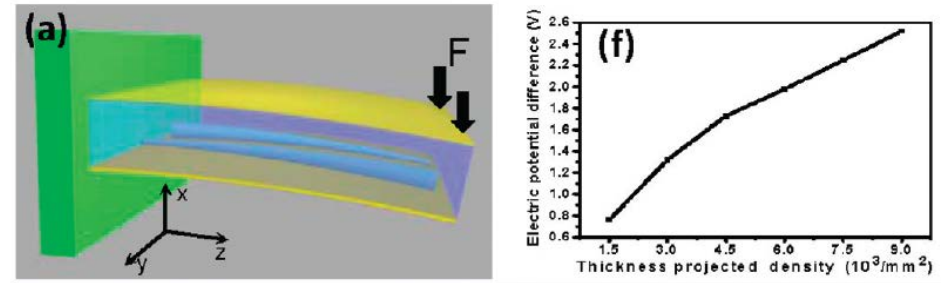
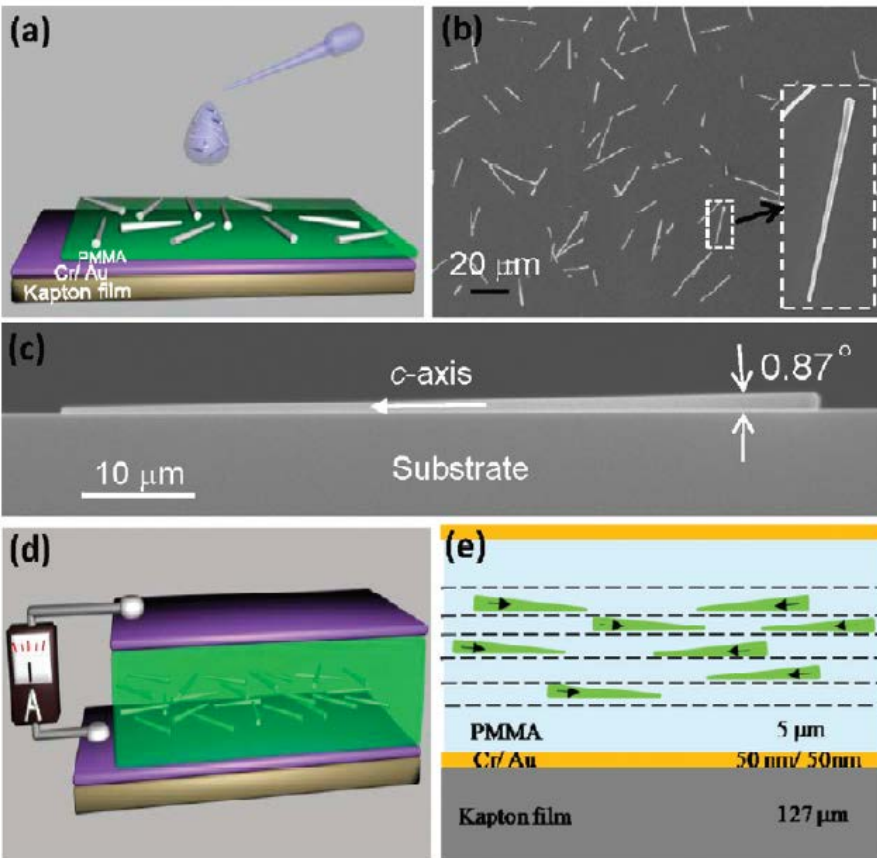
Finger movement-drive



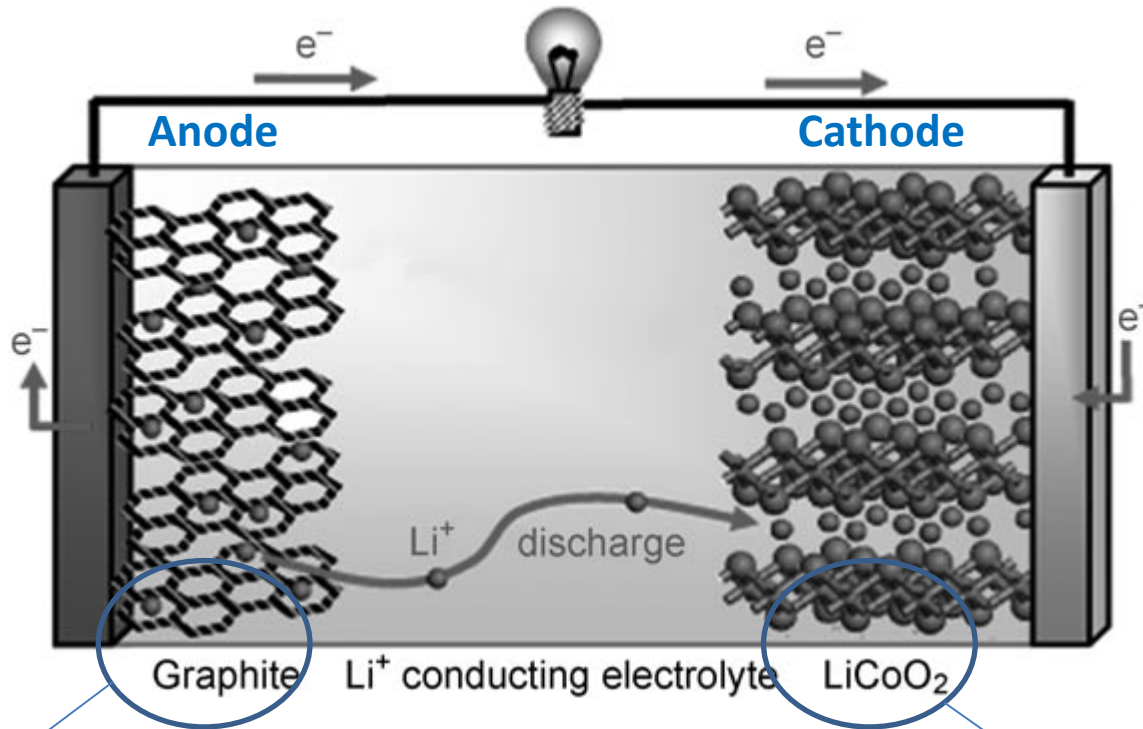
Mouse movement-drive



Nanogenerator for driving LCD display



New Electrodes for Lithium batteries



-Only ~ 375 Ahg⁻¹

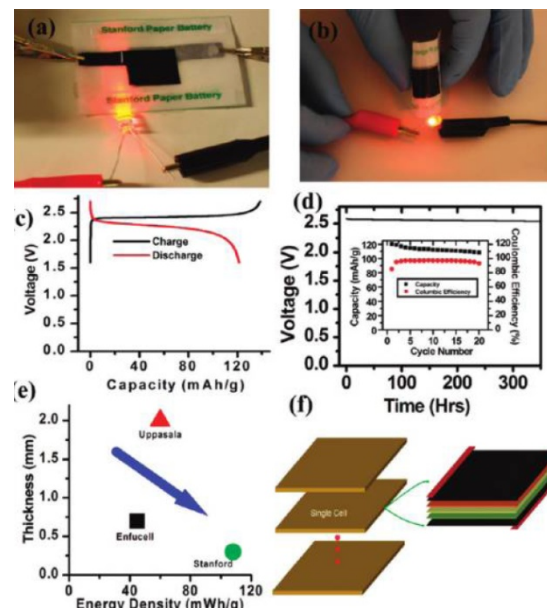
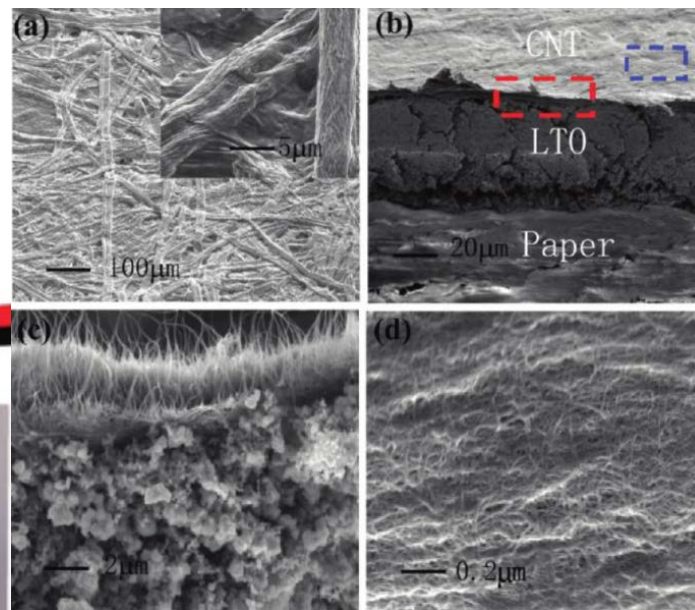
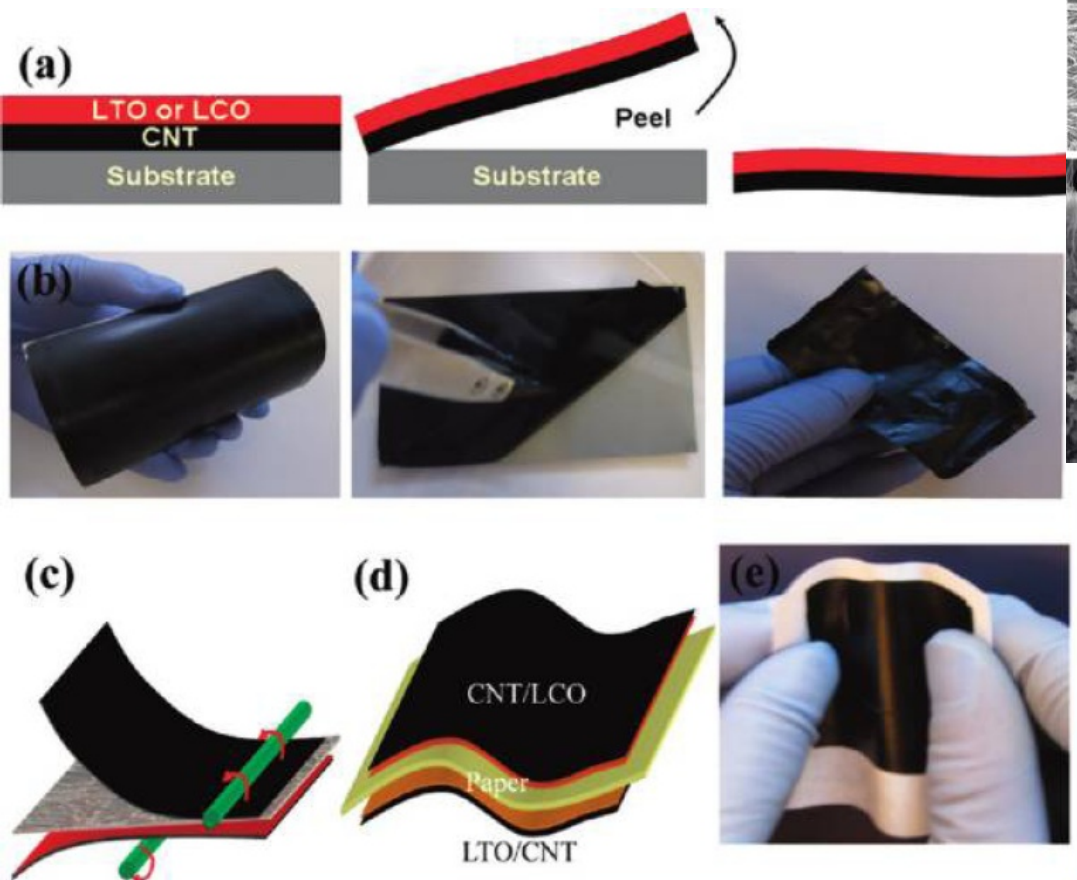
-Replaced by new material:

- Si (~4400、Ge~1600、SnO₂~782 Ahg⁻¹)

-New structure (mesoporous、branched)

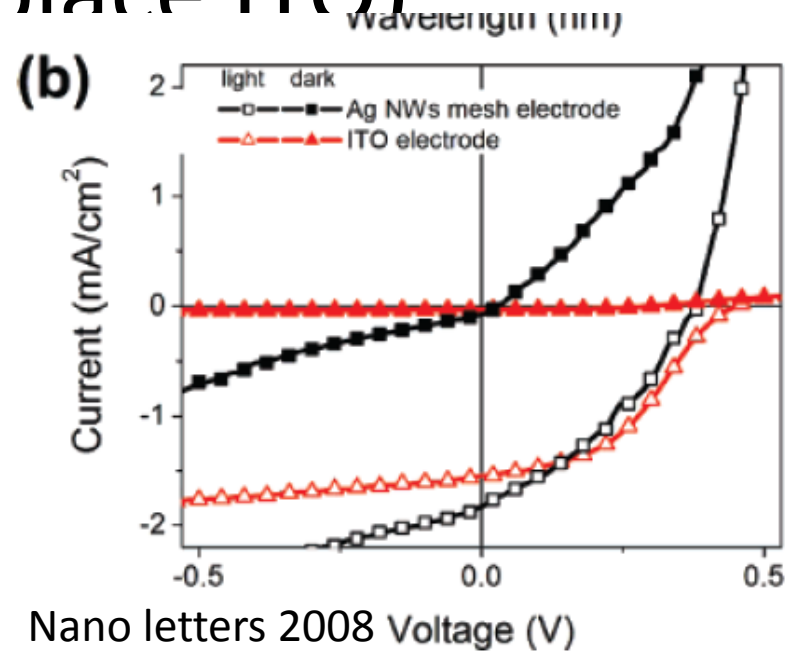
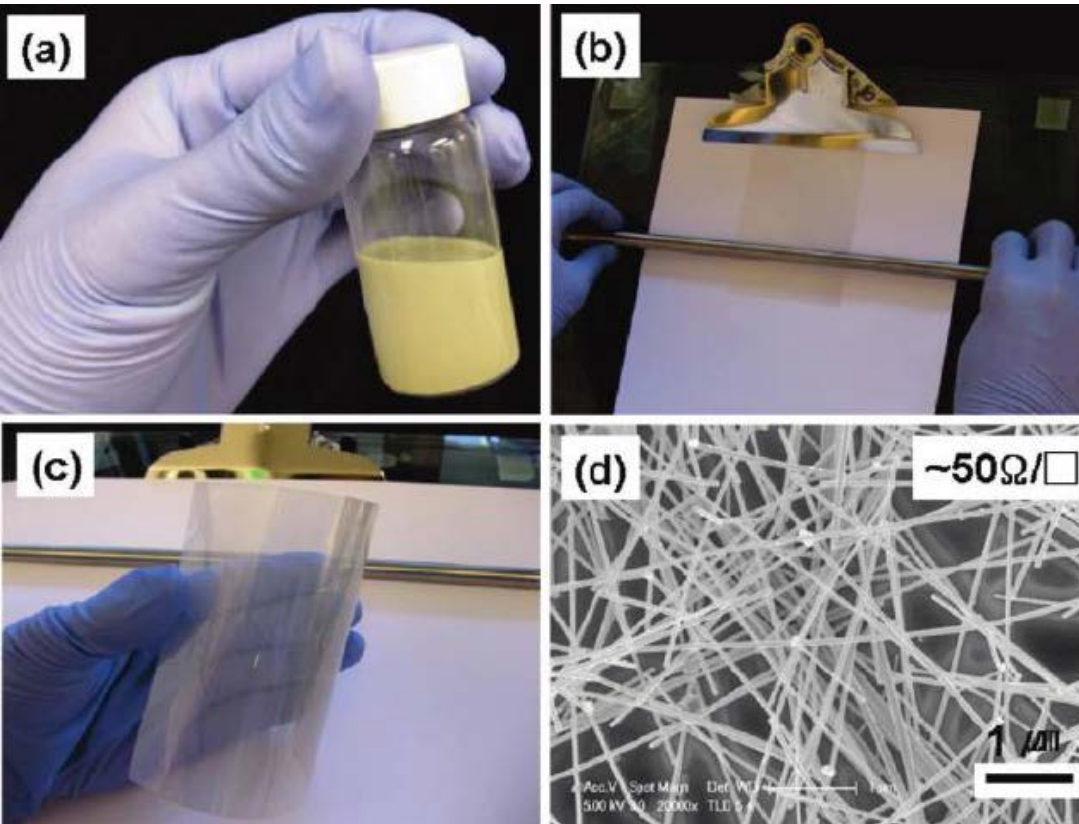
-New material (Li₂S : 1166 Ahg⁻¹)

Lithium ion Paper batteries

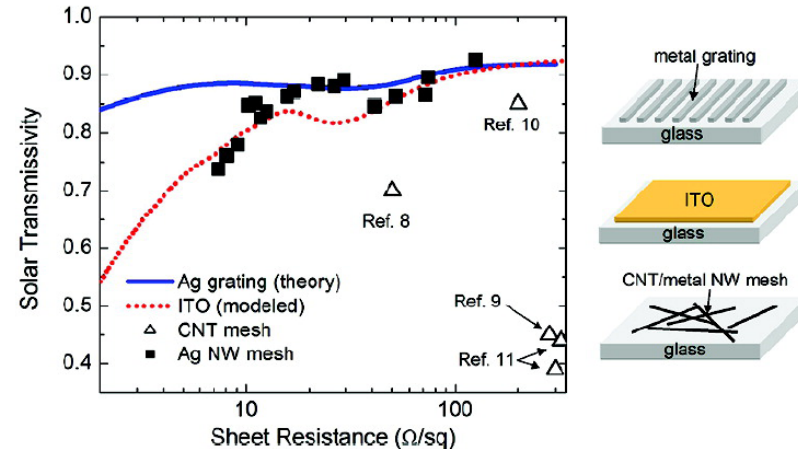


Silver nanowire transparent conducting glass or plastic (replace ITO)

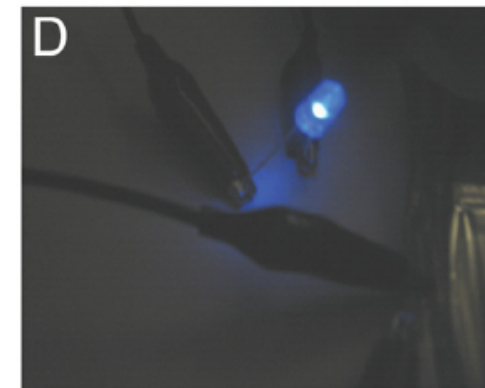
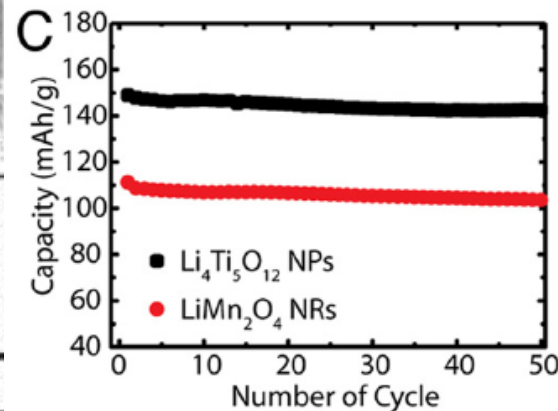
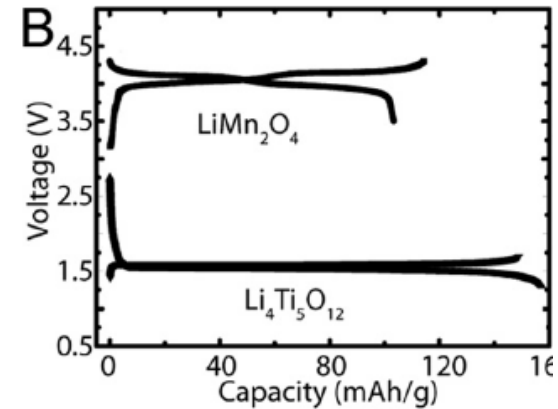
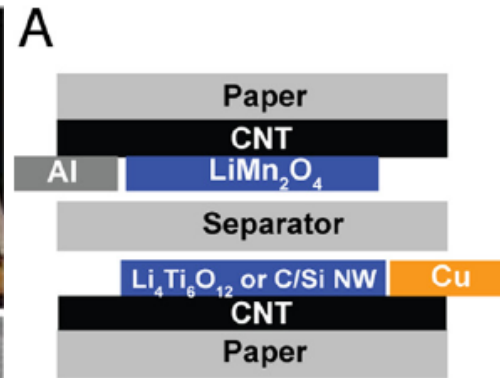
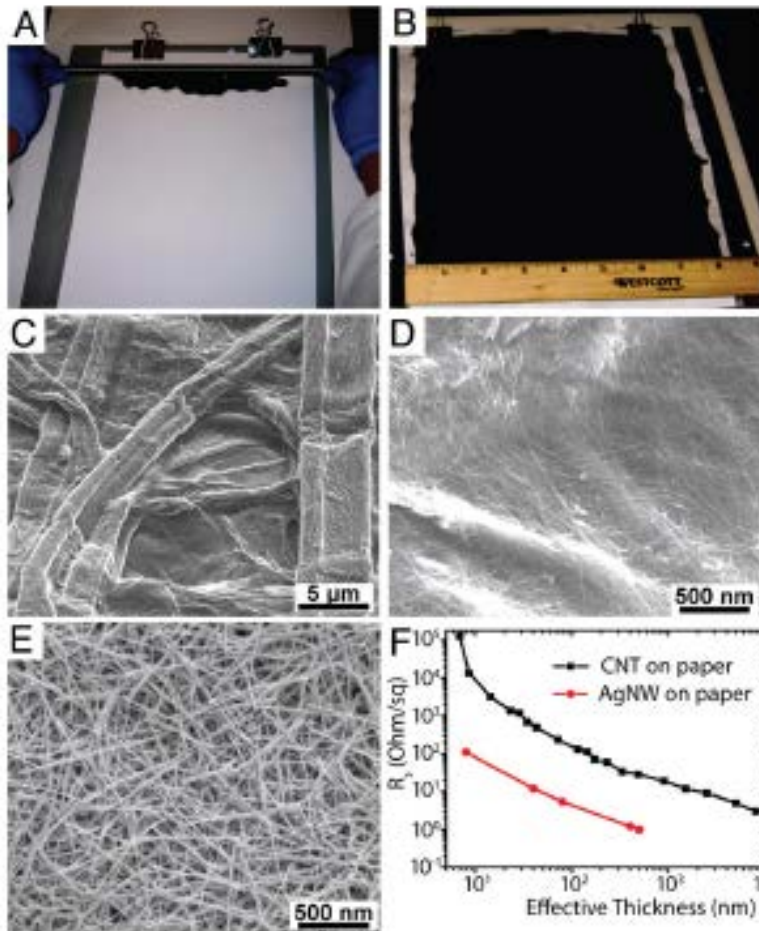
Coating Silver nanowires on a substrate to make it conductive



Nano letters 2008 Voltage (V)
ACS Nano 2010



Nanotubes + ink + paper = conducting paper



Highly conductive paper for energy-storage devices

Liangbing Hu^{a,1}, Jang Wook Choi^{a,1}, Yuan Yang^{a,1}, Sangmoo Jeong^b, Fabio La Mantia^a, Li-Feng Cui^a, and Yi Cui^{a,2}

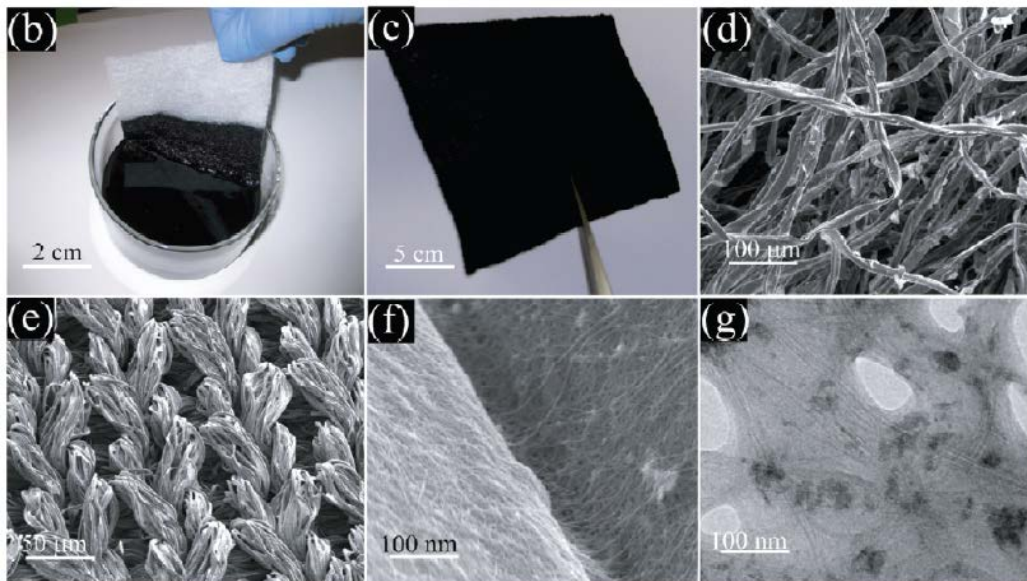
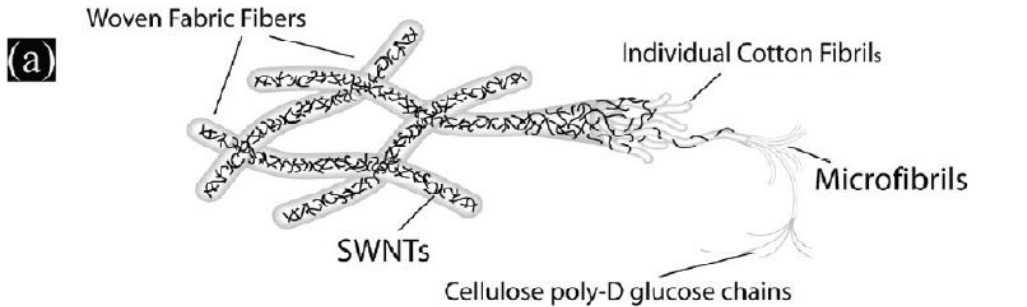
Departments of ^aMaterials Science and Engineering and ^bElectrical Engineering, Stanford University, Stanford, CA 94305

Edited by Charles M. Lieber, Harvard University, Cambridge, MA, and approved October 21, 2009 (received for review August 6, 2009)

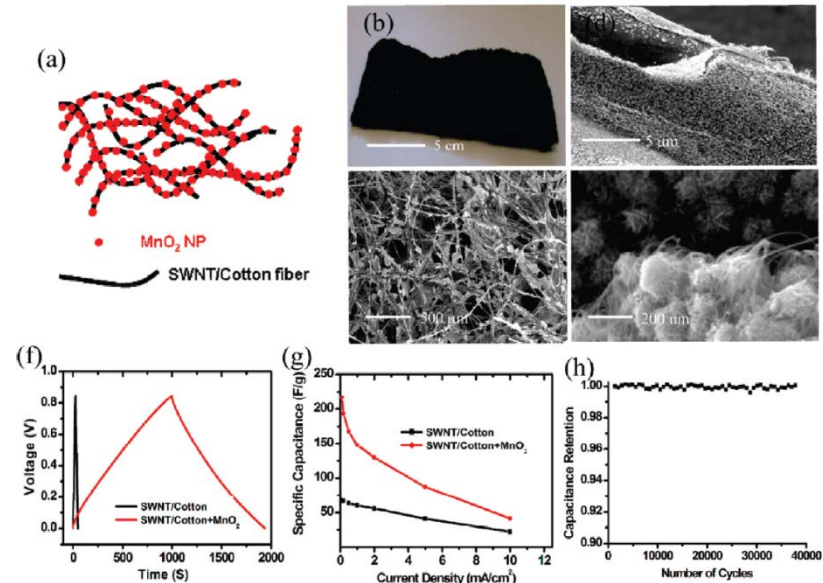
Paper invented more than 3,000 versions and widely used today... hierarchical porous fiber structures, surface charges, and fu

PNAS 2010

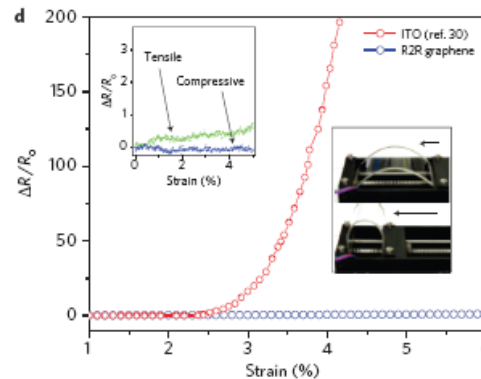
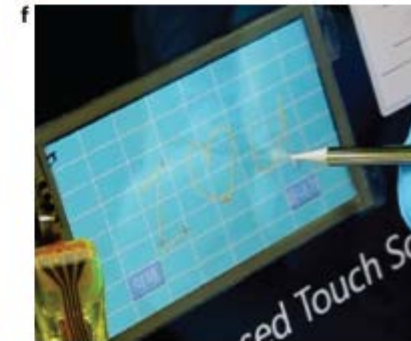
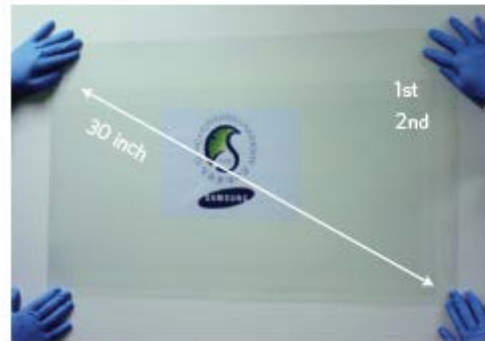
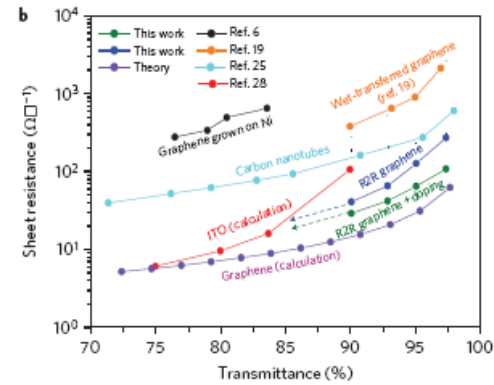
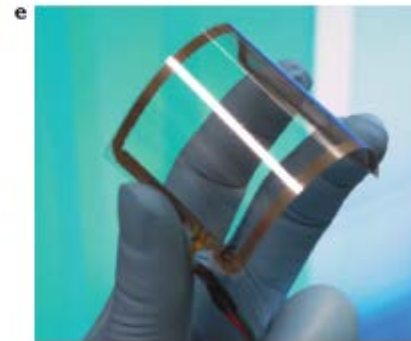
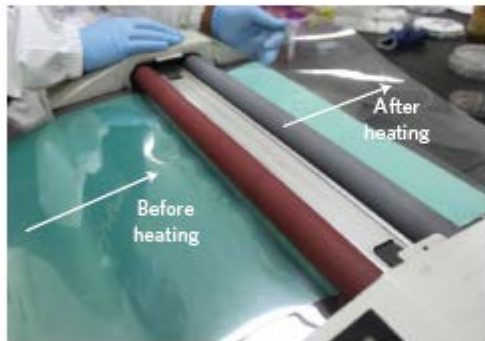
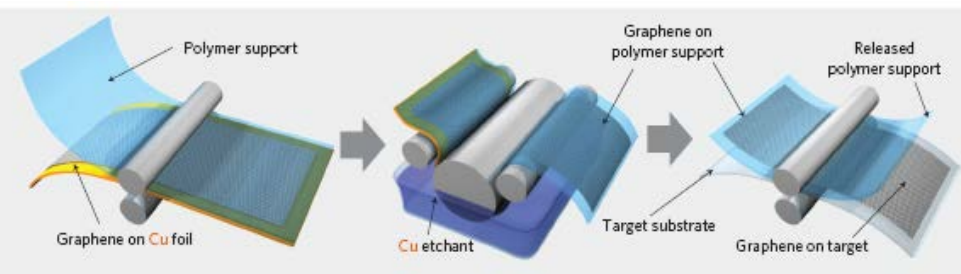
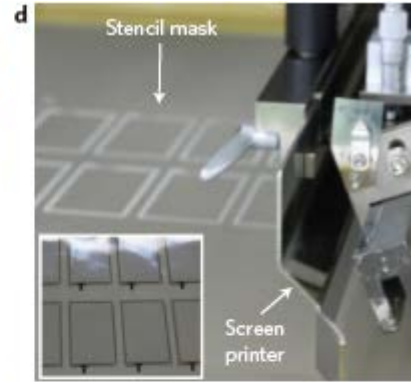
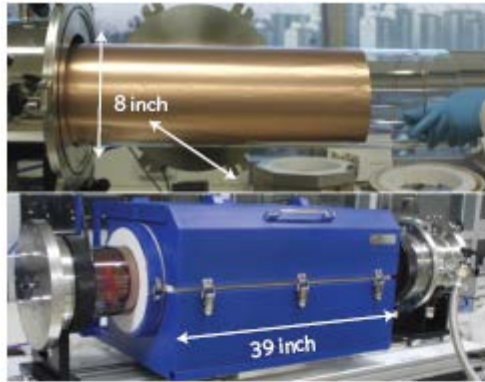
Stretchable, Porous, and Conductive Energy Textile



Textile capacitor



Roll-to-Roll production of 30-inch graphene films for transparent electrodes



Resistance
Not affected
under
strain

Nanostructures as high-performance anodes for Lithium-ion battery

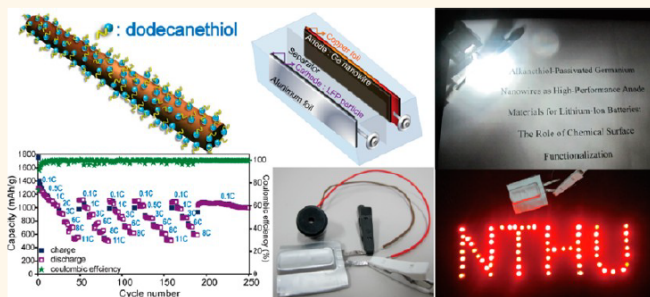
Alkanethiol-Passivated Ge Nanowires as High-Performance Anode Materials for Lithium-Ion Batteries: The Role of Chemical Surface Functionalization

Fang-Wei Yuan, Hong-Jie Yang, and Hsing-Yu Tuan*

Department of Chemical Engineering, National Tsing Hua University, 101, Section 2, Kuang-Fu Road, Hsinchu, Taiwan 30013, ROC

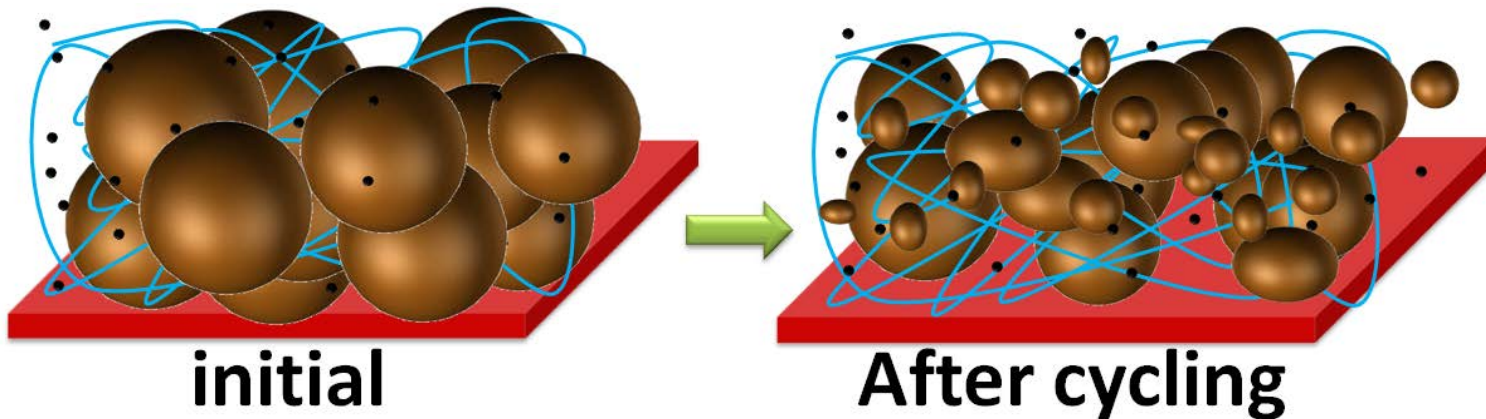
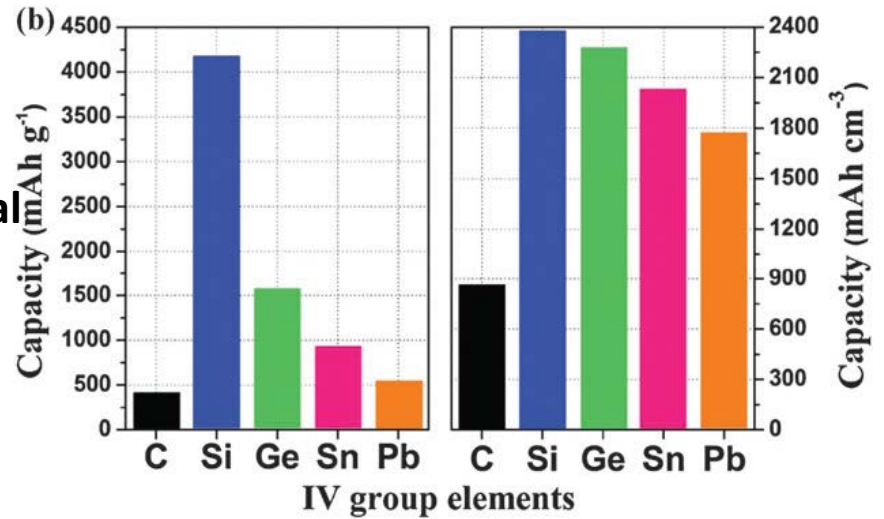
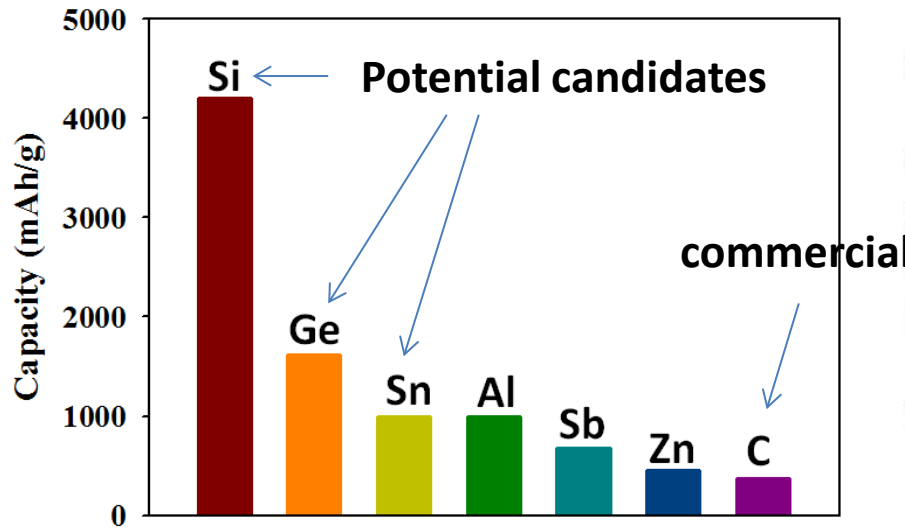
段興宇
清大化工系

ABSTRACT We demonstrate that dodecanethiol monolayer passivation can significantly enhance the anode performance of germanium (Ge) nanowires in lithium-ion batteries. The dodecanethiol-passivated Ge nanowires exhibit an excellent electrochemical performance with a reversible specific capacity of 1130 mAh/g at 0.1 C rate after 100 cycles. The functionalized Ge nanowires show high-rate capability having charge and discharge capacities of ~ 555 mAh/g at high rates of 11 C. The functionalized Ge nanowires also

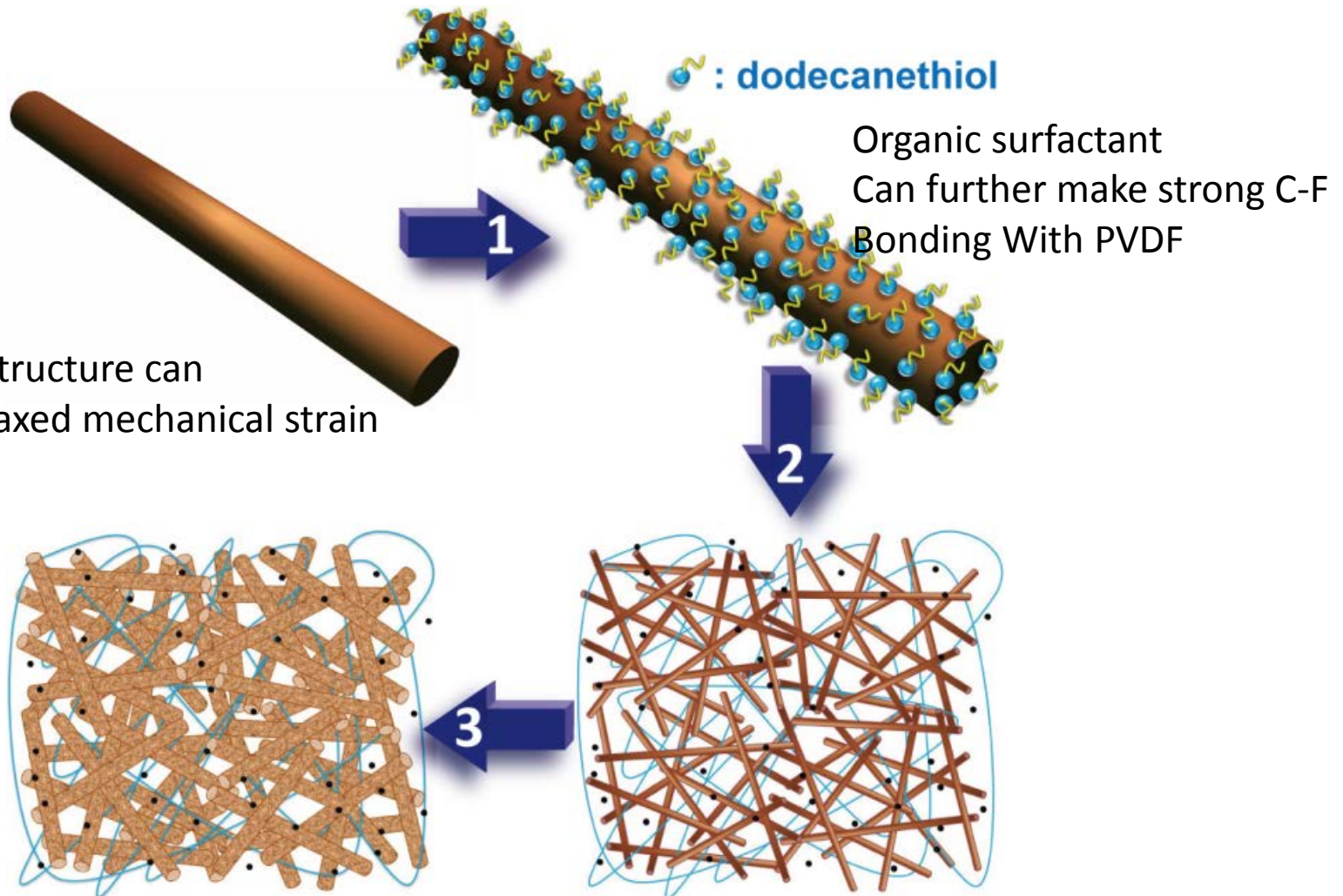


Tuan et al. ACS Nano, in press

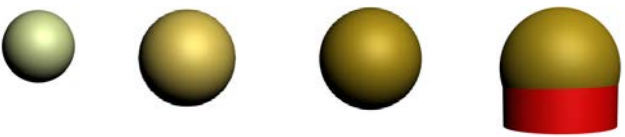
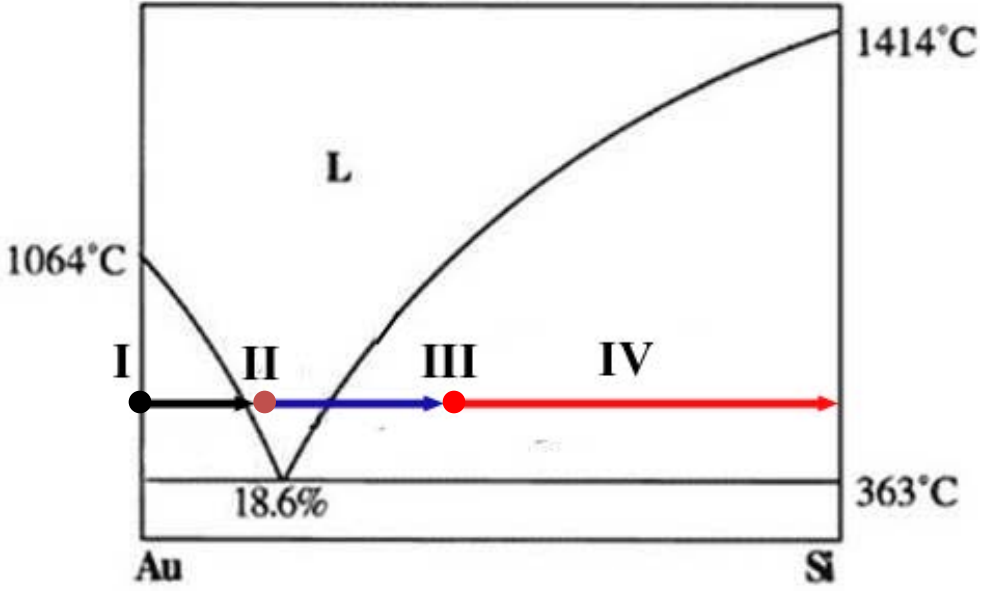
Alloying material for Lithium-ion anode



Using Ge nanowires as anode

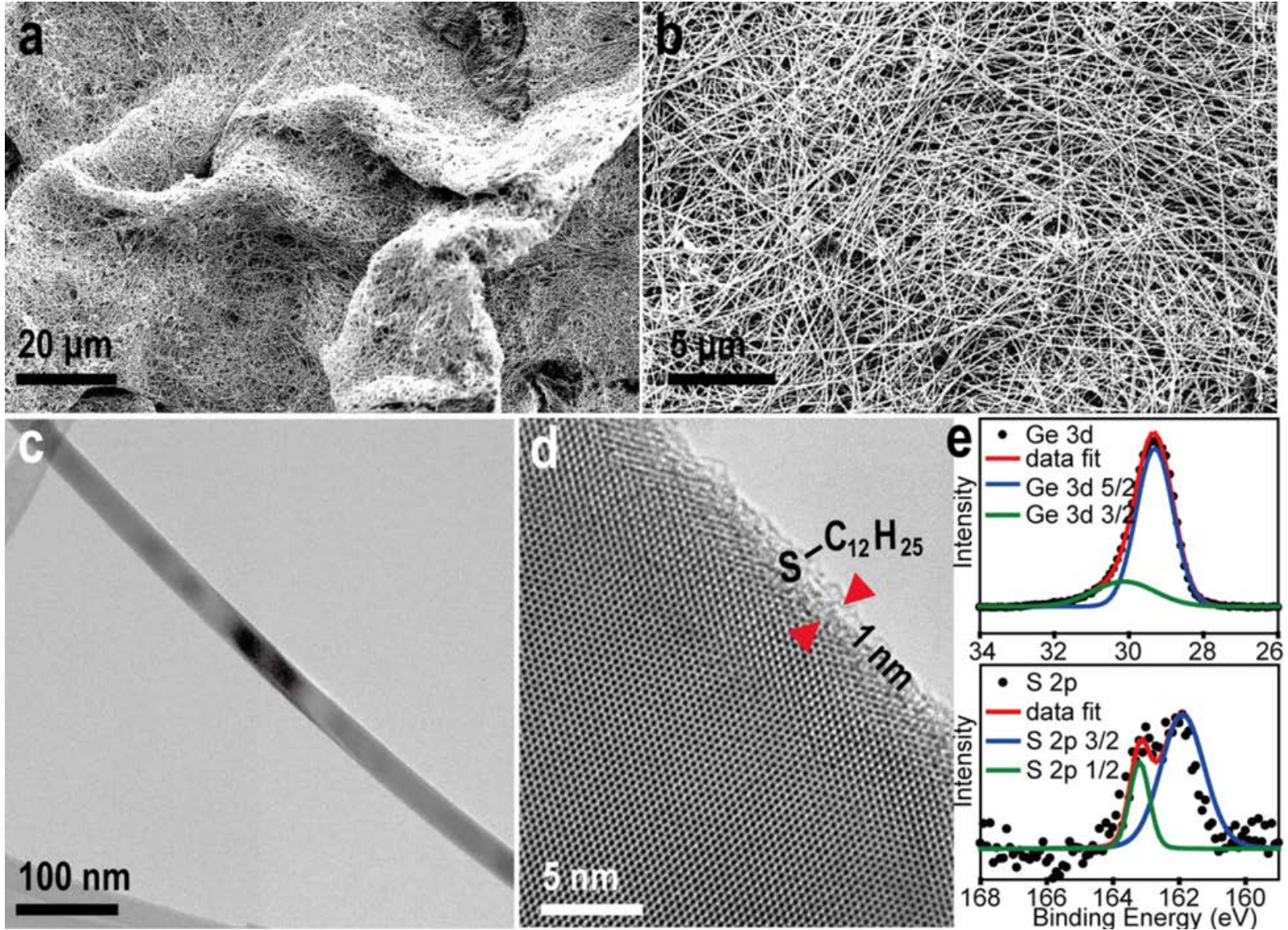


Growth of nanowires: metal seeded vapor-liquid-solid approach

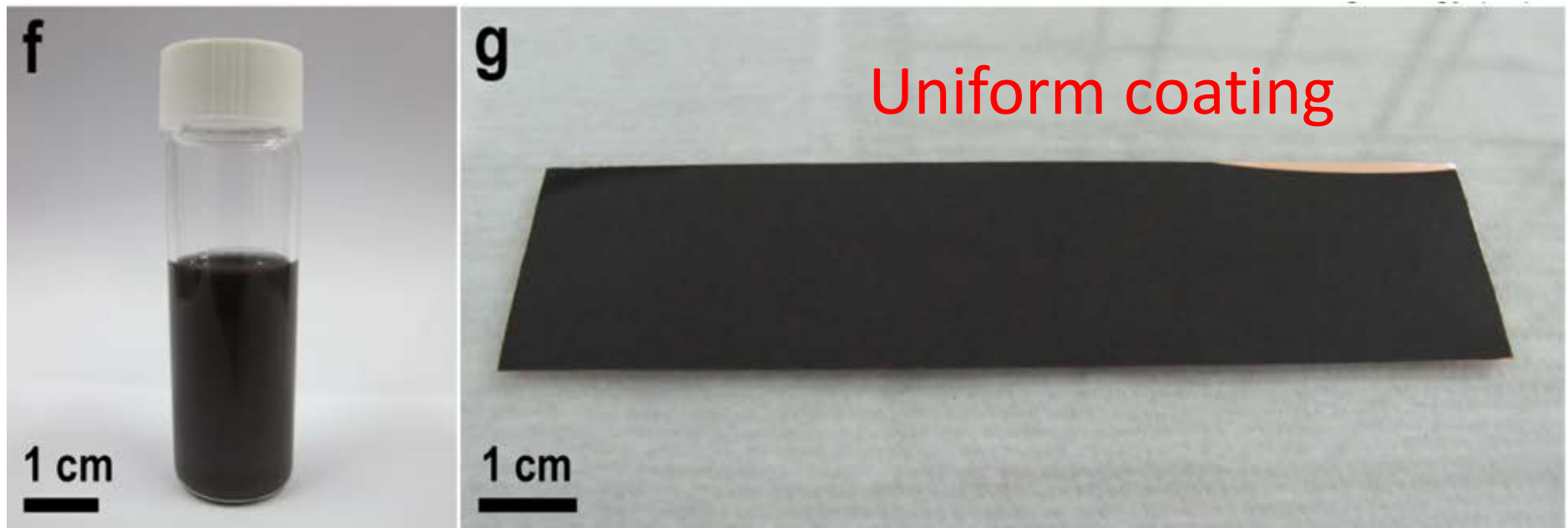


- metal nanoparticle-seeded Si and Ge nanowire synthesis
- most widely used metal is Au
- metal nanoparticles can control Si nanowire size

Germanium nanowire



Germanium Inks and coin cell fabrication

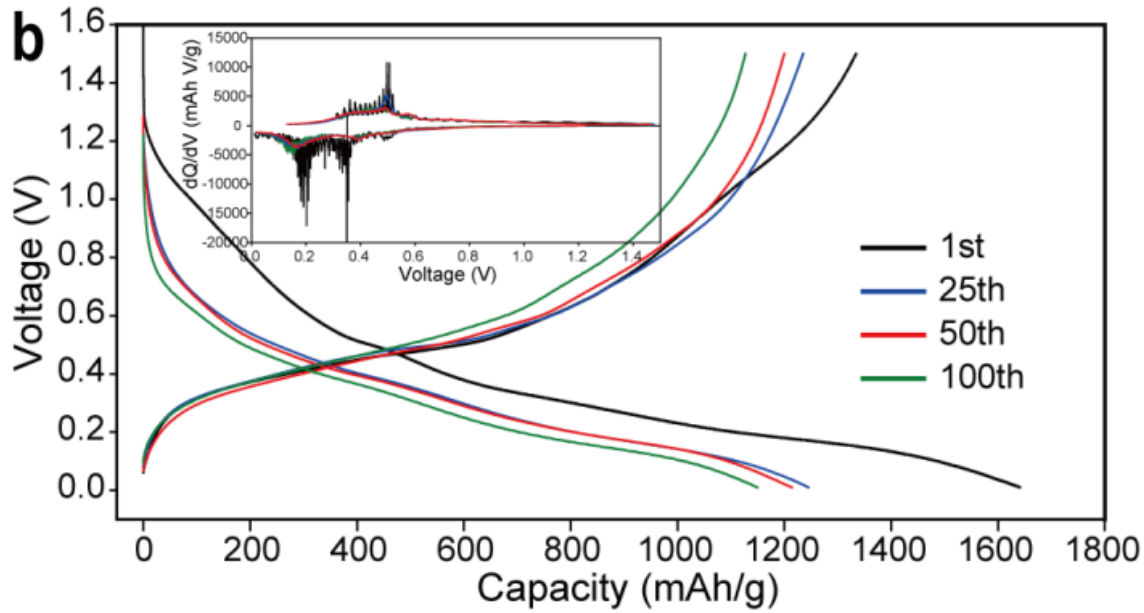
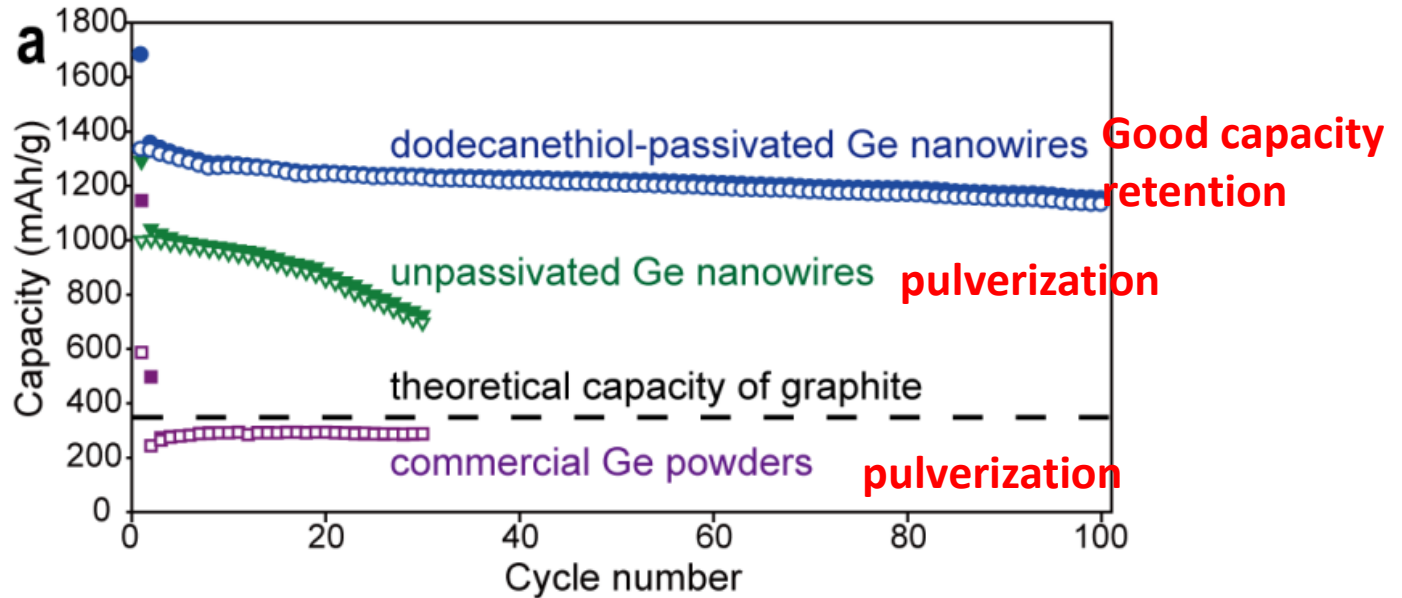


Stable suspension

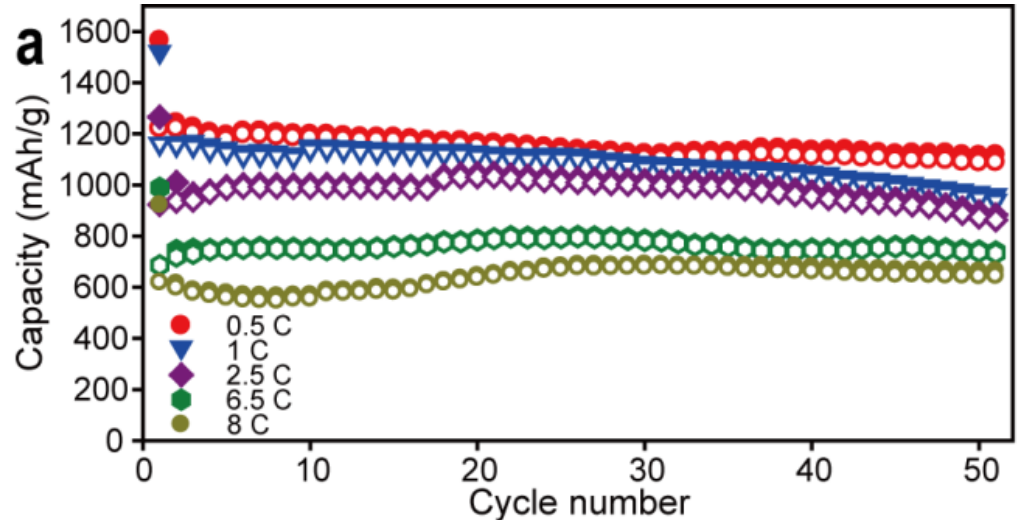
Coin cell



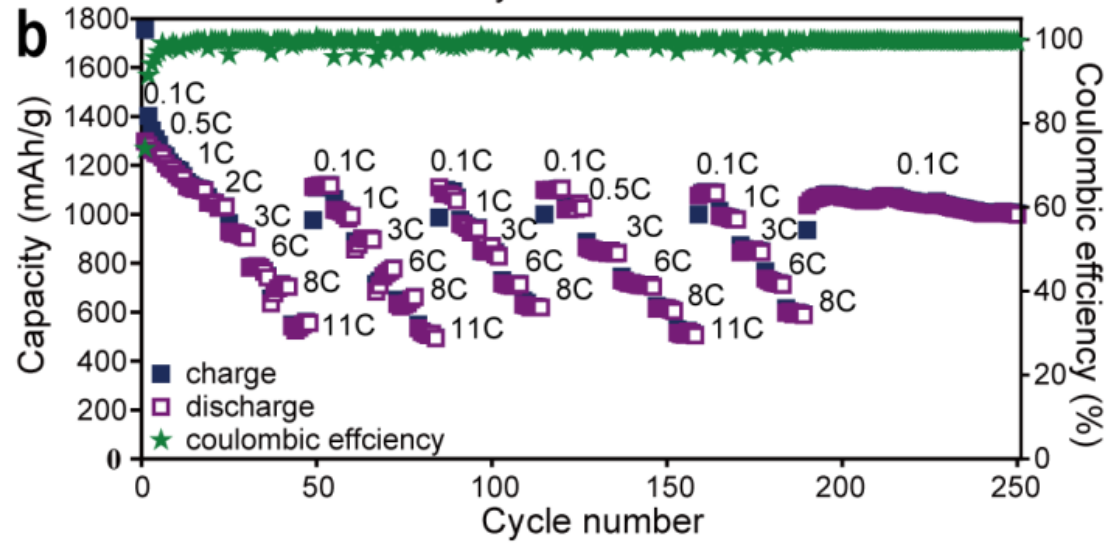
Performance of Ge nanowire anode



High-rate capability of Ge nanowire anode

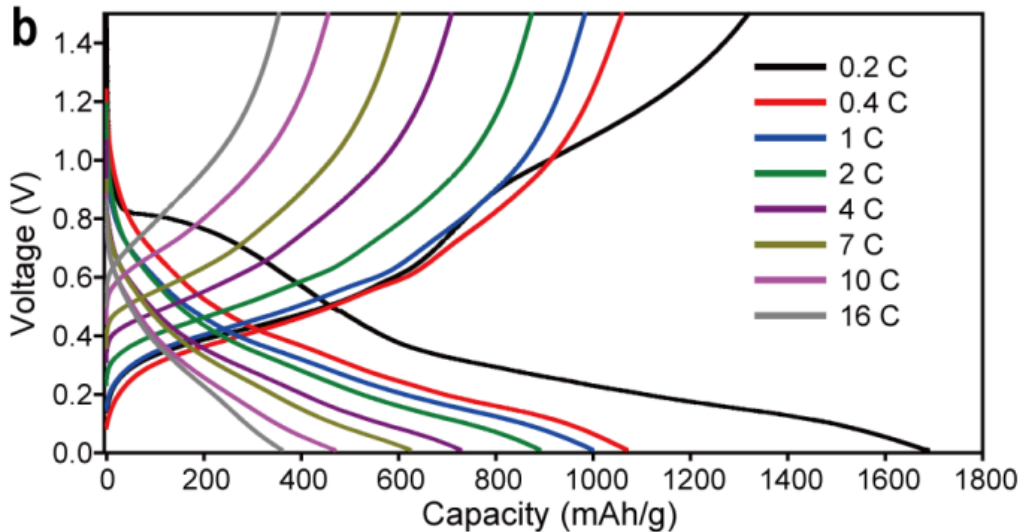
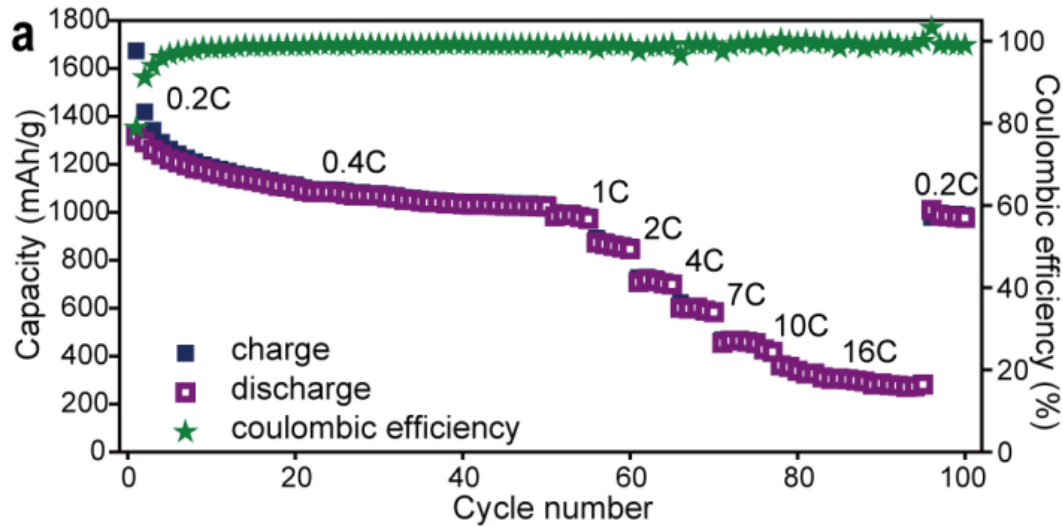


Very good high rate capability

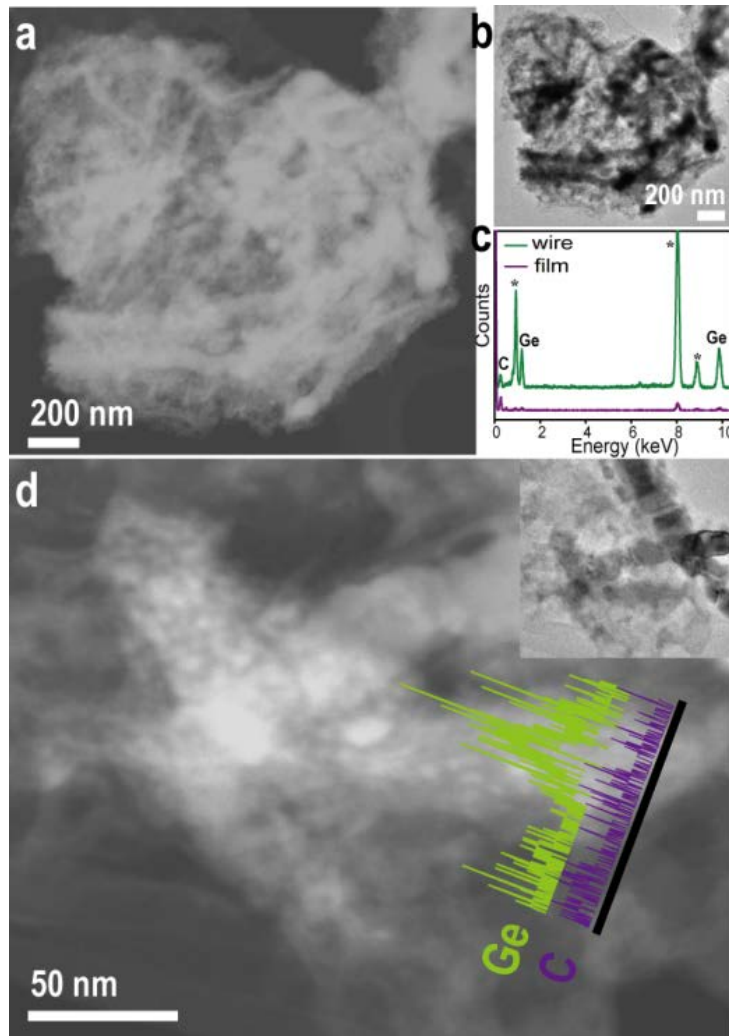


Five repeated cycles

High temperature performance (55 °C) of Ge nanowire anode

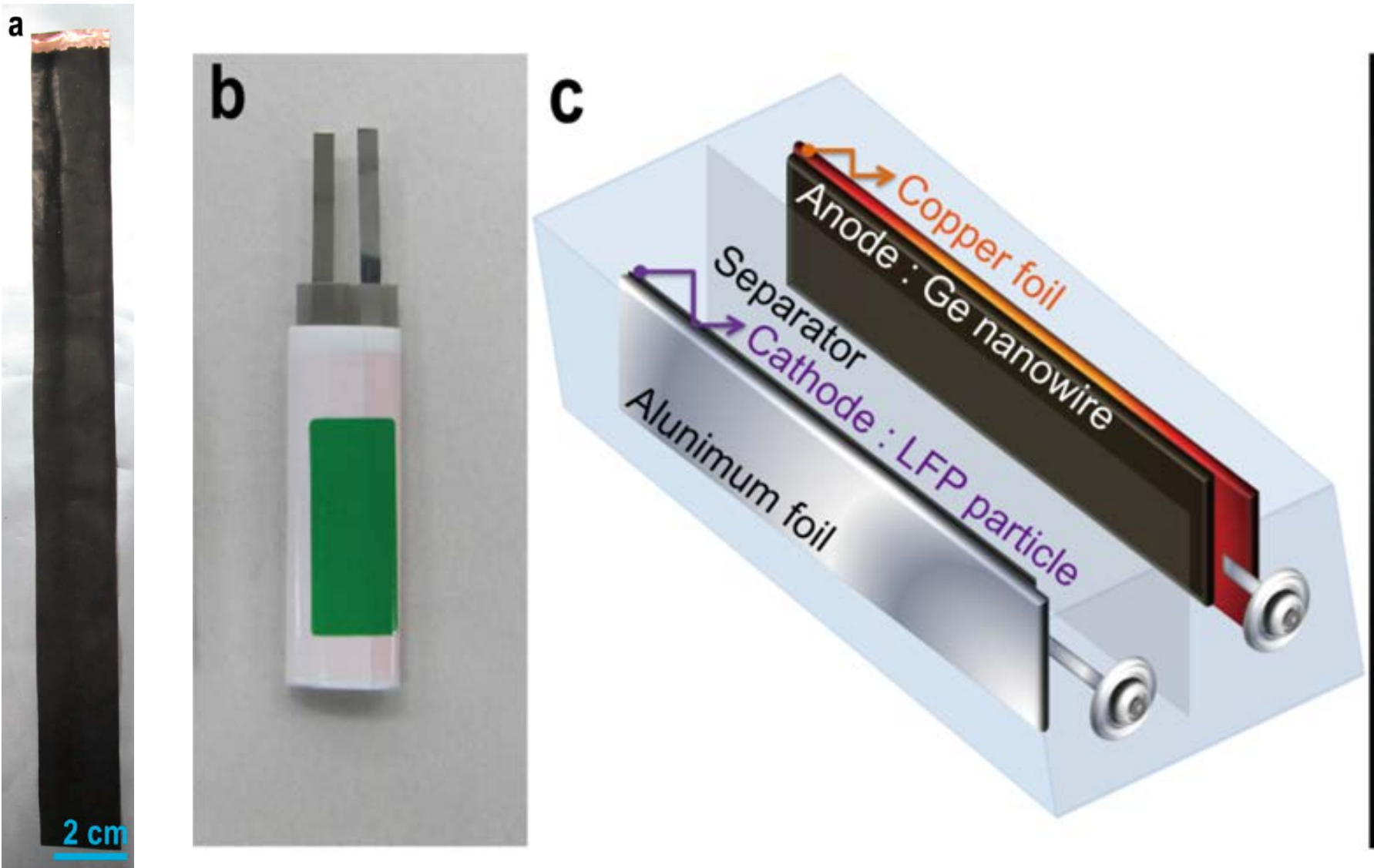


Robust nanowire/PVDF structure



After many cycles of lithium insertion and extraction, the structure is still very robust

A large-area assembled full cells



e

Alkanethiol-Passivated Germanium
Nanowires as High-Performance Anode
Materials for Lithium-Ion Batteries:
The Role of Chemical Surface
Functionalization


d





f

Synthesis of $\text{CuIn}_{1-x}\text{Ga}_x(\text{S}_y\text{Se}_{1-y})_2$ (CuInGaSSe) Nanocrystal inks for low-cost photovoltaic devices

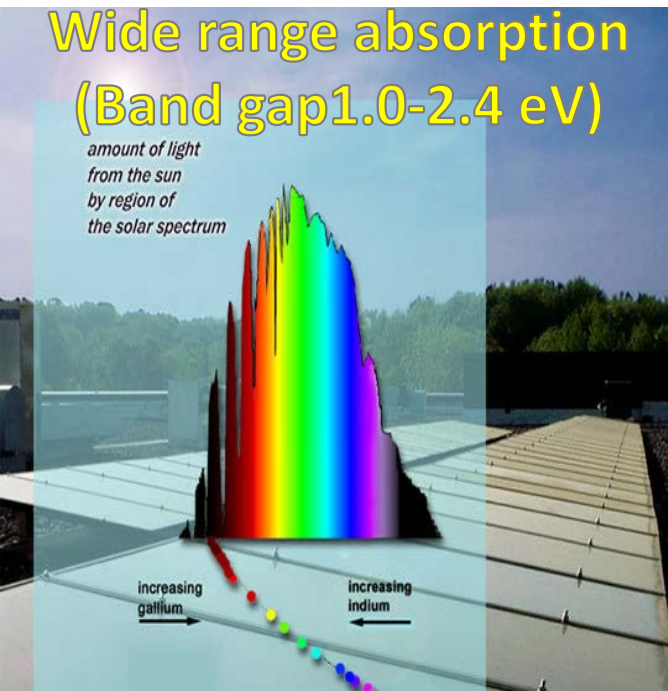


29 C Cu 63.55	49 I In 114.81	31 G Ga 69.72	16 S S 32.07	34 Se Se 78.96
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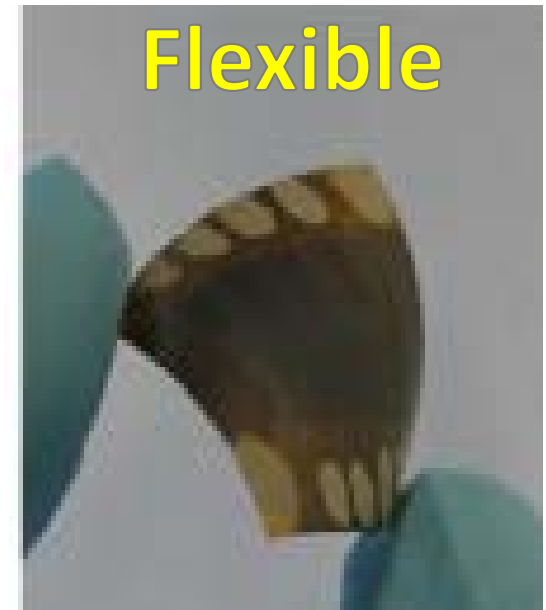
Tuan et al.

- *Energy & Environmental Science*, 2011, 4, 4929-4932
- *The Journal of Physical Chemistry C*, 2011, 115(5), 1592-1599
- *Langmuir*, 2012, accepted

CIGS solar cell characteristics



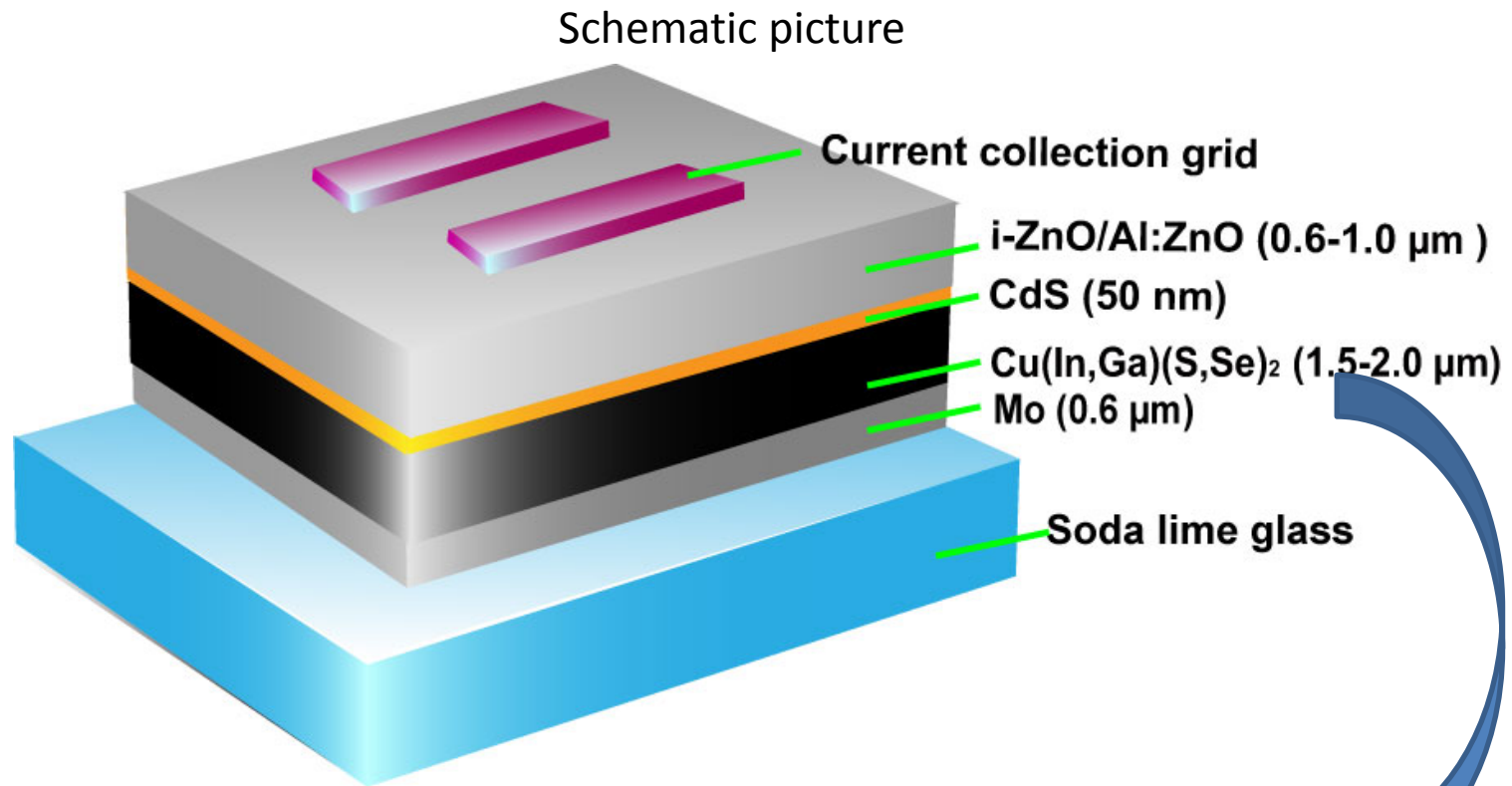
Berkely lab news center website



Journal of Solid State Chemistry
189 (2012) 2-12

Cu(In,Ga)(S,Se)₂ (CIGS) device structure

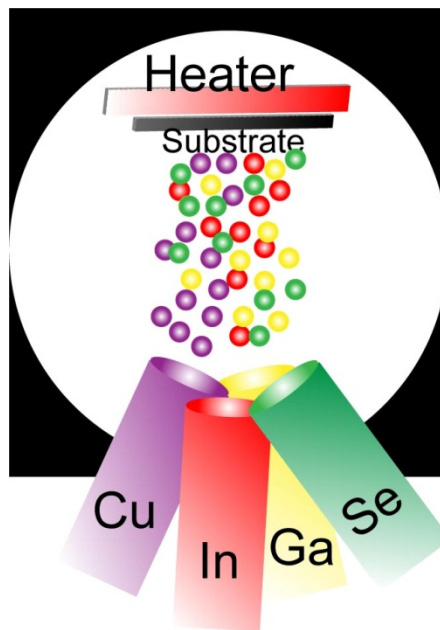
Total device thickness less than 5 μm (Crystalline Si module ~200 μm)



The CIGS_{Se} absorber layer can be made via a **vacuum** or a **nonvacuum** route.

Vacuum-based CIGS film deposition

Could make the Highest efficiency cell in the lab ~20%, but



TIME-CONSUMING

EXPENSIVE

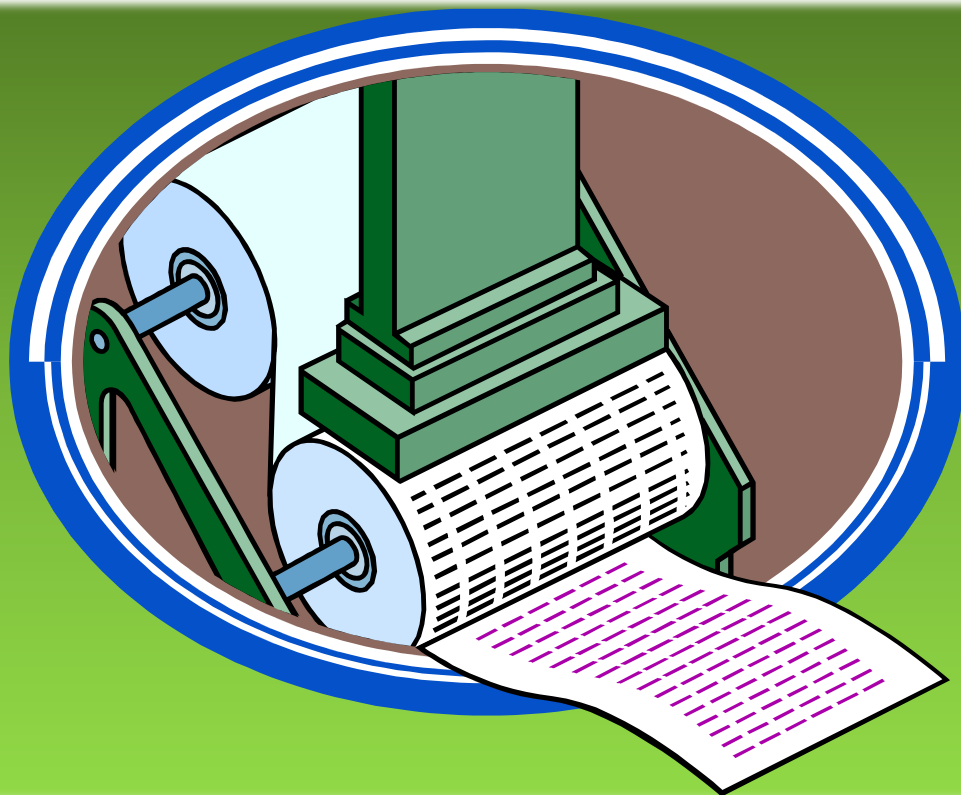
LOW THROUGHPUT

**DIFFICULT TO CONTROL
STOICHIOMETRY
OVER LARGE AREAS**

**POOR MATERIALS
UTILIZATION (30-50%)**



Non-Vacuum Processing for CIGS thin film deposition



ROLL-TO-ROLL PROCESSING

COST EFFECTIVE

**STOICHIOMETRY
CONTROLLABLE OVER
LARGE AREA**



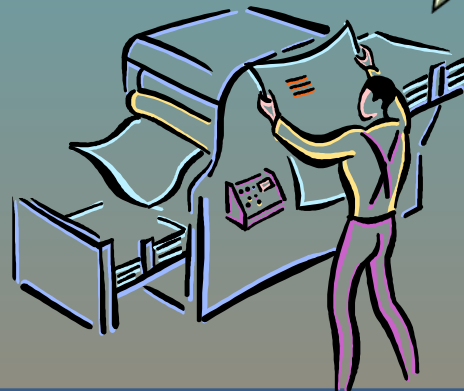
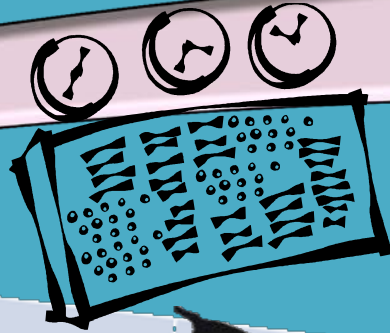
Vacuum method

COST

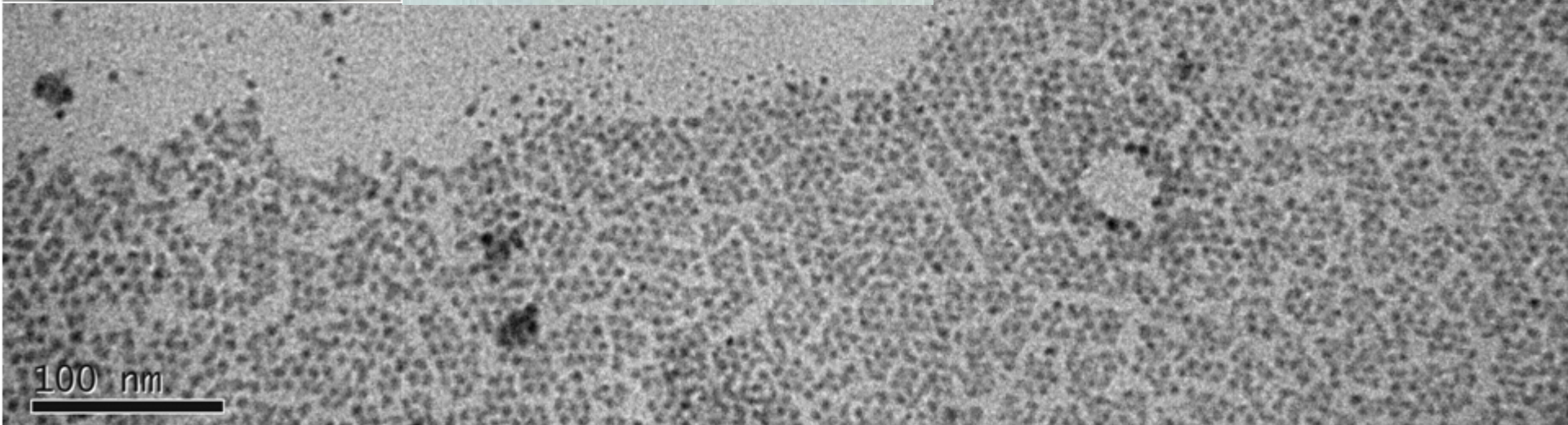
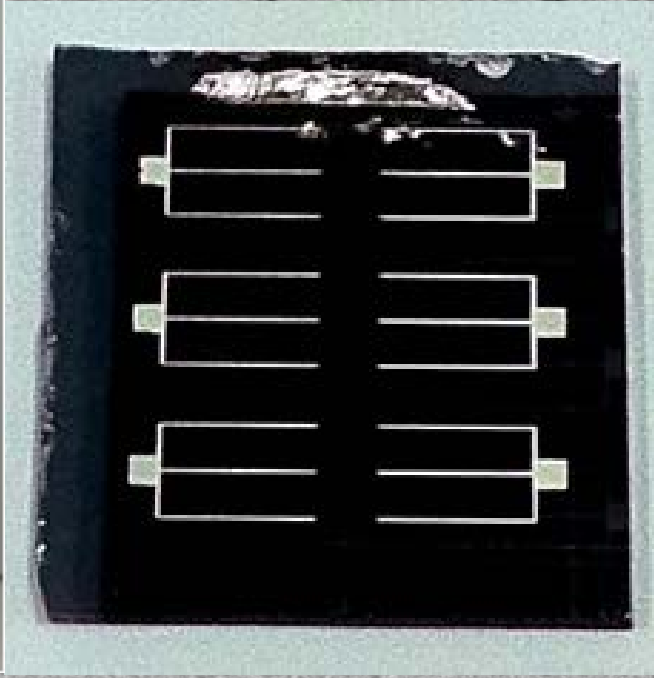
Lab scale

Industry

Non-vacuum route



Nanocrystal ink for CIGS solar ce



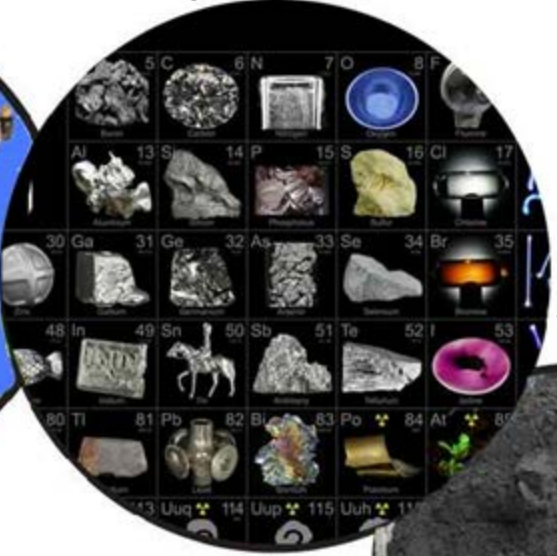
100 nm

Size control

Composition control

What can CIGS nanocrystals offer?

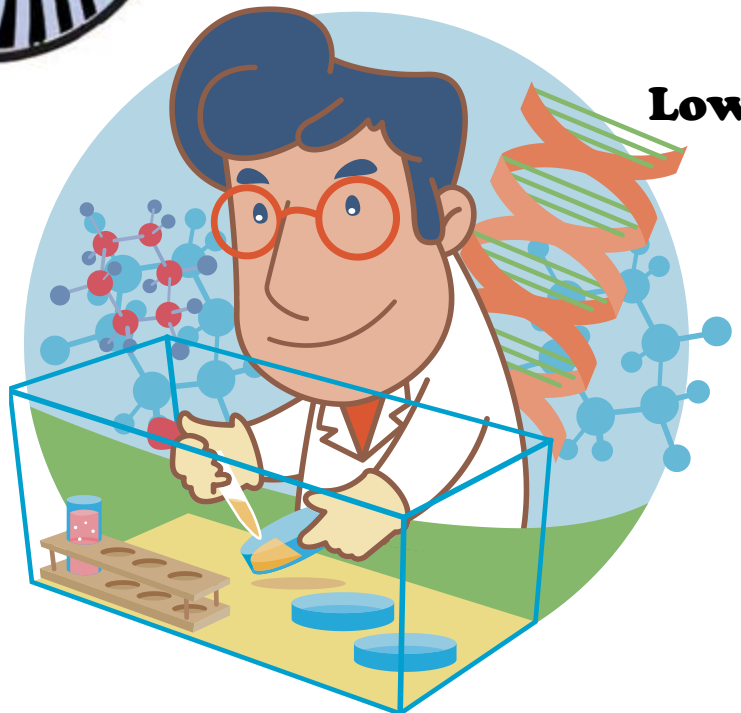
Shape control



Large quantity

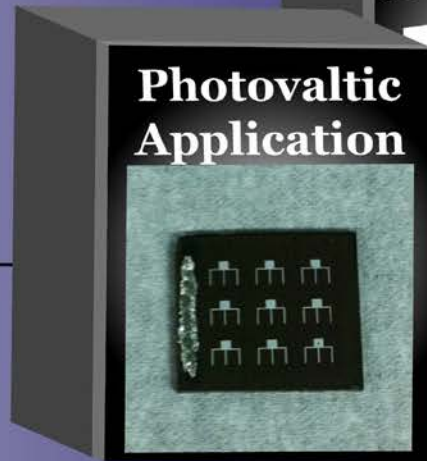
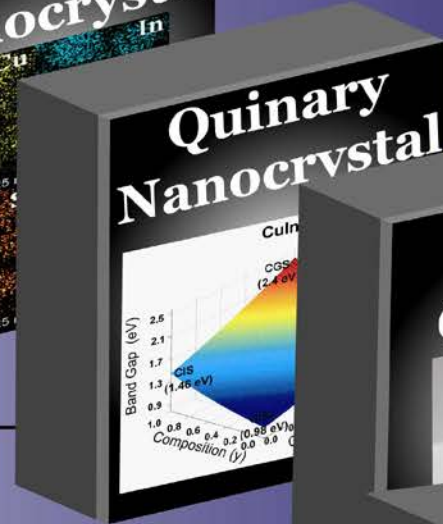
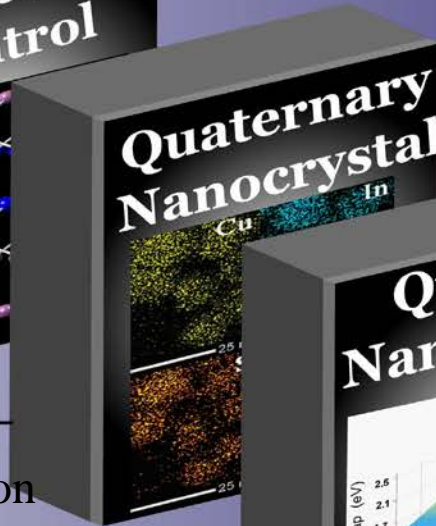


Low cost



Powder like appearance

Outline



2008.10

CIGS project begin

2008.10

Ternary nanocrystal phase & size control

2010.02

Tuning quaternary nanocrystal composition & optical properties

2010.09

Tuning quinary nanocrystal composition & optical properties

2011.06

$\text{CuIn}_{1-x}\text{Ga}_x(\text{S}_y\text{Se}_{1-y})_2$ Nanocrystal large scale production over 1 g yield.

2011.06

Developing spraying technique

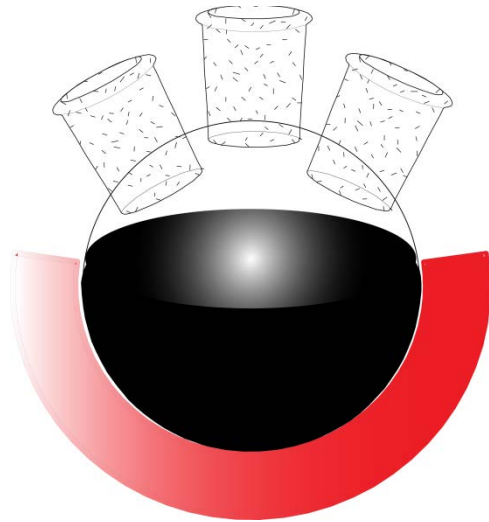
2011.10

Solar cell devices made

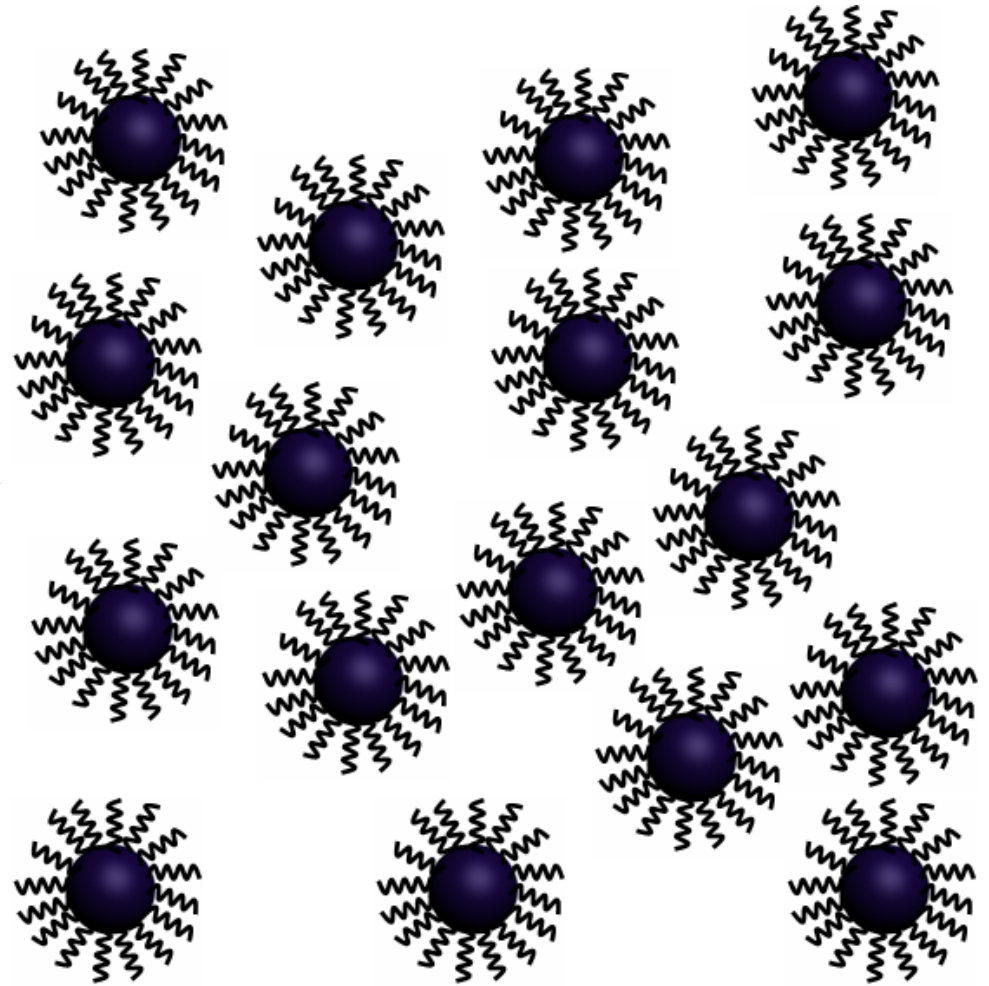
Facile Batch reaction Synthesis

Hot Solvent Method

- Cu, In, Ga, S, Se precursors
- Solvent
- Surfactant

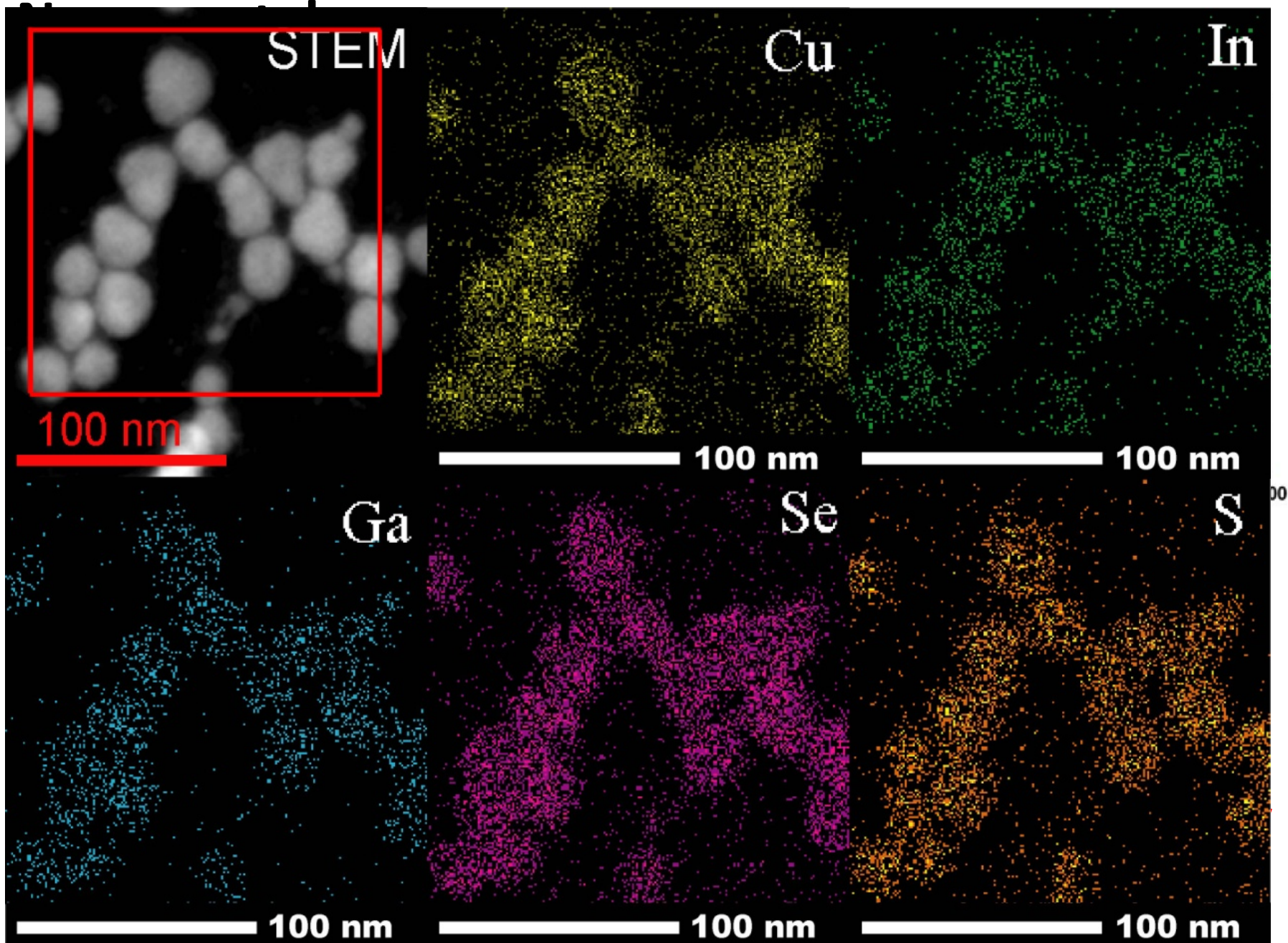


200~300°C

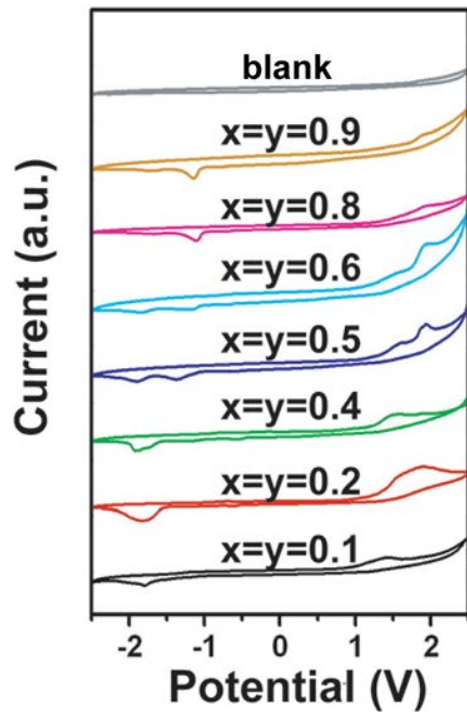




Composition Tuning of $\text{Cu}(\text{In}_{1-x}\text{Ga}_x)(\text{S}_y\text{Se}_{1-y})_2$

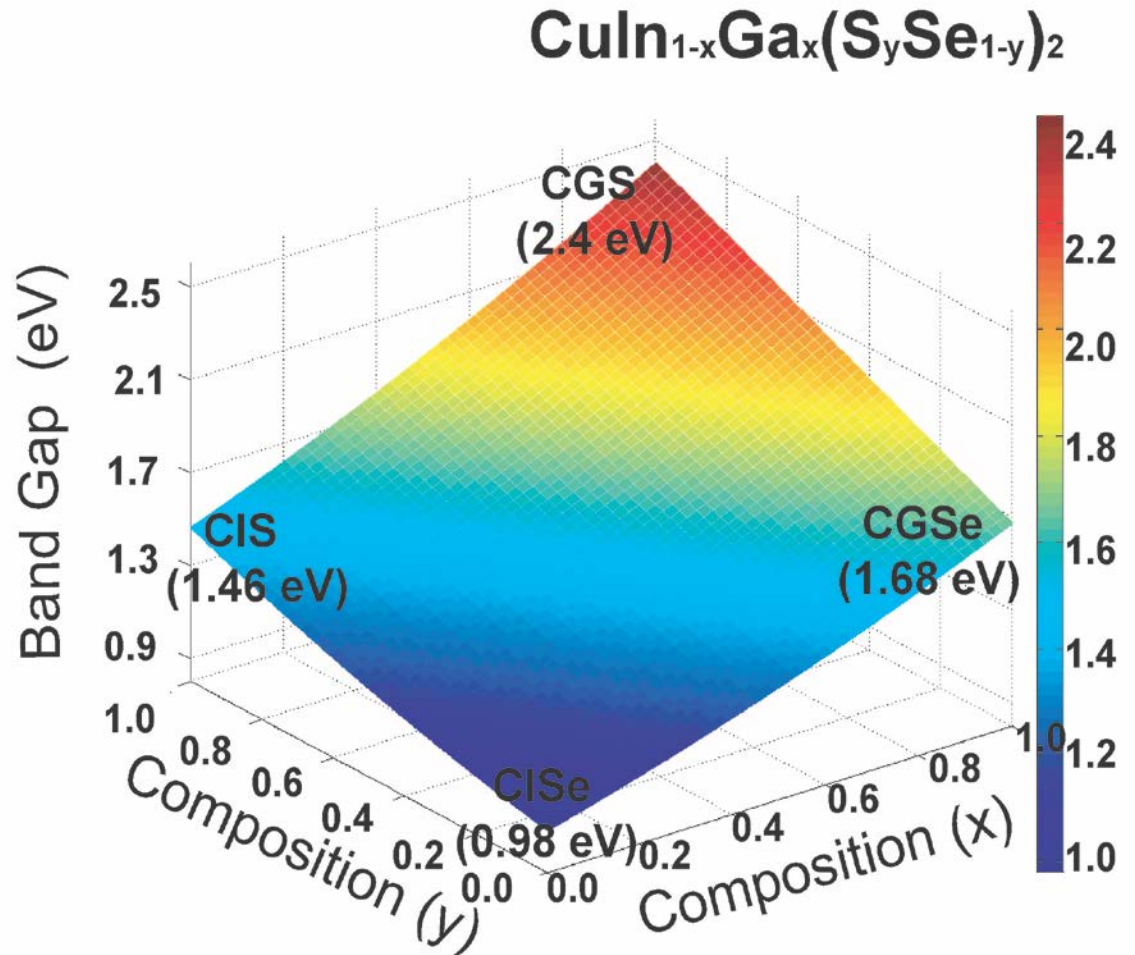
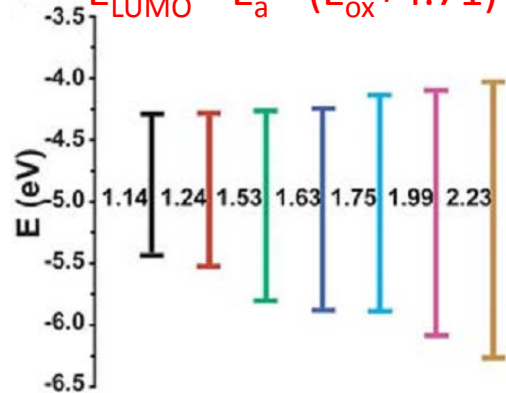


Cyclic voltammograms of $\text{Cu}(\text{In}_{1-x}\text{Ga}_x)(\text{S}_y\text{Se}_{1-y})_2$ nanocrystals

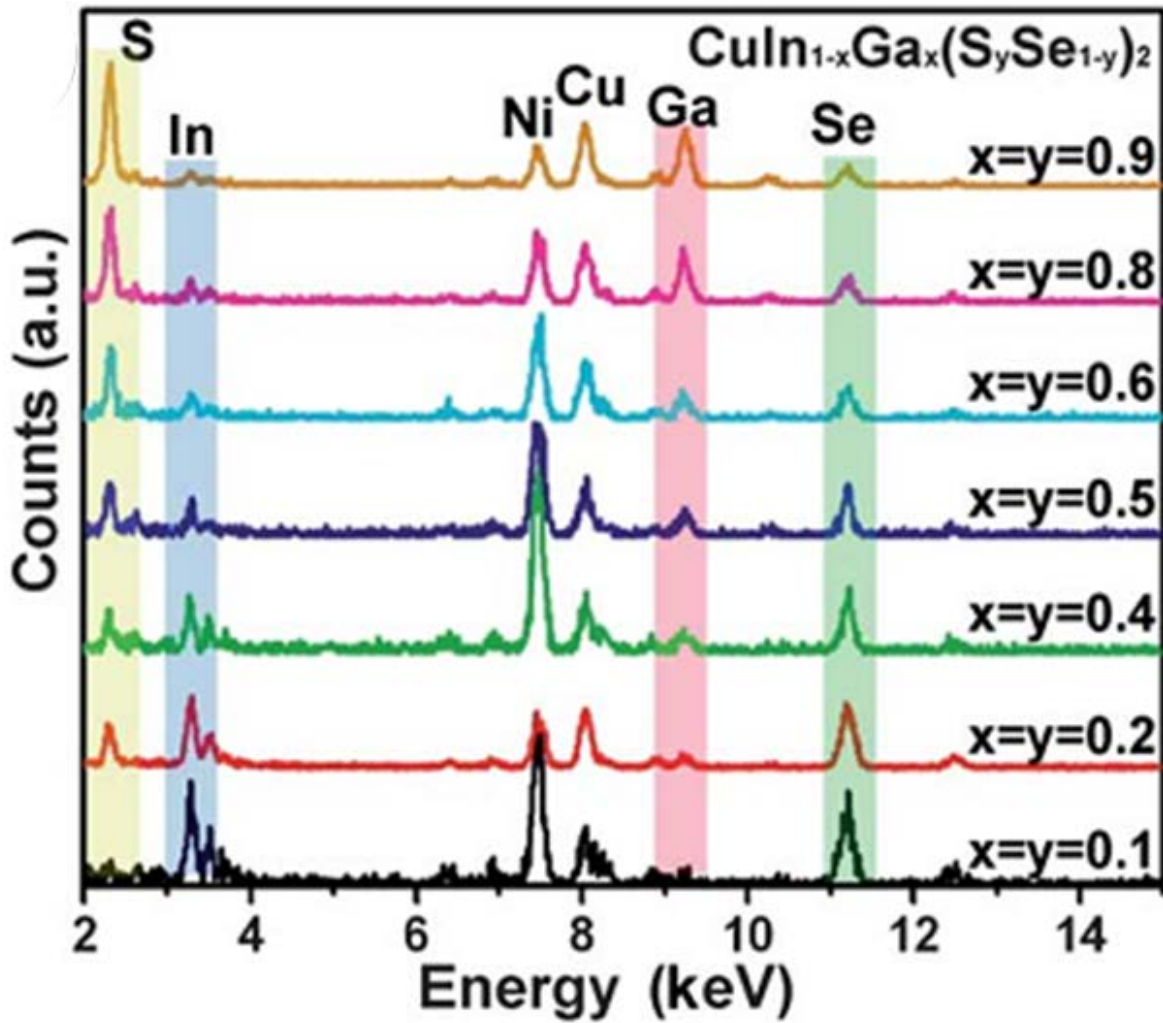


$$E_{\text{HOMO}} = -I_p = -(E_{\text{ox}} + 4.71) \text{ eV}$$

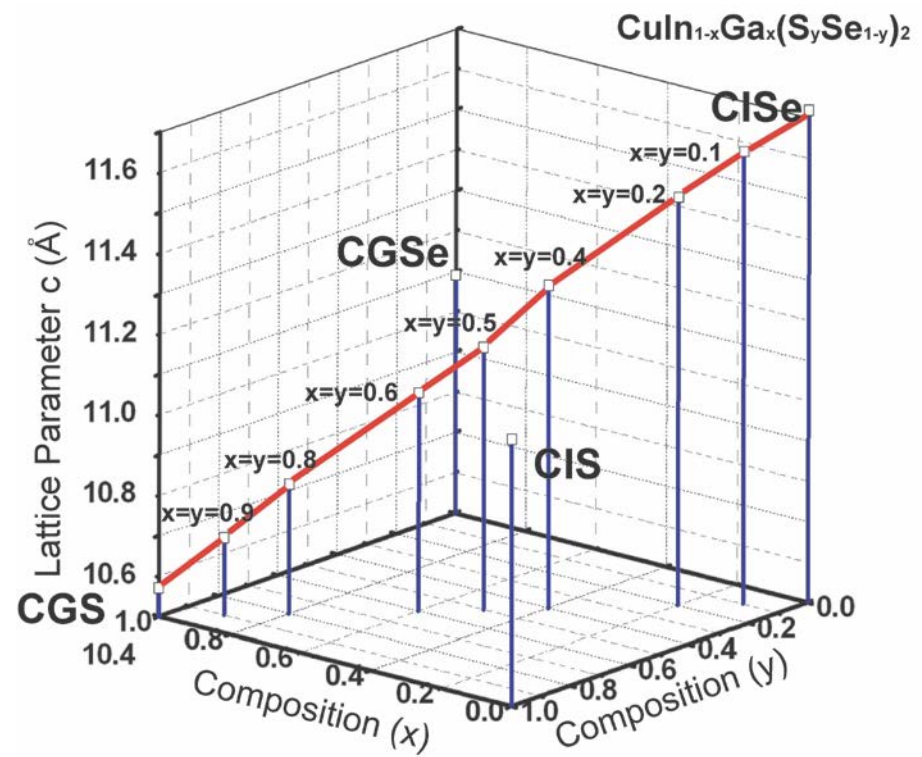
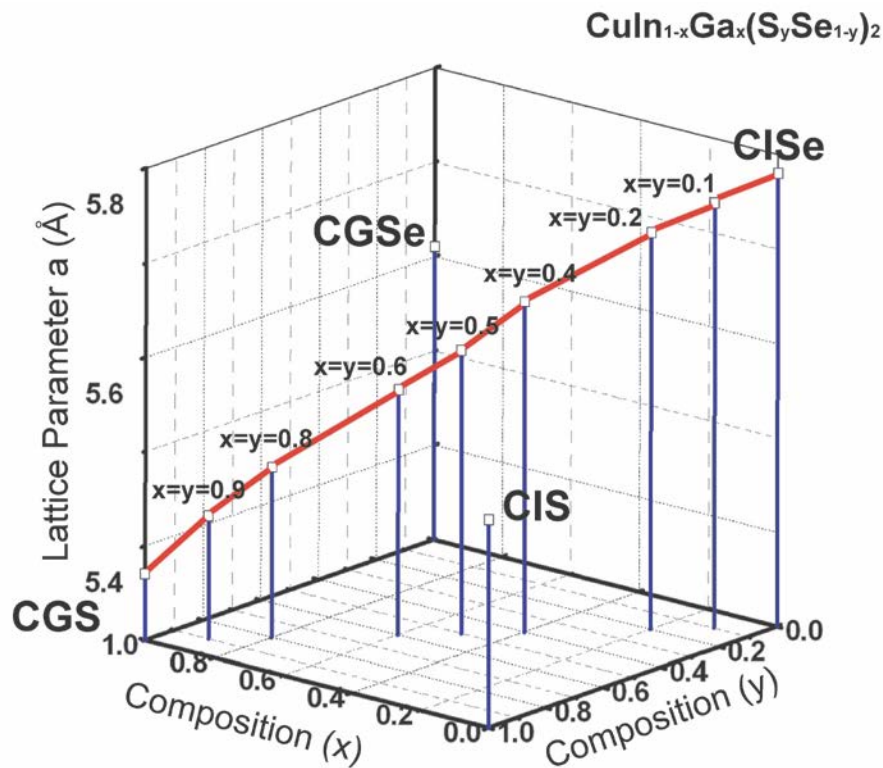
$$E_{\text{LUMO}} = -E_a = -(E_{\text{ox}} + 4.71) \text{ eV}$$



$\text{Cu}(\text{In}_{1-x}\text{Ga}_x)(\text{S}_y\text{Se}_{1-y})_2$ nanocrystal EDS analysis



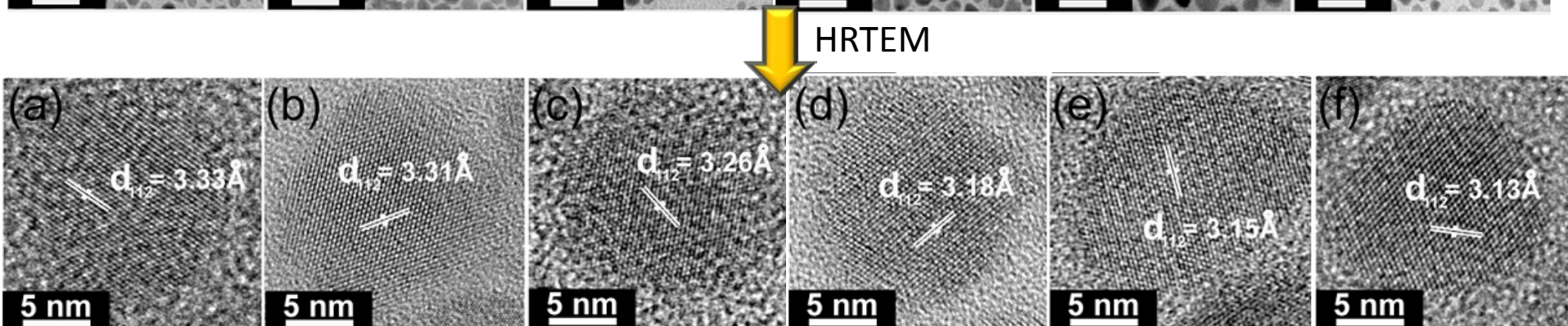
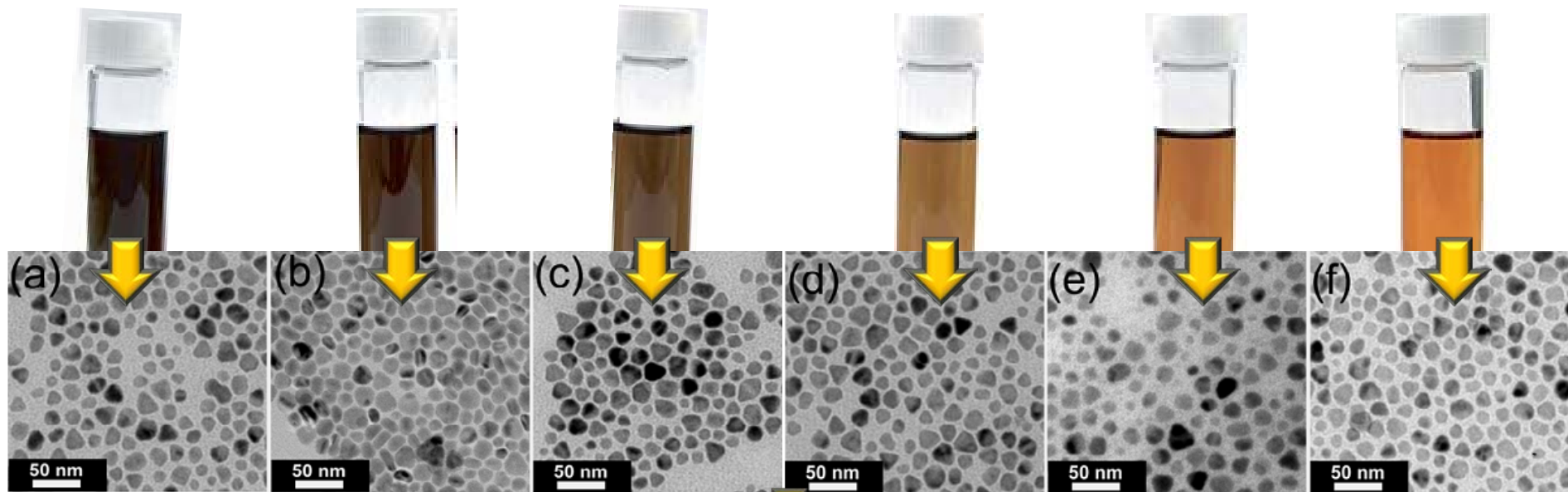
Cu(In_{1-x}Ga_x)(S_ySe_{1-y})₂ lattice parameter (derived from XRD)



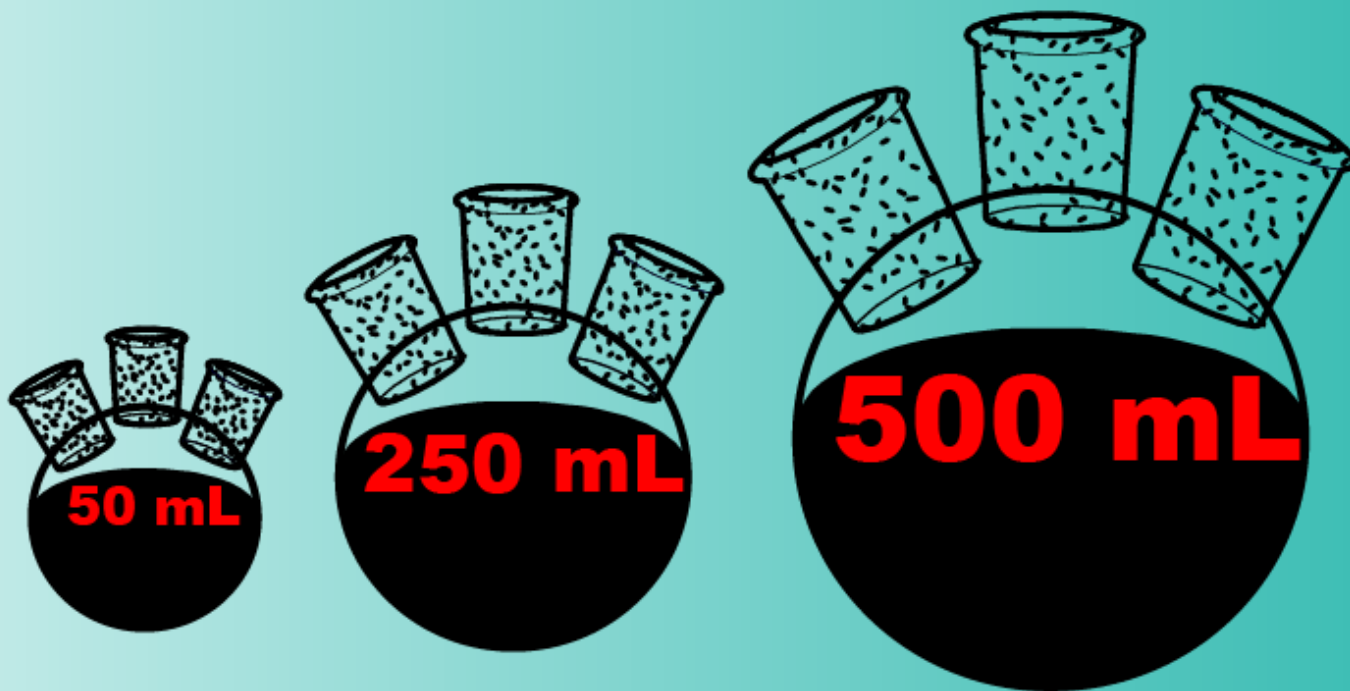
Agree with Vegard's law (red lines)

$\text{CuIn}_{1-x}\text{Ga}_x(\text{S}_y\text{Se}_{1-y})_2$ size and shape

$x=y=0.1$ $x=y=0.2$ $x=y=0.4$ $x=y=0.6$ $x=y=0.8$ $x=y=0.9$
 $E_g=1.08$ eV $E_g=1.17$ eV $E_g=1.42$ eV $E_g=1.71$ eV $E_g=2.01$ eV $E_g=2.20$ eV



d_{112} decrease



Large scale

Scale-up synthesis of CIGS nanocrystals



Yield > 70 %
Gram-scale
production

Large scale synthesis + composition tuning

a $\text{CuIn}(\text{S}_{0.5}\text{Se}_{0.5})_2$
weight : 1.08 g



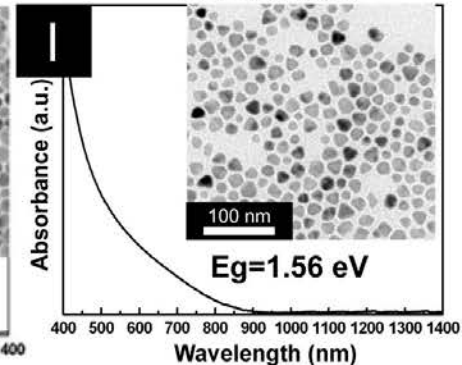
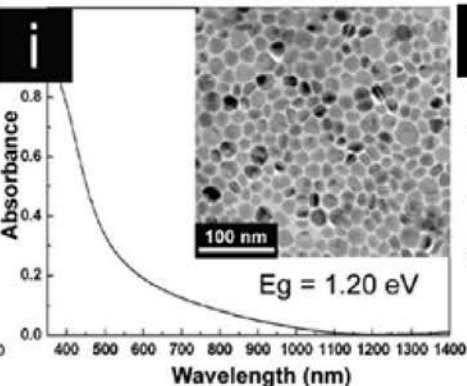
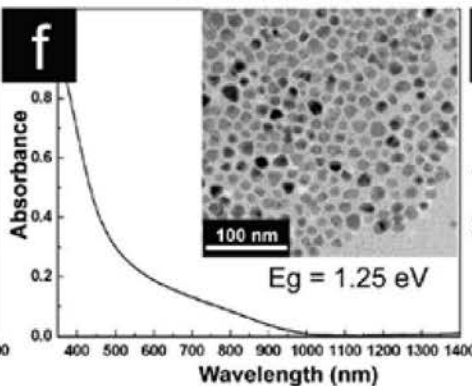
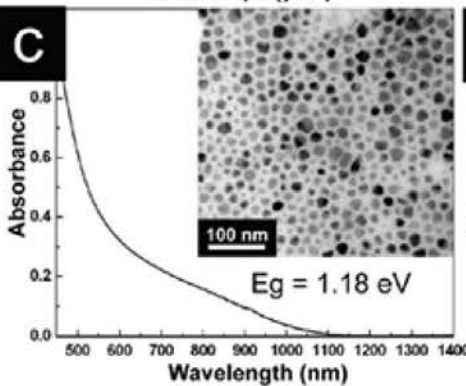
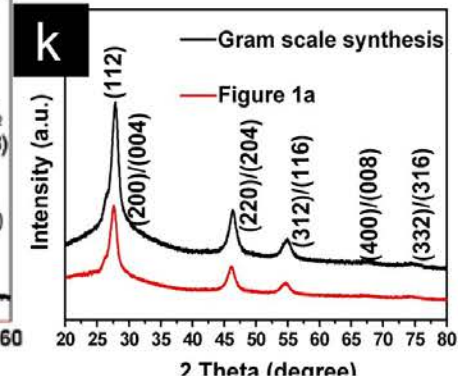
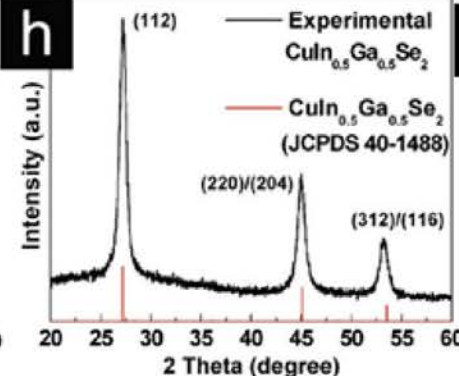
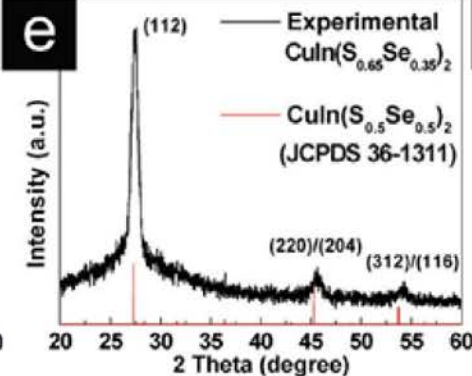
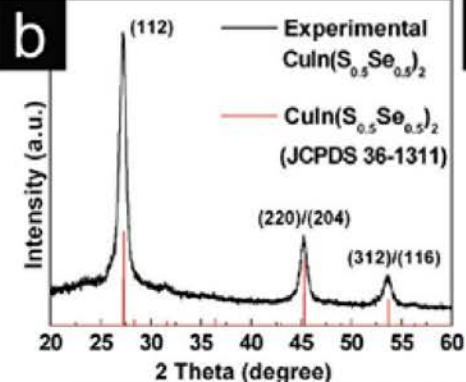
d $\text{CuIn}(\text{S}_{0.65}\text{Se}_{0.35})_2$
weight : 1.18 g



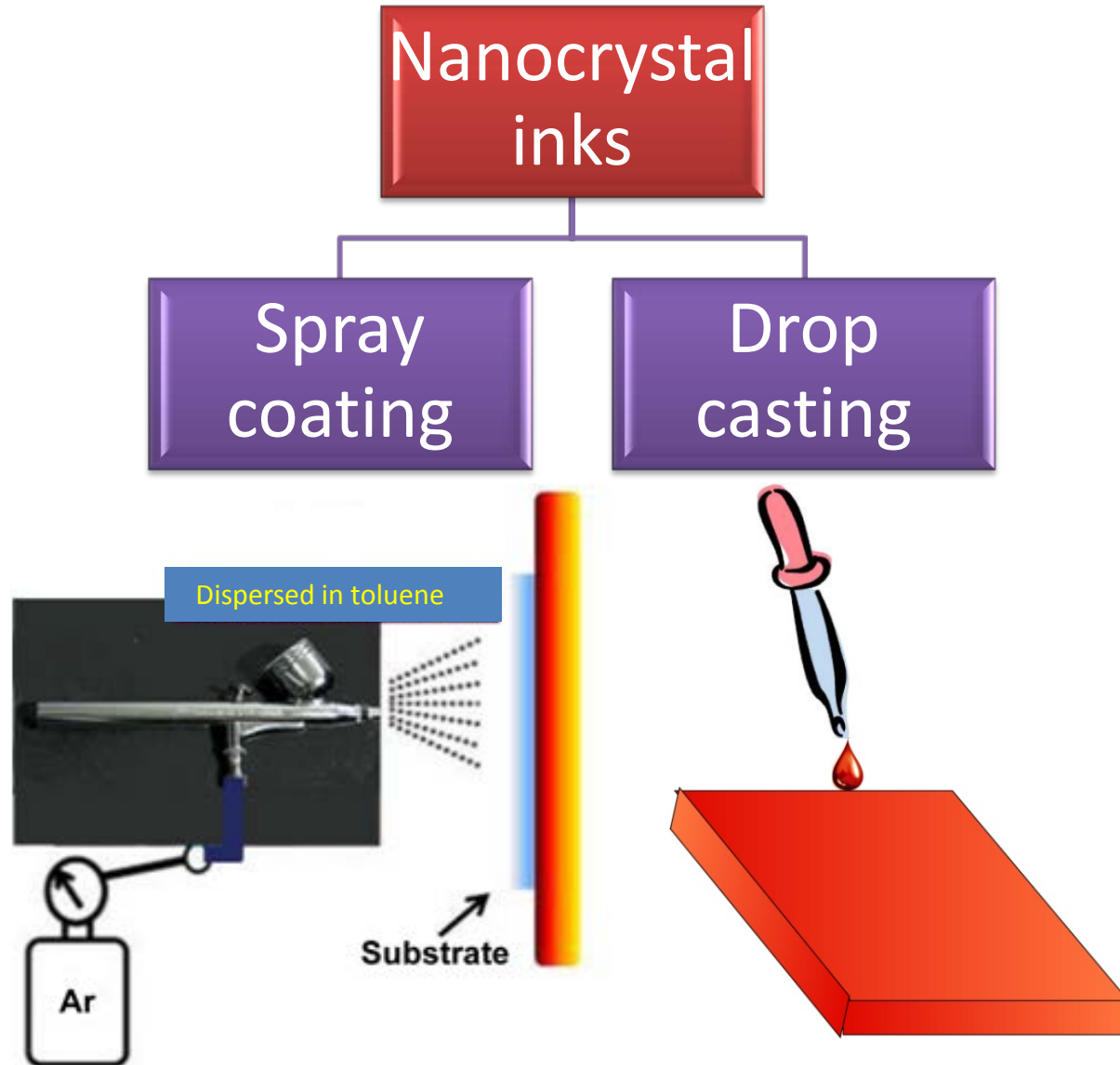
g $\text{CuIn}_{0.5}\text{Ga}_{0.5}\text{Se}_2$
weight : 1.25 g



j $\text{CuIn}_{0.5}\text{Ga}_{0.5}(\text{S}_{0.5}\text{Se}_{0.5})_2$
weight : 1.34 g



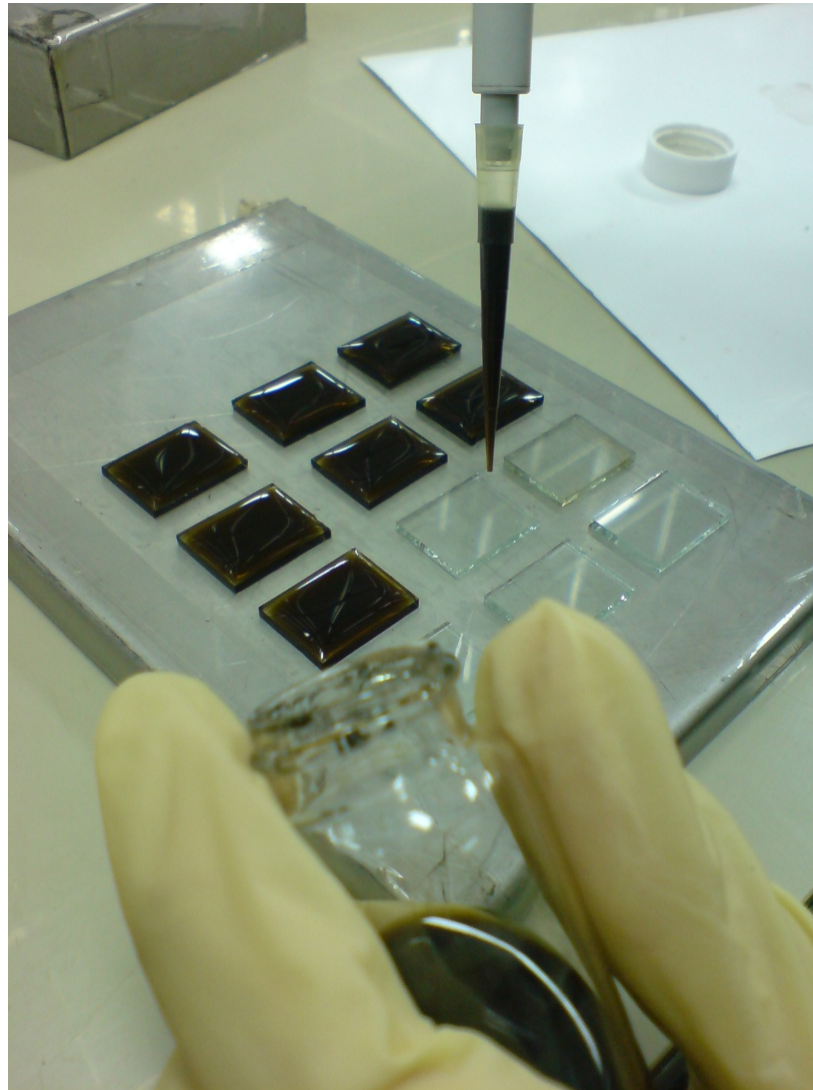
Methods to prepare a absorber film with uniform thickness for photovoltaic device fabrication



Photos of CIS_2 , CISe_2 , CIGS
nanocrystals made in our lab

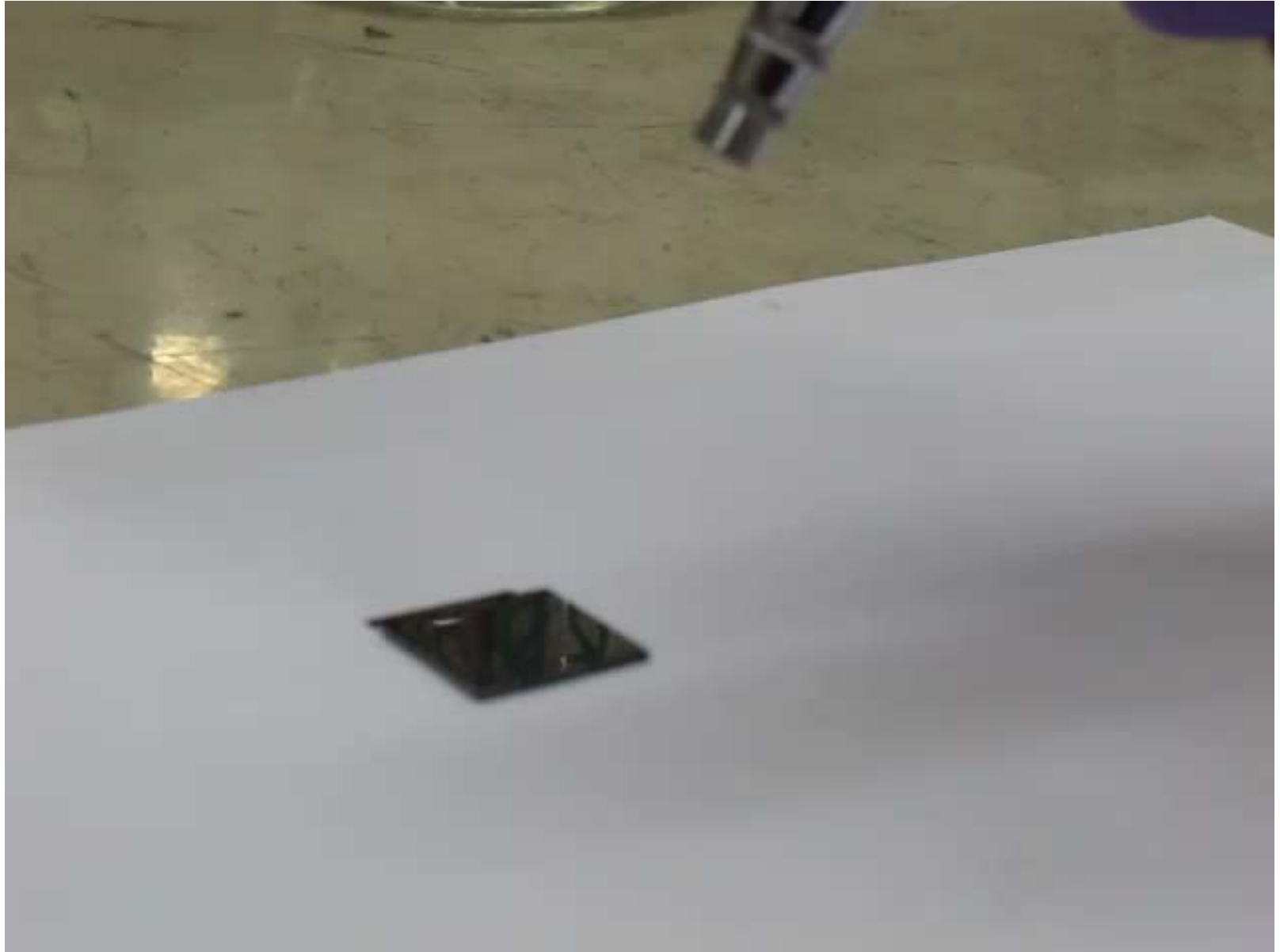


Drop-casting of ClSe_2 Nanocrystal

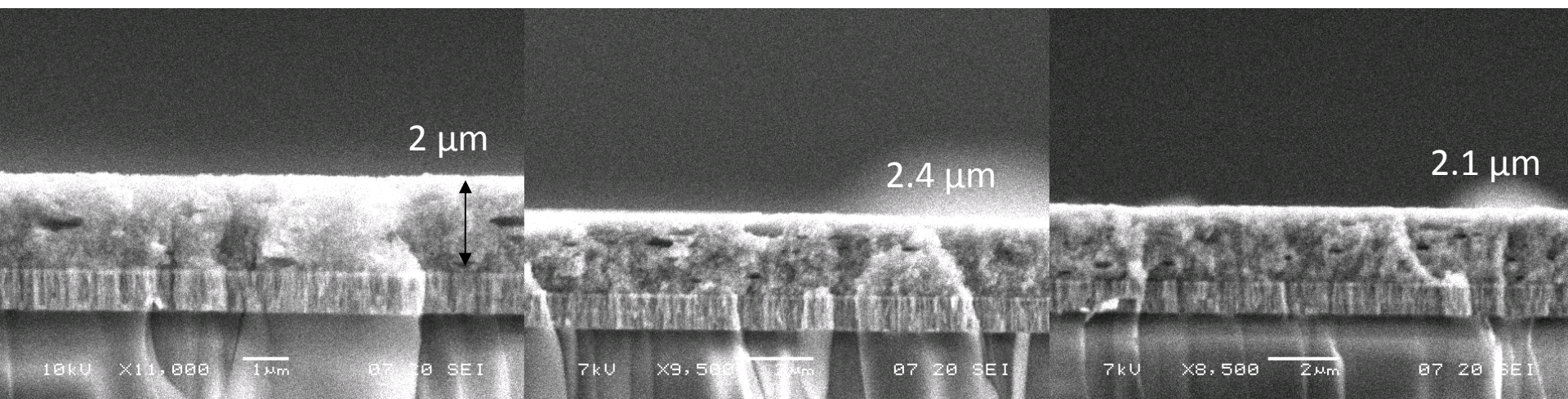
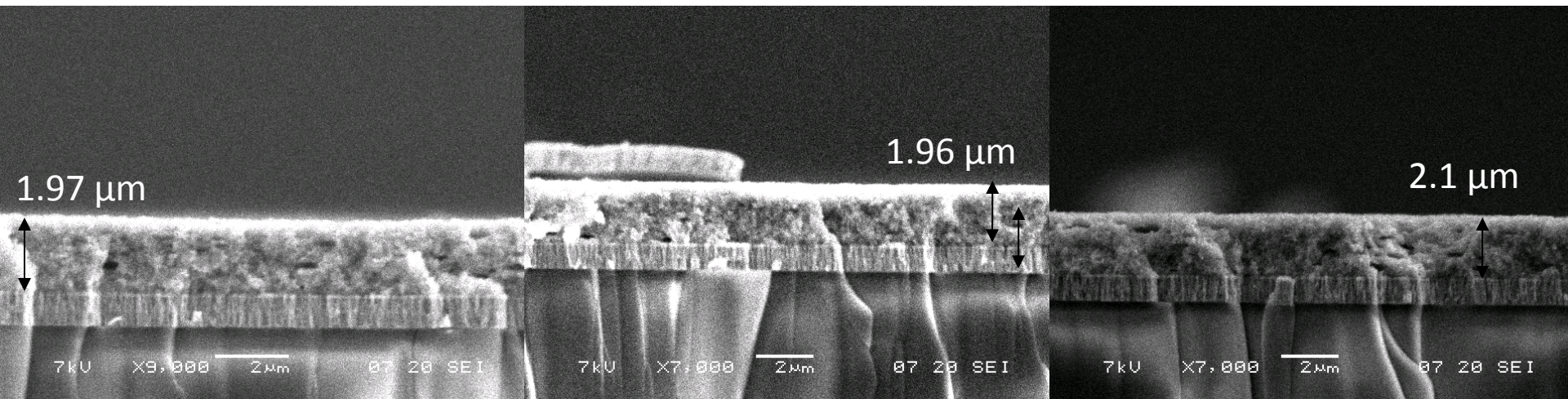


Glass : 20mmx15mm

Spray-depositing Nanocrystals on Mo-coated Soda Glass



Spray-deposited Film results



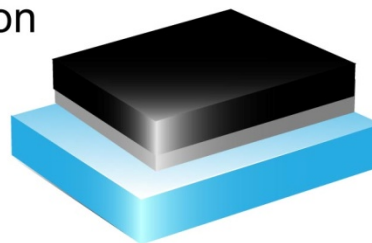
Procedure of CIGS photovoltaic device fabrication

CIGSSe ink spraying
on Mo glass



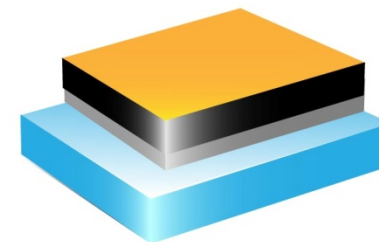
Selenization

CIGSSe/Mo glass

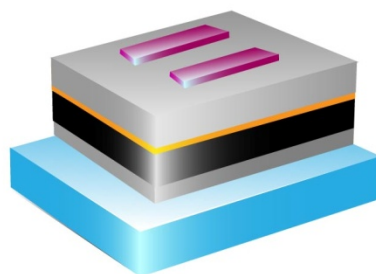


CBD

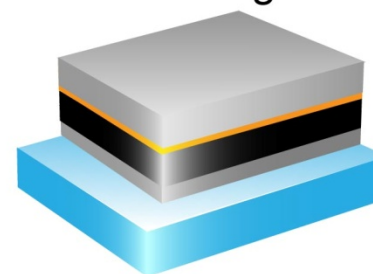
CdS deposition



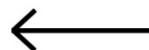
Current collection grid



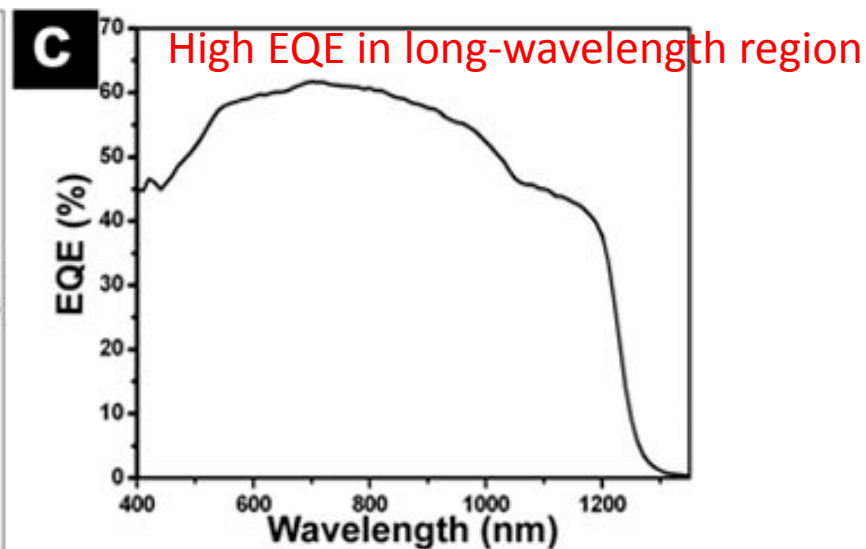
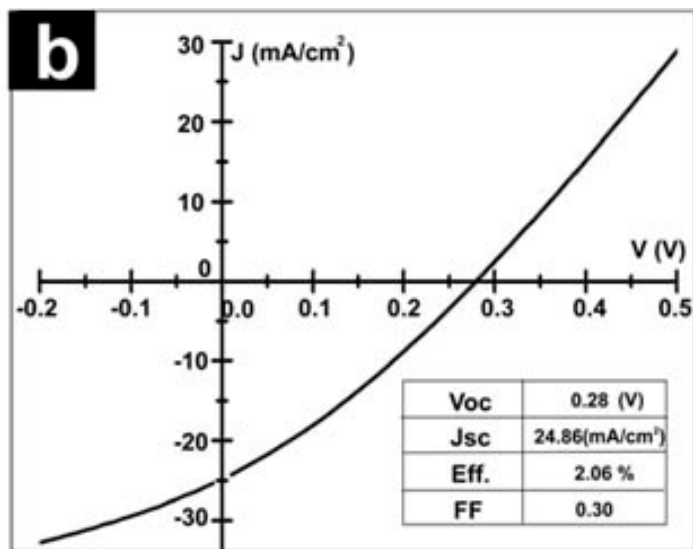
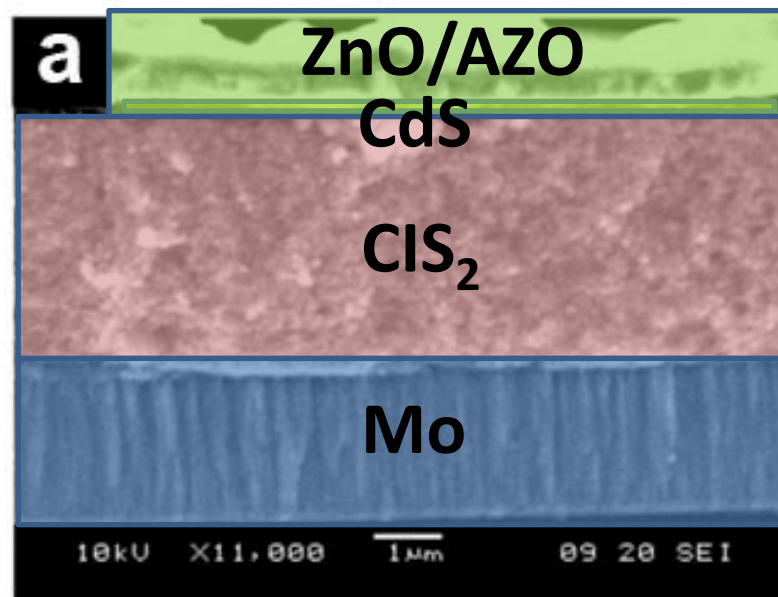
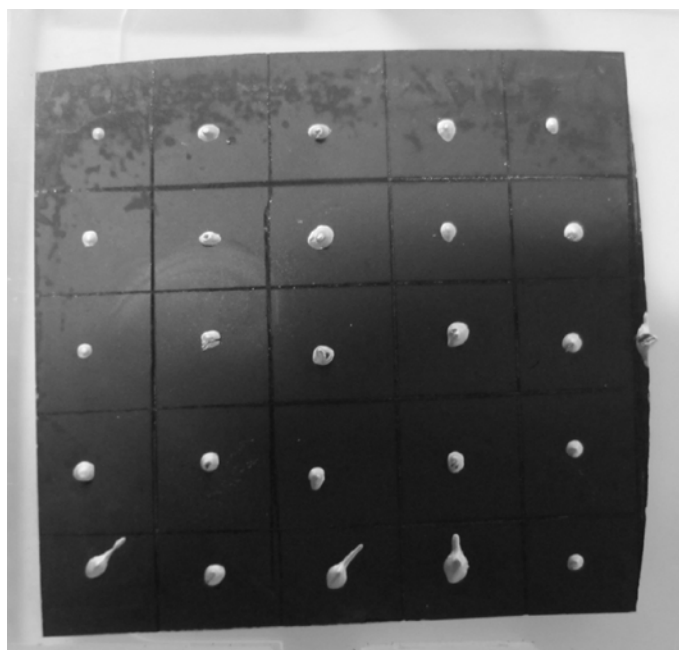
Al-ZnO/i-ZnO/CdS
/CIGSSe/Mo/glass



ZnO sputter



Electrical characteristics of Devices



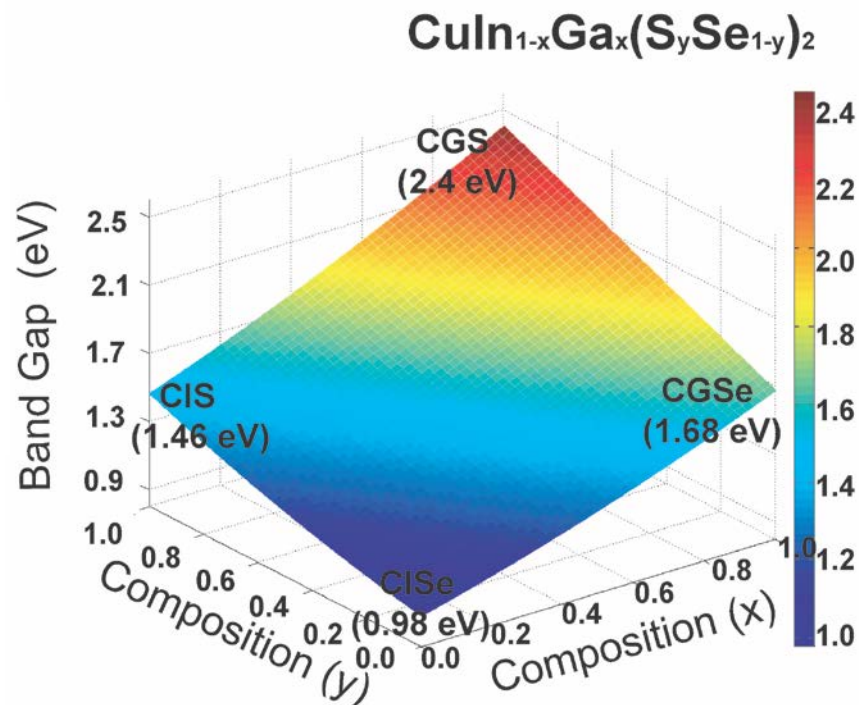
Facile colloidal synthesis of quinary $\text{CuIn}_{1-x}\text{Ga}_x(\text{S}_y\text{Se}_{1-y})_2$ (CIGSSe) nanocrystal inks with tunable band gaps for use in low-cost photovoltaics†

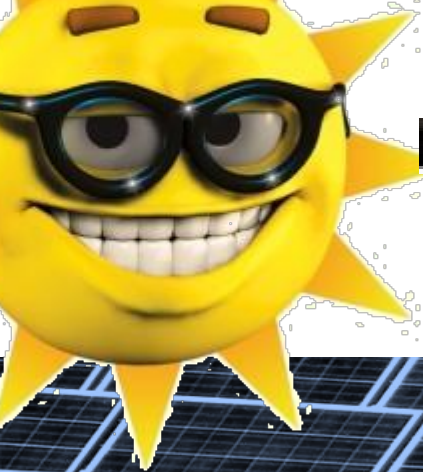
Shu-Hao Chang,^a Ming-Yi Chiang,^a Chien-Chih Chiang,^b Fang-Wei Yuan,^a Chia-Yu Chen,^a Bo-Cheng Chiu,^a Tzu-Lun Kao,^a Chi-Huang Lai^c and Hsing-Yu Tuan^{*a}

Received 11th August 2011, Accepted 26th September 2011

DOI: 10.1039/c1ee02341a

We report, for the first time, colloidal synthesis of quinary $\text{CuIn}_{1-x}\text{Ga}_x(\text{S}_y\text{Se}_{1-y})_2$ (CIGSSe) nanocrystals across the entire composition range $(x,y) = 0$ to 1 with band gaps tunable in the range of 0.98 to 2.40 eV by facile chemical synthesis. As a proof-of-concept, thin-film solar cells made by using the CIGSSe nanocrystal inks as an absorber layer precursor exhibited an efficiency over 1% under AM 1.5 illumination.





CIGS₂Se nanoinks

Composition control

Phase Control

Shape Control

Size control

Phase transfer

Large quantity

Low cost Solar cell application